

# Applications of optical analysis in Reverse-Engineering

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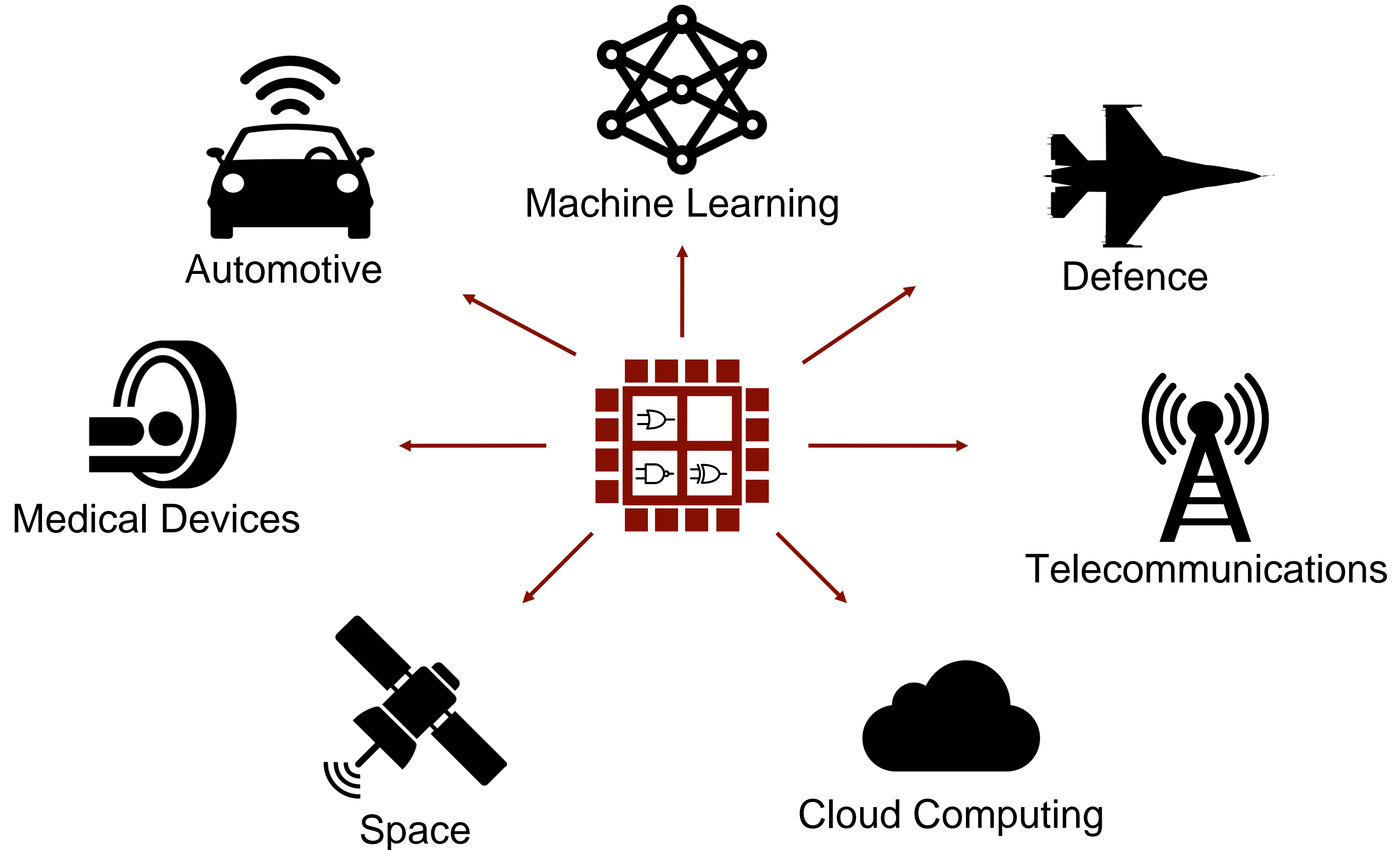
Physical Inspection and Attacks on ElectronicS (PHIKS)

**HAMAMATSU**  
PHOTON IS OUR BUSINESS

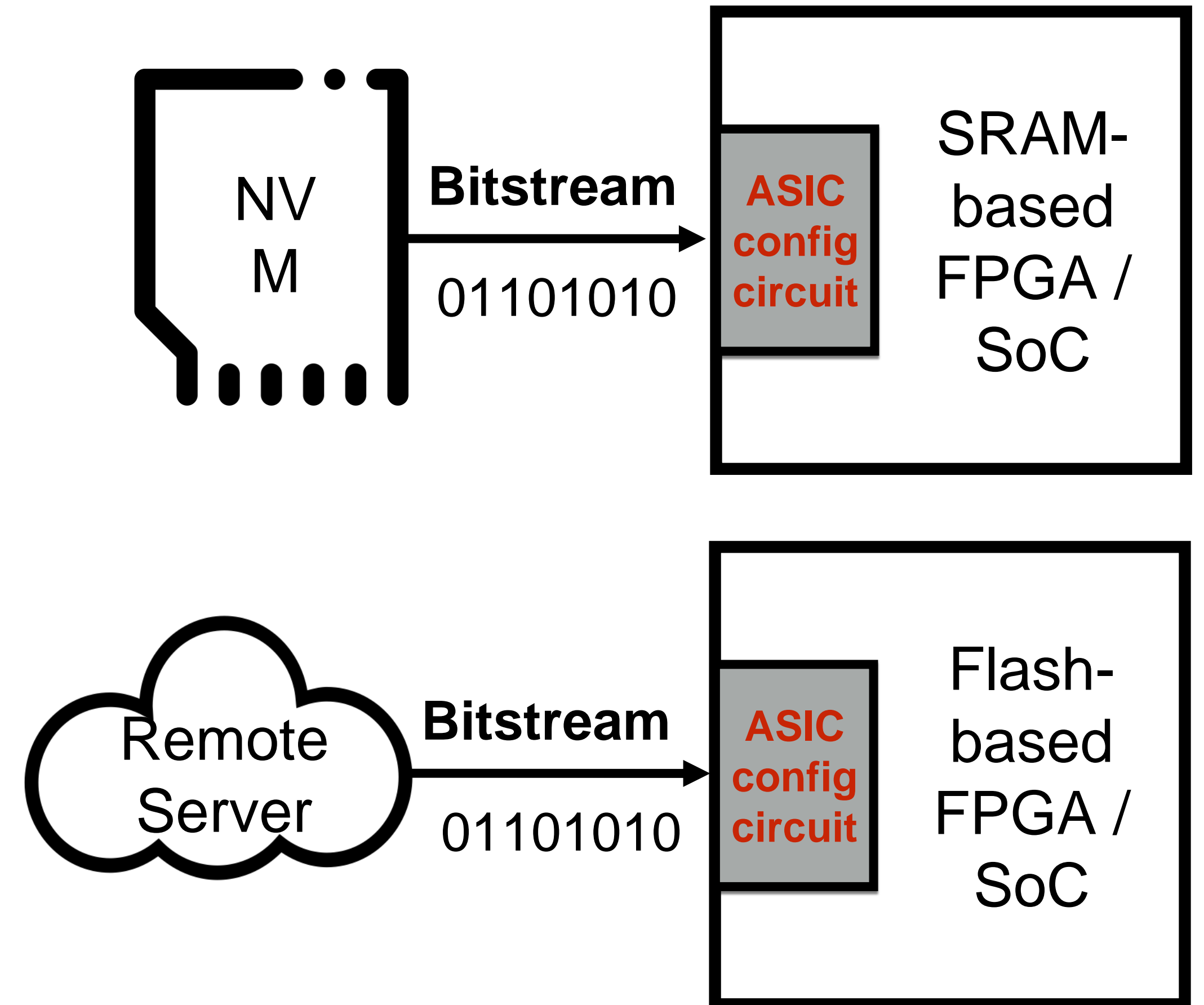
**FOS**  
Research

# Evaluating the security of Field Programmable Gate Arrays (FPGAs) as case studies

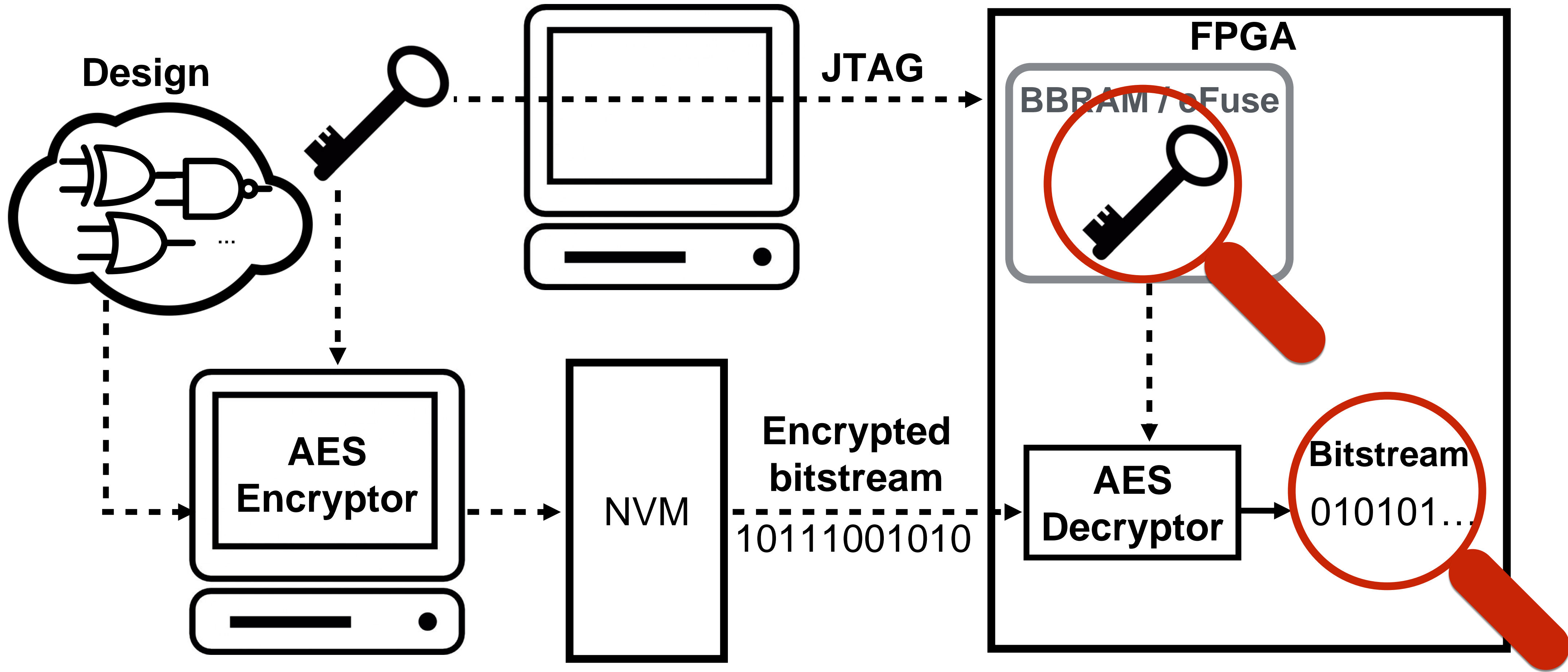
# Field Programmable Gate Array (FPGA)



- **Bitstream:** configuration data containing Intellectual Property (IP) and secrets for reconfigurable hardware
- The bitstream can be loaded in the field (**adversarial environment**)
- **Threats:** cloning, reverse-engineering, tampering or spoofing



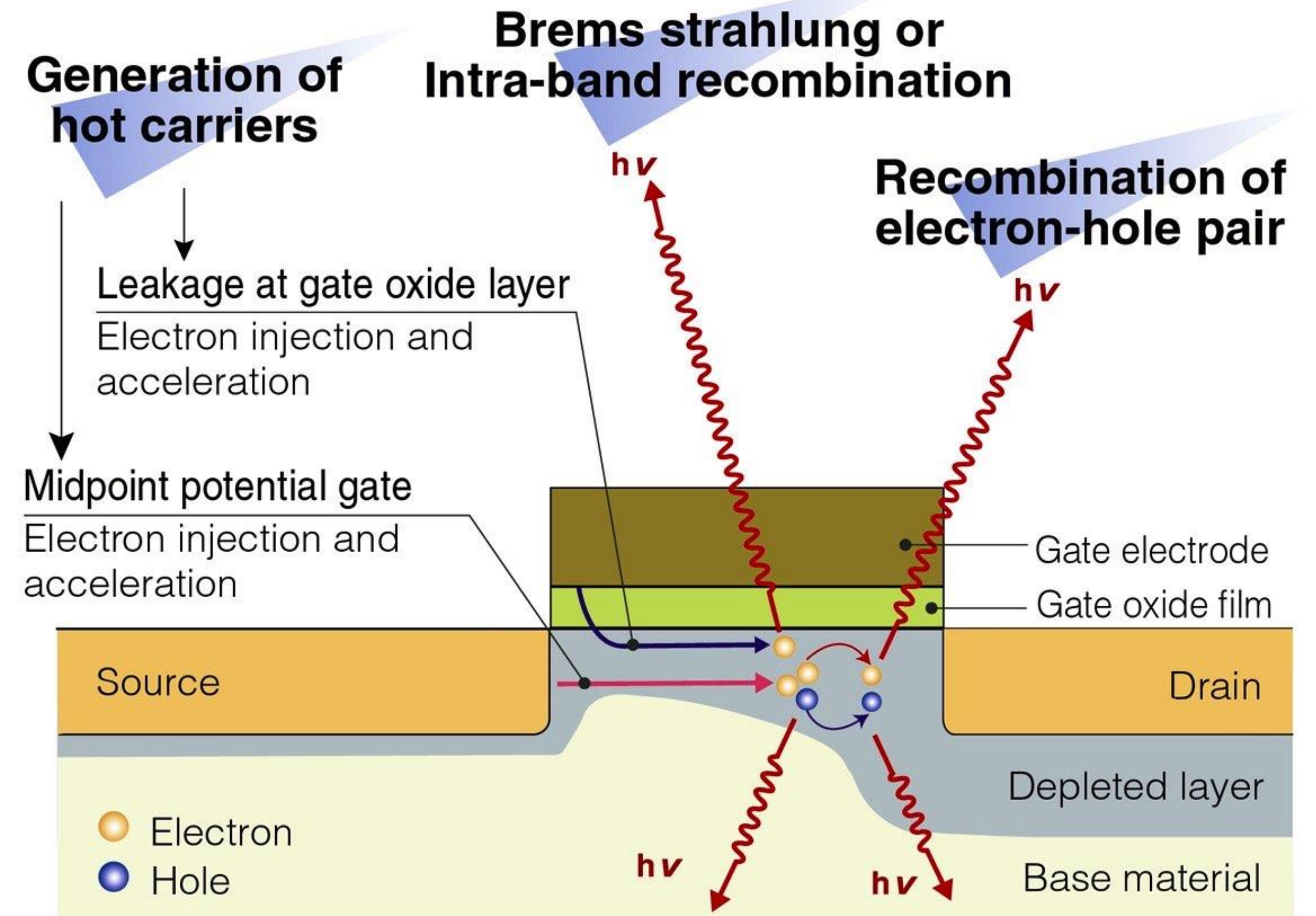
# Case Study: Attacking Bitstream Encryption of FPGAs



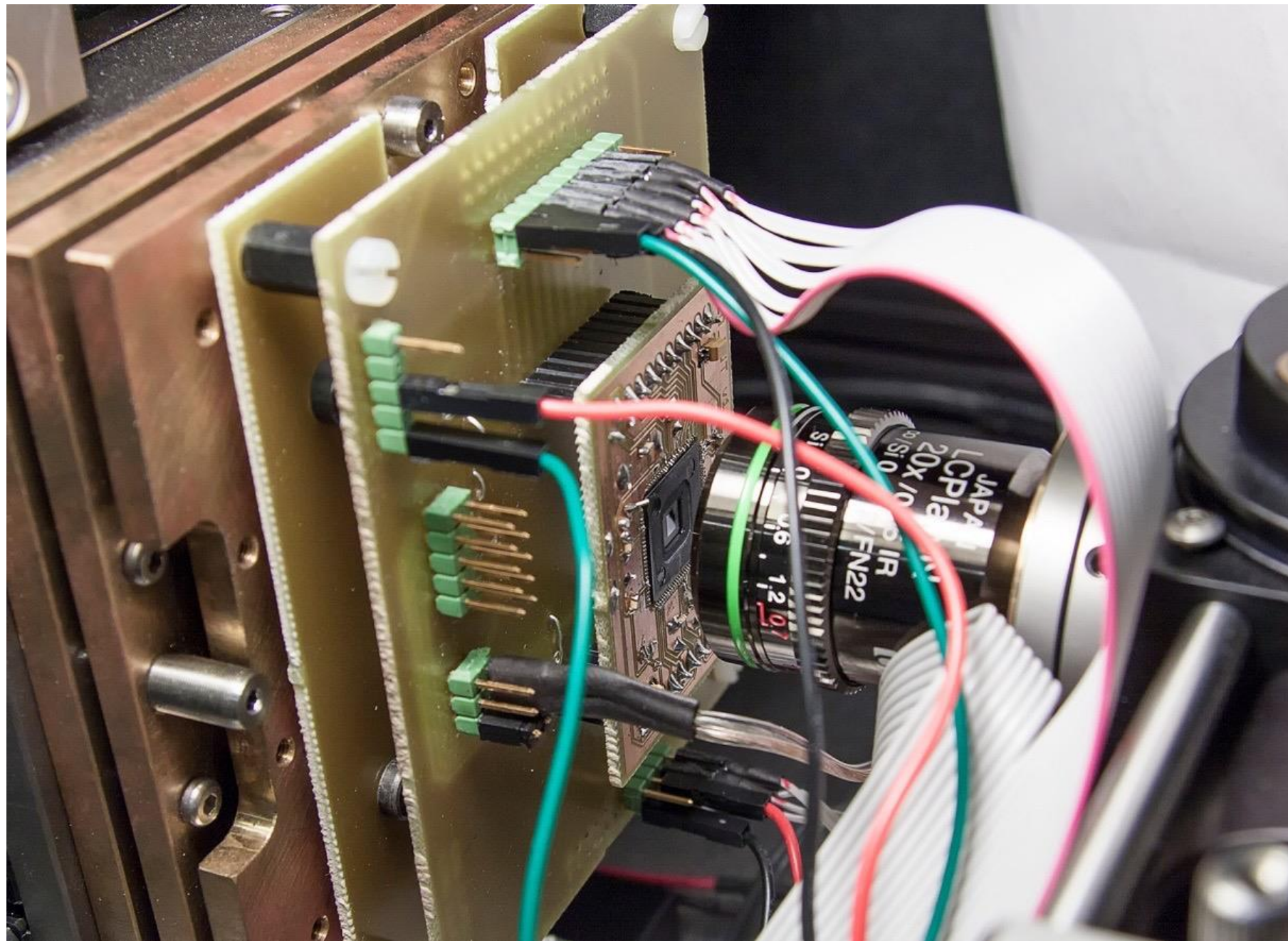
# Photon Emission Analysis

# Mechanism of Photon Emission

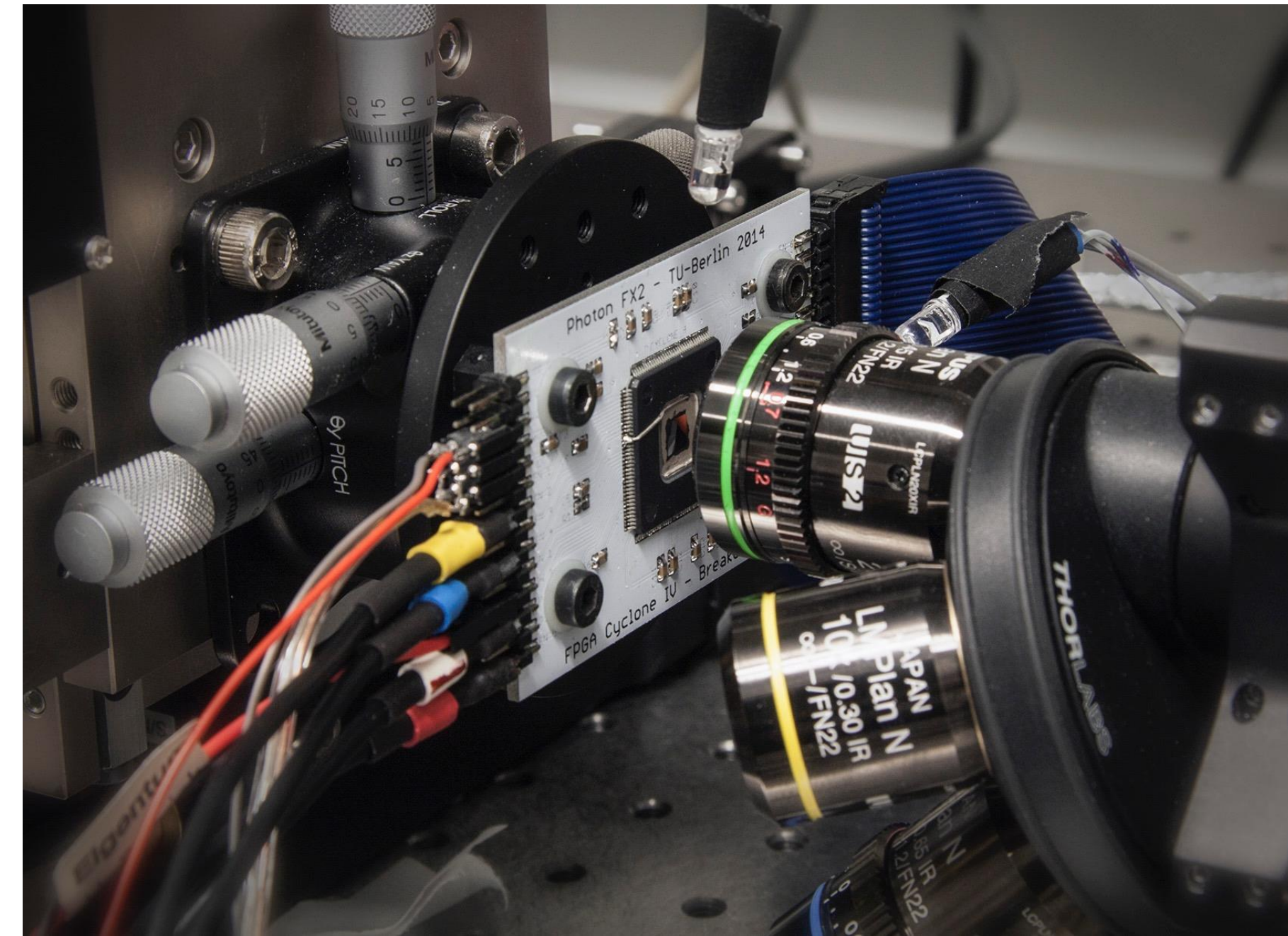
- As carriers are accelerated by electric fields they gain kinetic energy, which is then released via generating photons.
- In CMOS transistors this hot-carrier luminescence takes place at the drain edge where the source-drain electric field is most intense and **predominantly in n-type transistors as electrons are more easily accelerated than holes.**
- In the case of CMOS-inverter, the vast majority of photons are generated **when the input switches from 0 to 1 >> data dependent**
- The photon generation rate is governed primarily by the supply voltage and the switching frequency of the transistor under observation.



- Older package technologies like QFPs should be decapsulated and soldered upside down on a custom PCB



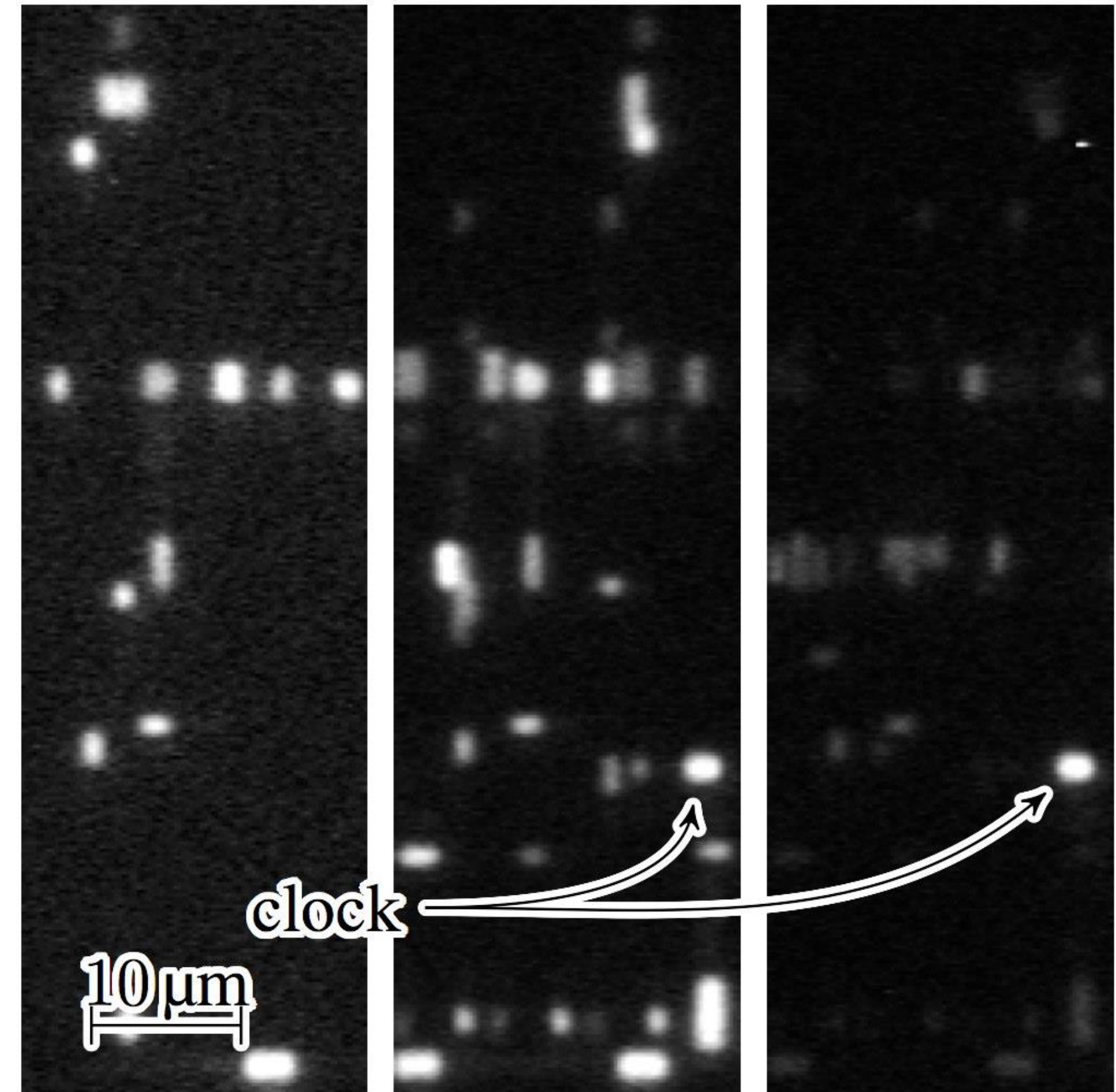
Altera MAX V CPLD (180 nm)



Altera Cyclone IV FPGA (60 nm)



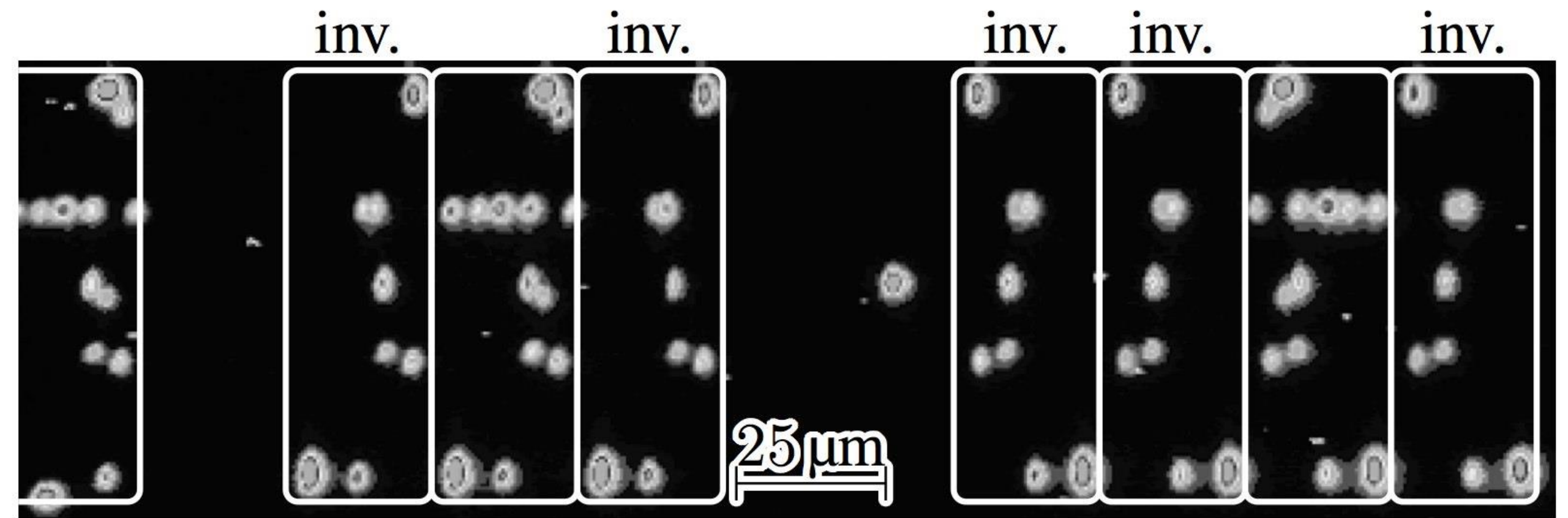
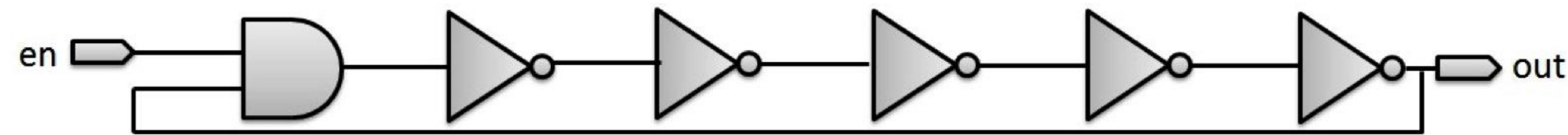
- A Combinatorial Logic: **AND, OR, NOT, XOR**, etc.
- Sequential Logic: Counter, Shift Register, State Machines, etc.
- **Presence of Clock buffers in Sequential Logic**



Altera MAX V (180 nm)

# Example (1): Emission of a Ring-Oscillator

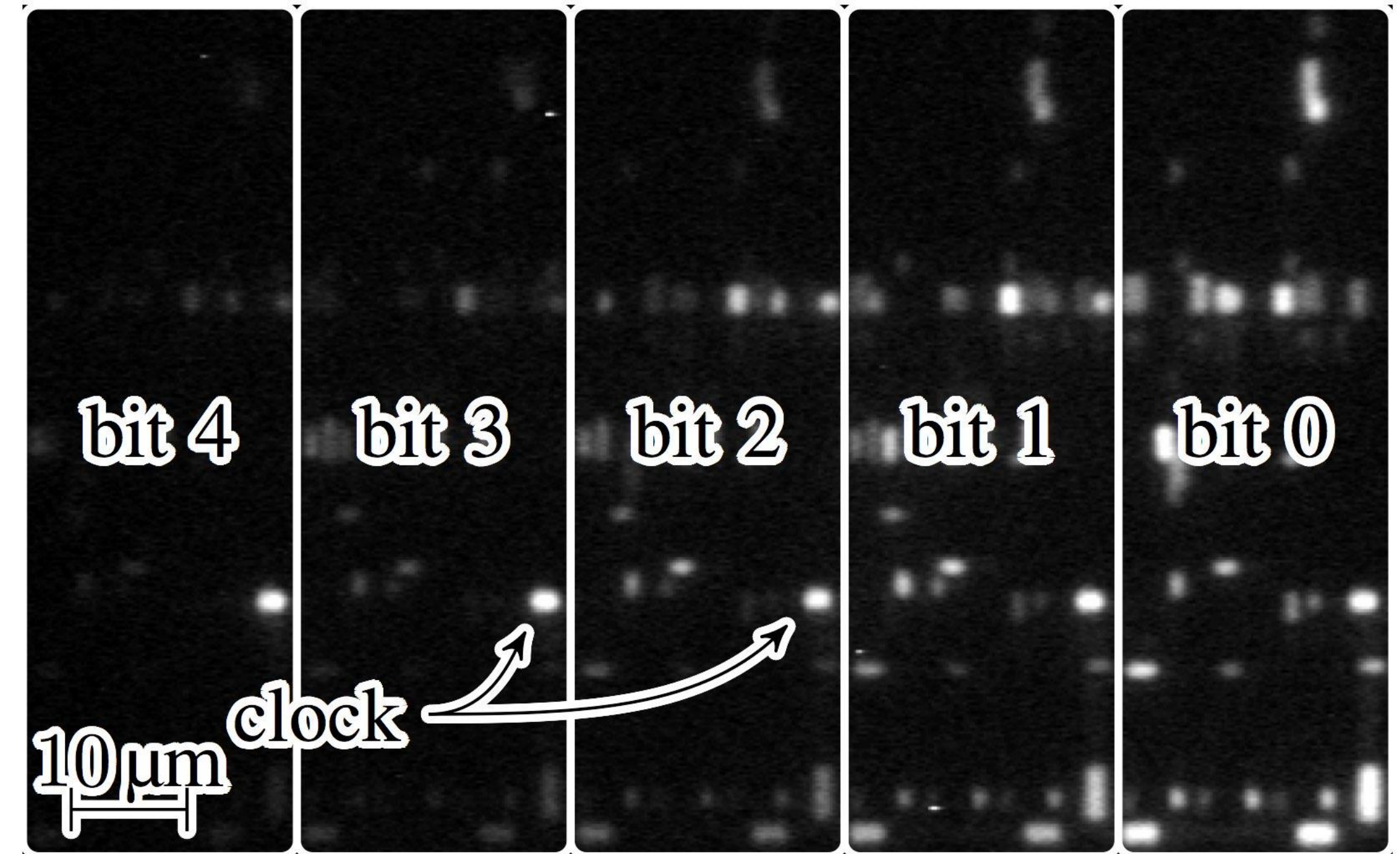
- Identical Switching Frequency by all LEs
- Switching frequency independent and generally higher than clock frequency
- **Applications:** TRNG and Internal Clocks



Altera MAX V (180 nm)

# Example (2): Emission of a Binary Counter

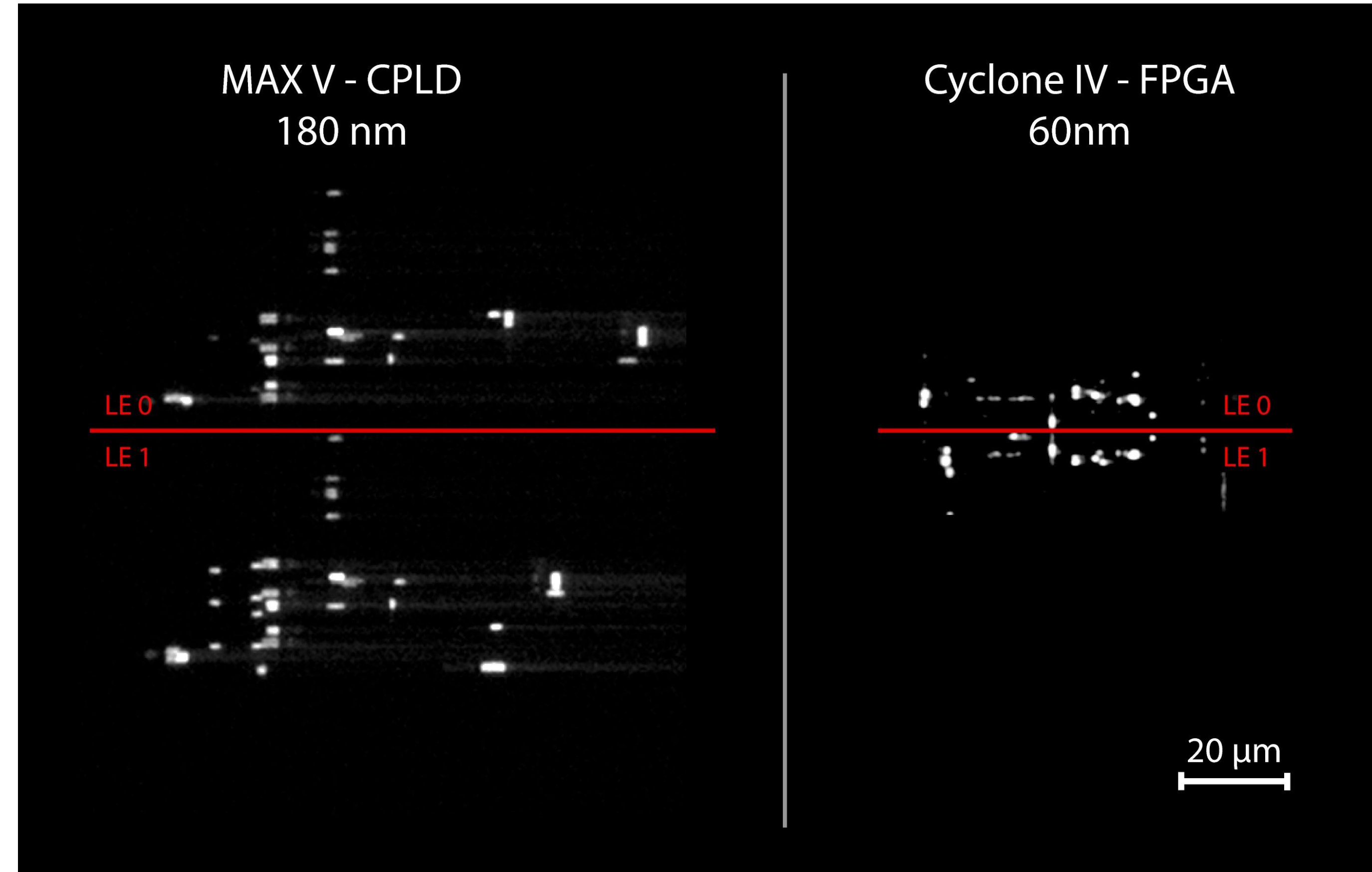
- n-bit counter = n clocked registers + some combinatorial logic
- Identical switching frequency of the clock for all registers
- **Applications:** Delay and Timing circuits such as asynchronous protocols



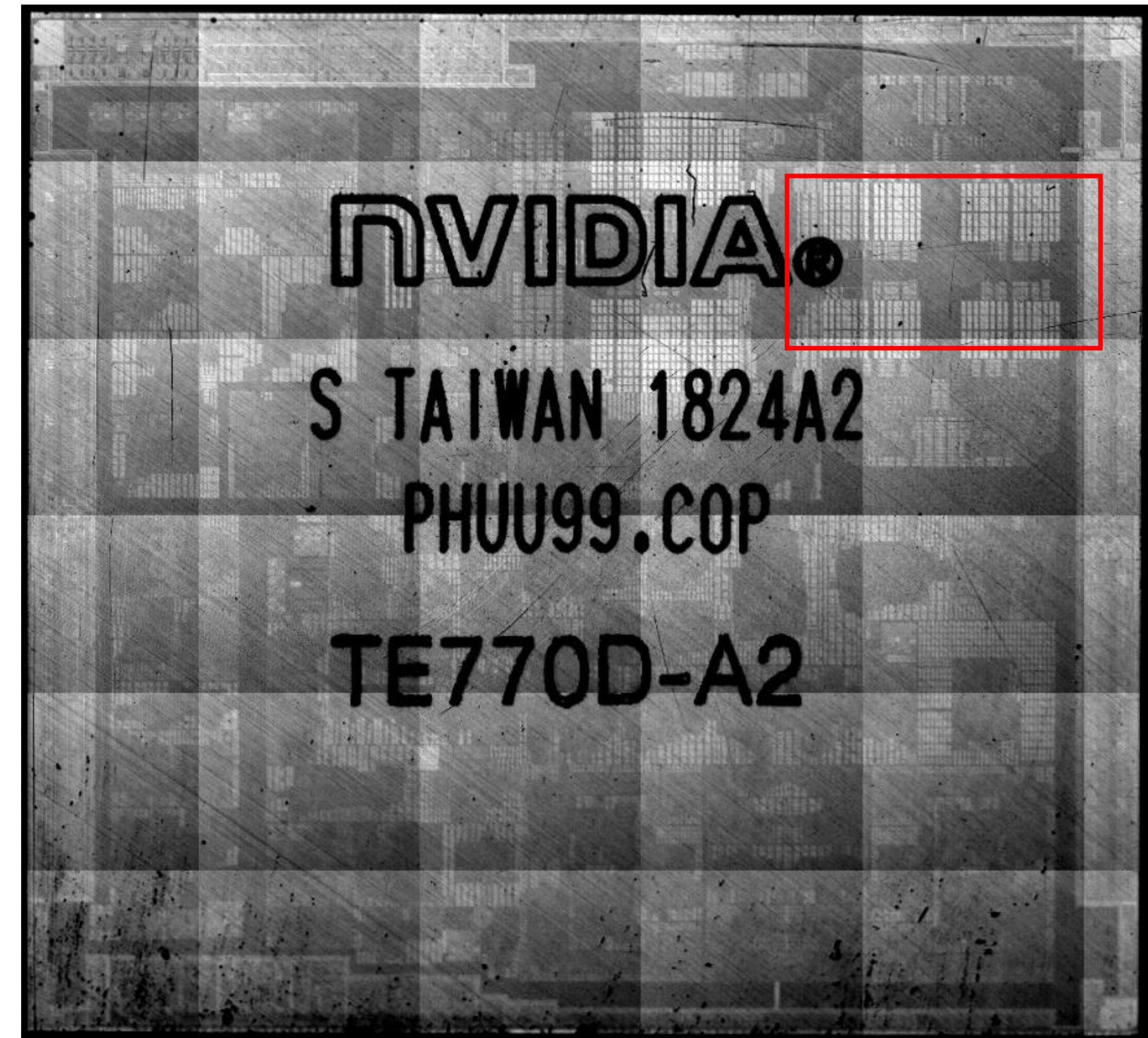
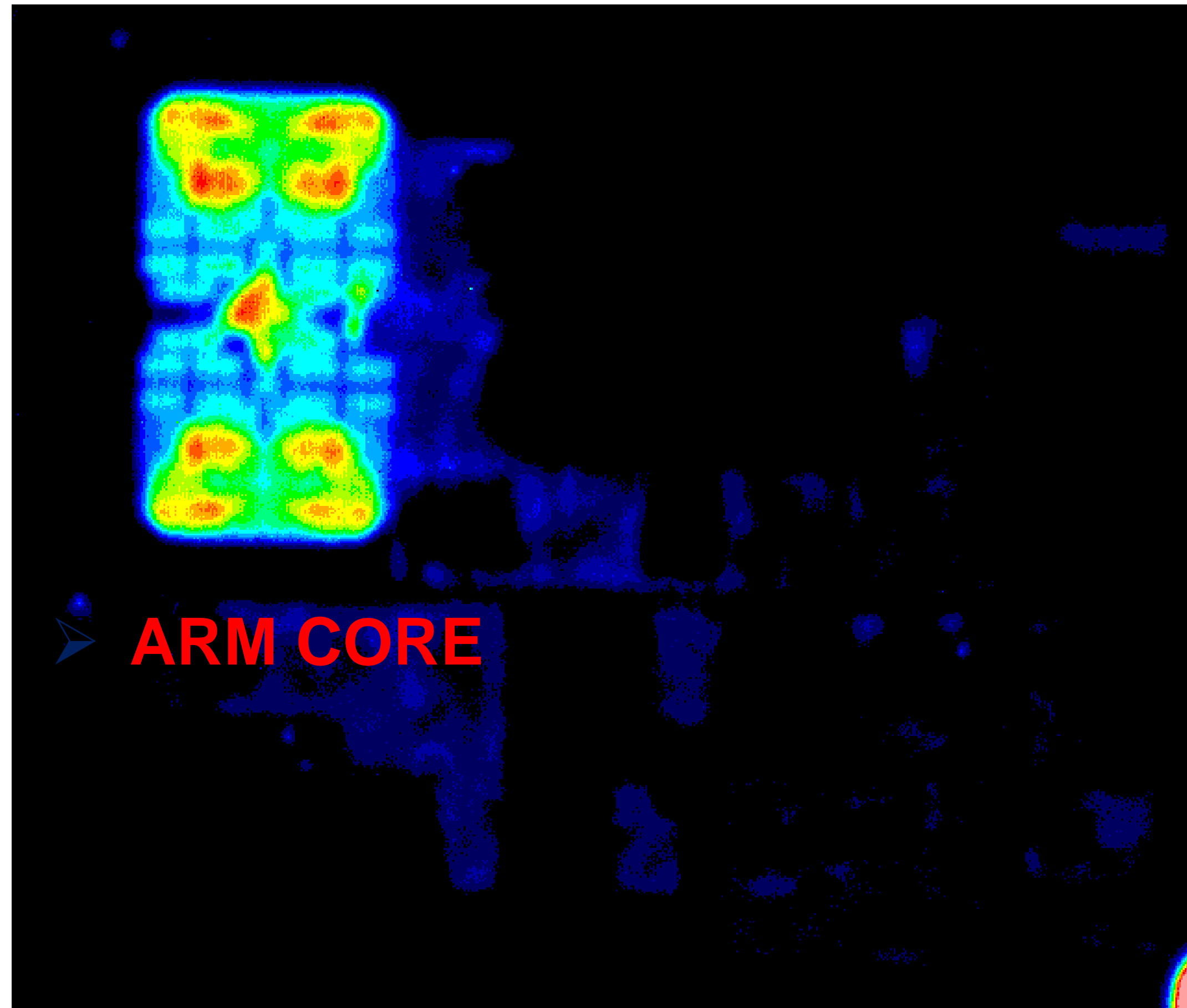
Altera MAX V (180 nm)

# Impact of Technology size on Photon Emission

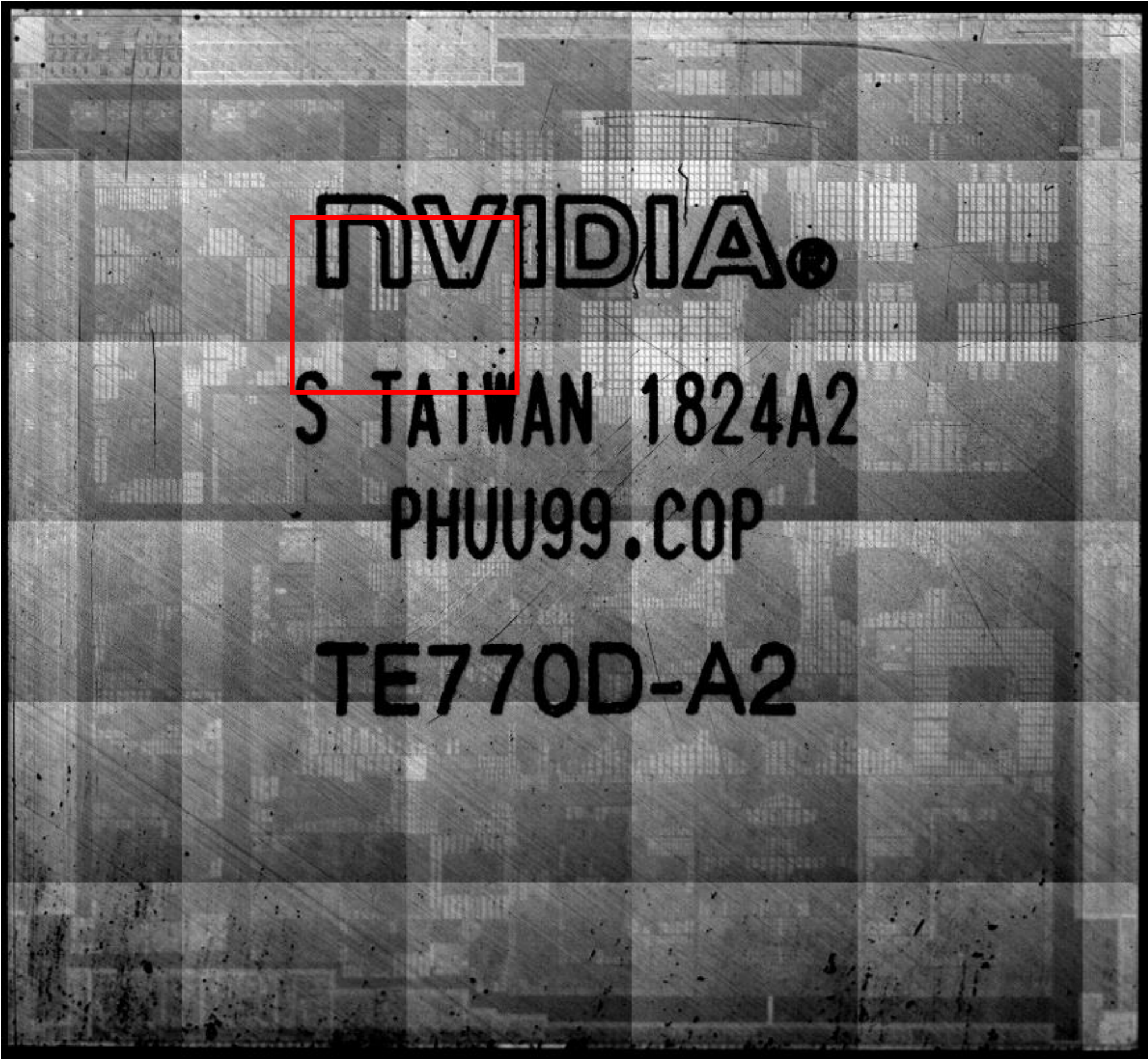
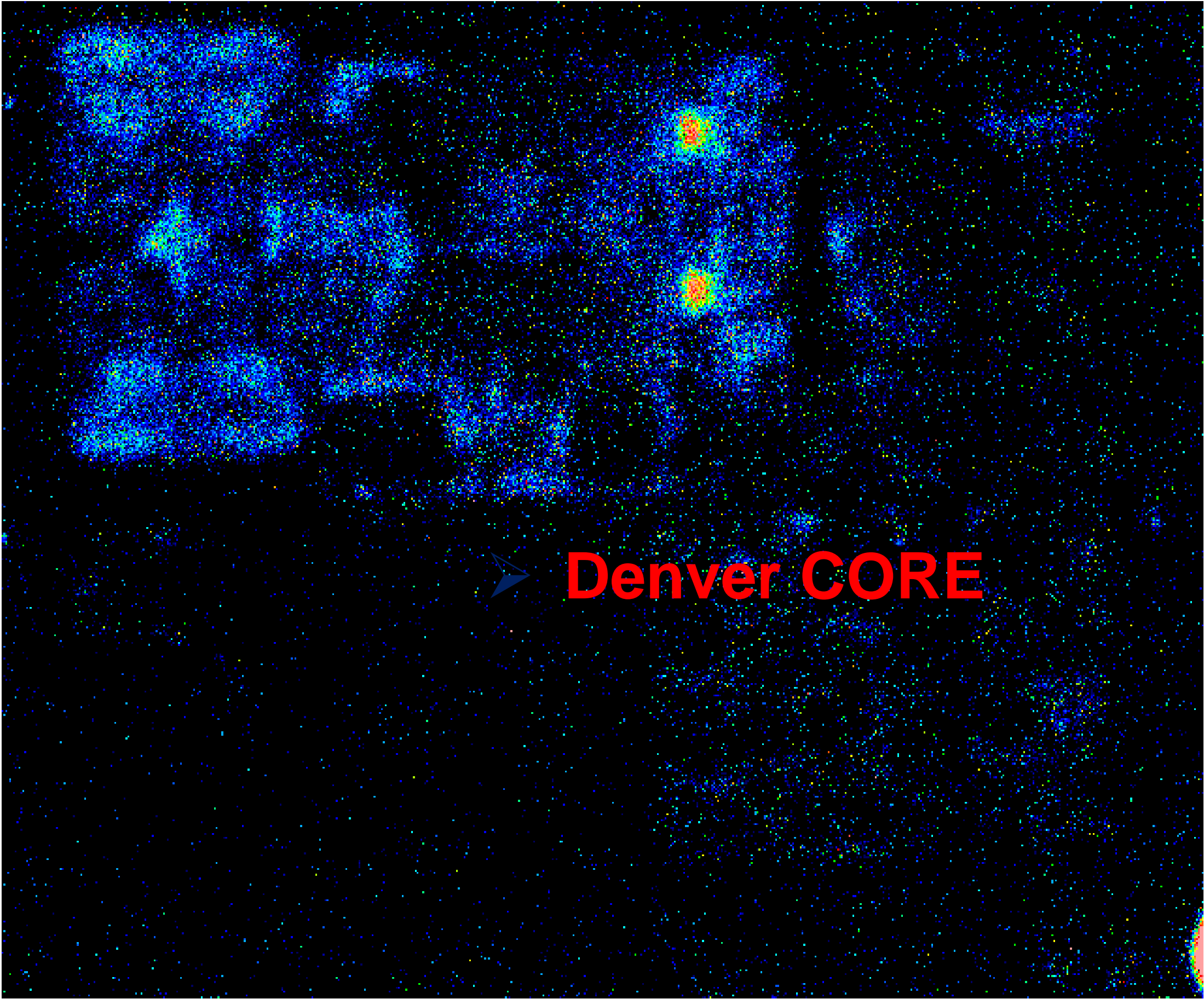
- Lower supply voltage for smaller technologies >> **less photon emission rate**
- Smaller technology >> **harder to resolve a transistor**
- Large space between transistors in LUTs >> **resolving of transistors still possible for the attacker**



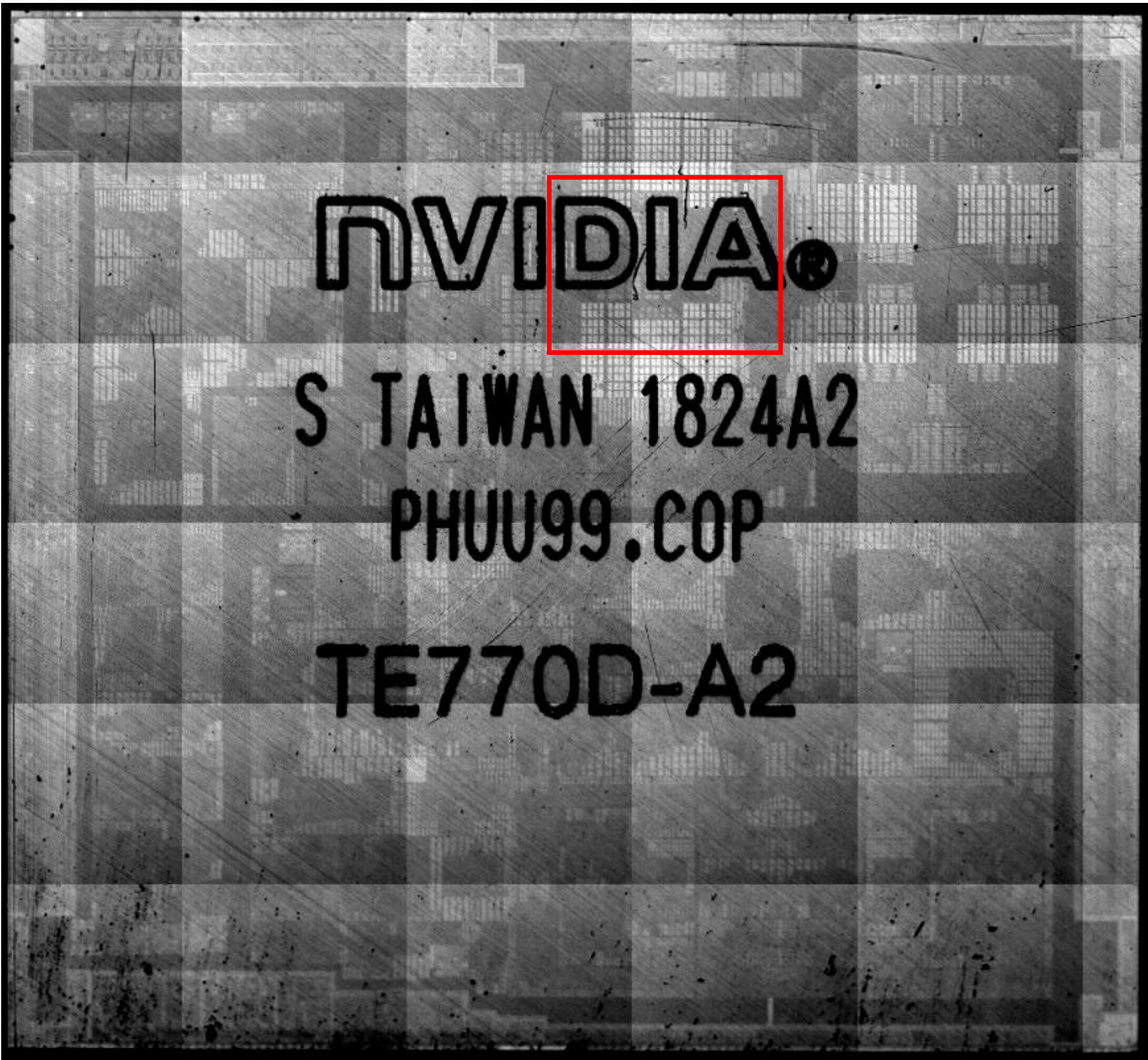
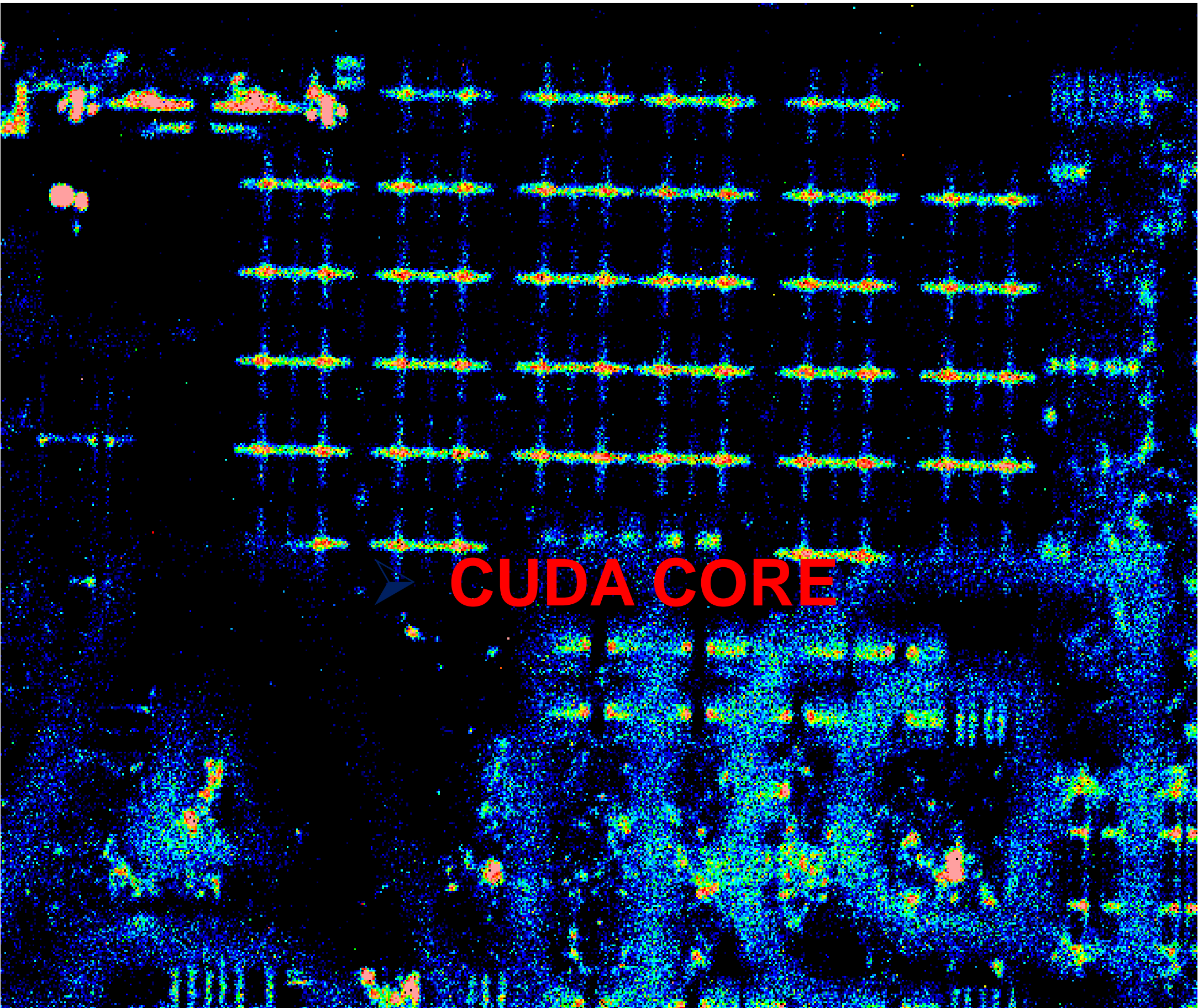
# Core Localizaiton in NVIDIA AI CHIP



# Core Localizaiton in NVIDIA AI CHIP

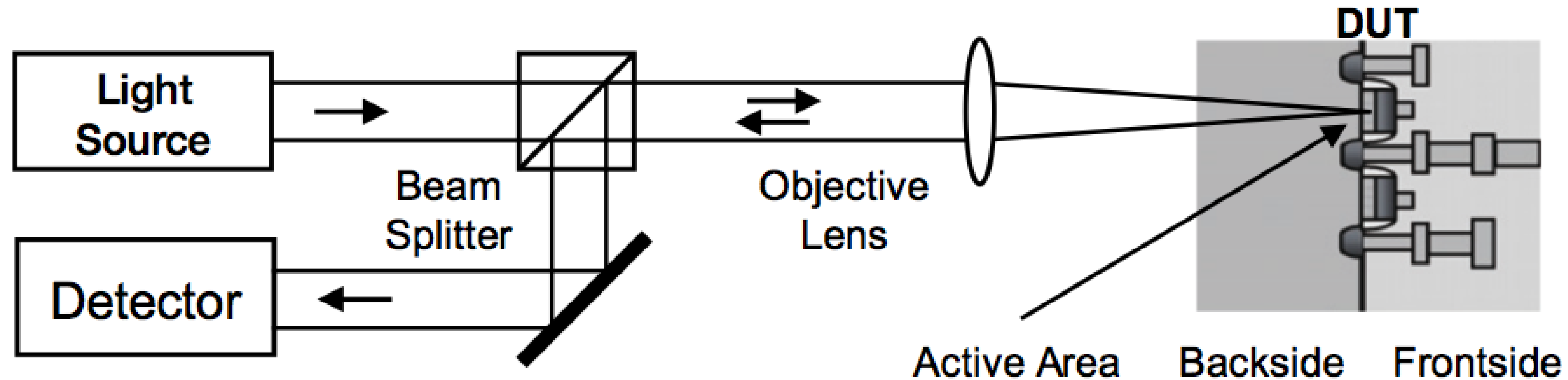


# Core Localizaiton in NVIDIA AI CHIP

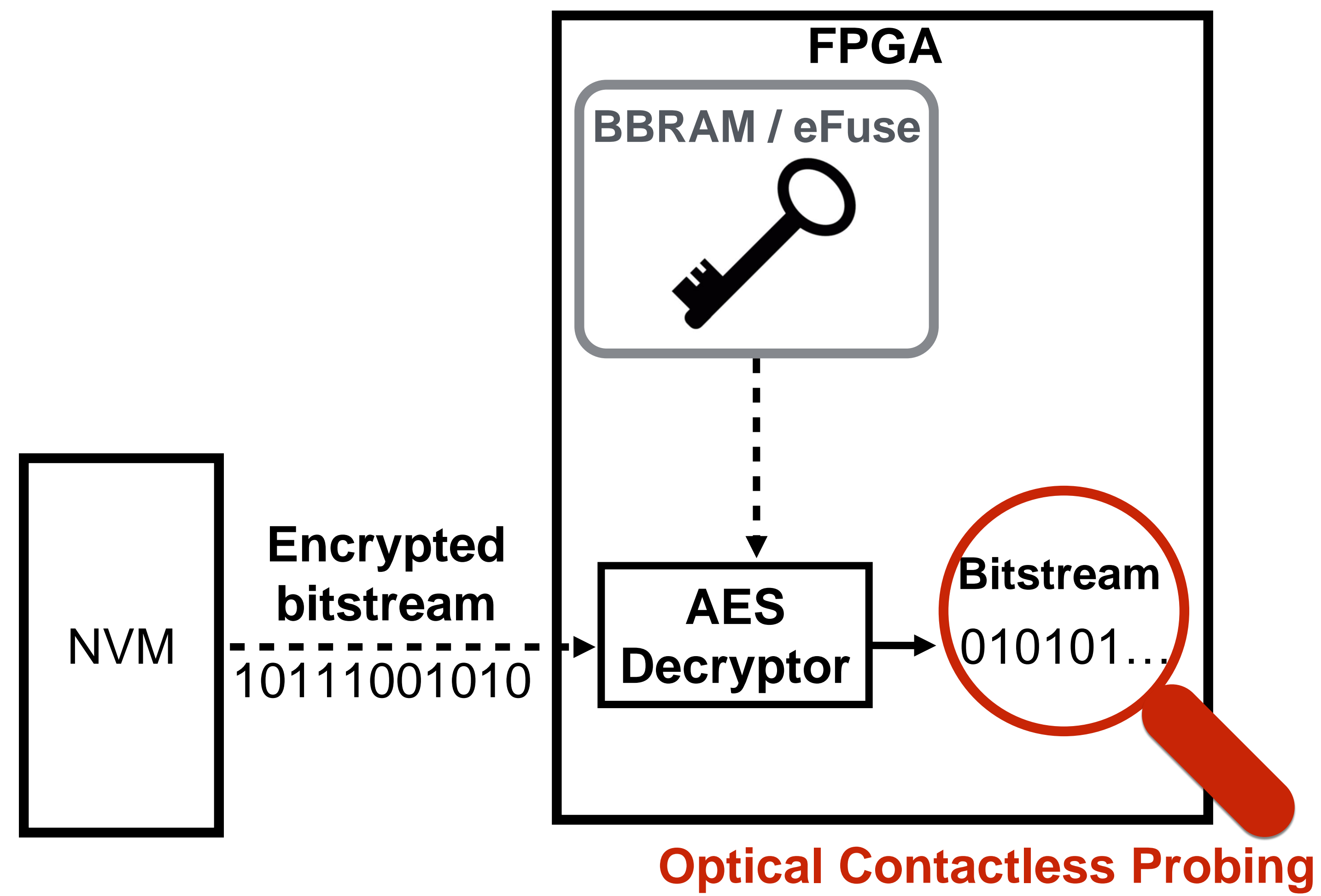


# Optical Contactless Probing



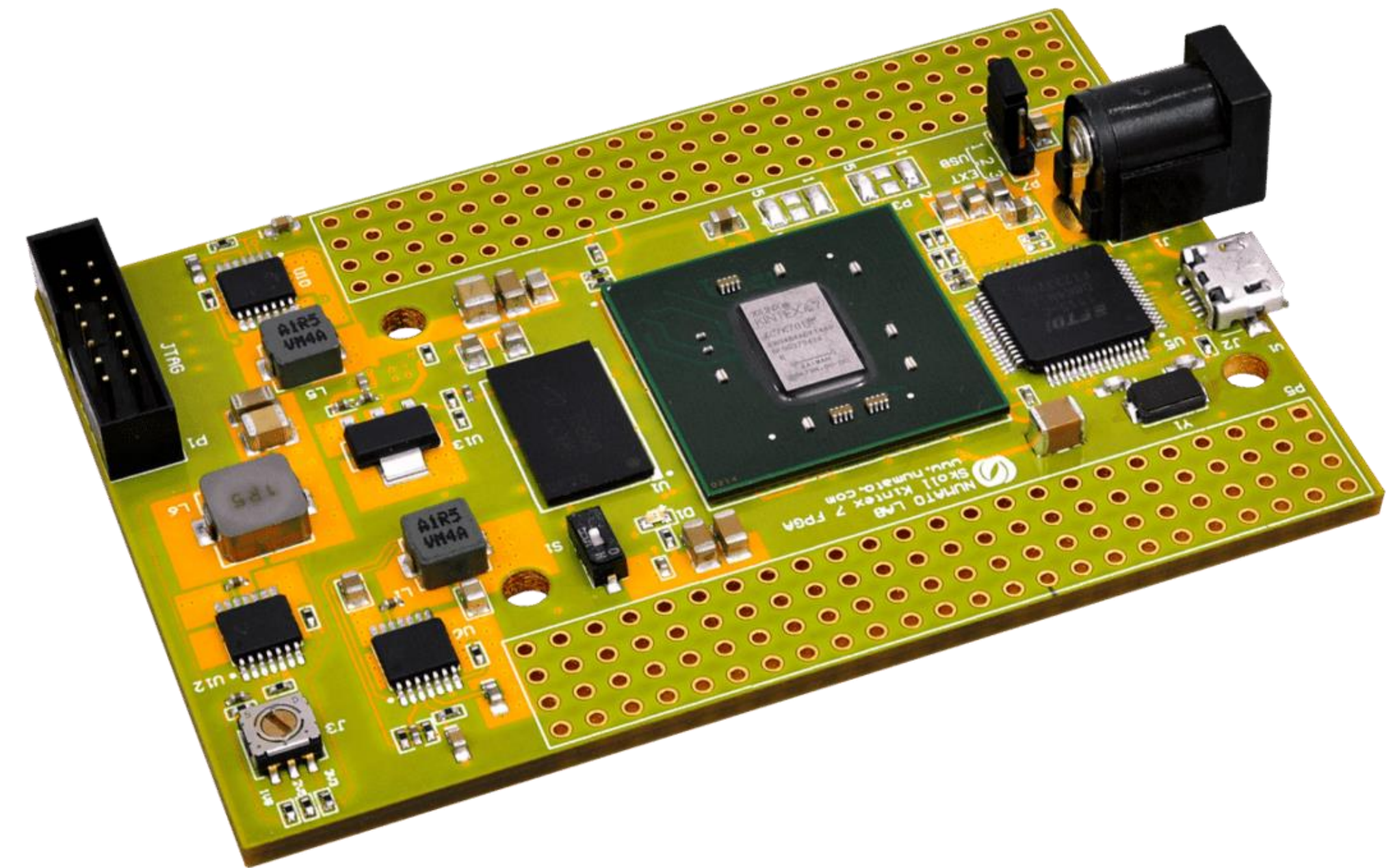


- **Changes in the absorption coefficient and the refractive index of device in active area by electrical field and current.**
- **Electro-Optical Probing (EOP) or Laser Voltage Probing (LVP):** Optical beam intensity altered by voltage/current —> probing of electrical signals on the node
- **Electro-Optical Frequency Mapping (EOFM) or Laser Voltage Imaging (LVI):** Feeding the reflected signal to a detector with a narrow band frequency filter while scanning the laser—> detecting node switching with this frequency



Tajik, S., Lohrke, H., Seifert, J. P., & Boit, C. "On the Power of Optical Contactless Probing: Attacking Bitstream Encryption of FPGAs," In Proceedings of the 2017 ACM SIGSAC Conference on Computer and Communications Security.

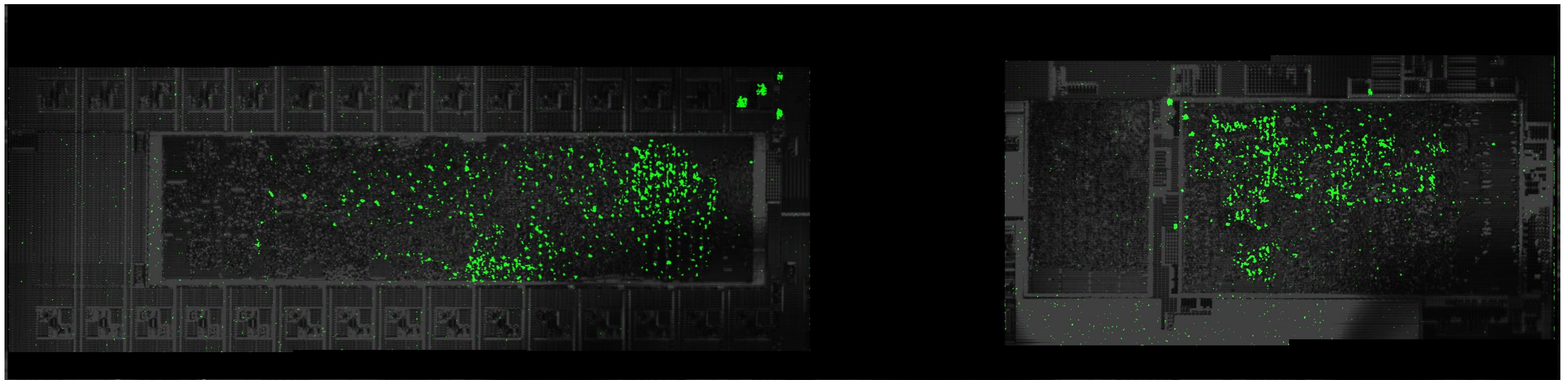
- **Device under Test (DUT):** Skoll - Xilinx Kintex 7 development board
- Chip's technology: 28 nm
- No chip preparation (e.g., depackaging, silicon polishing, etc.)
- **Optical Setup:** Hamamatsu PHEMOS-1000
  - Laser wavelength:  $1.3 \mu\text{m}$
  - Laser spot size:  $>1 \mu\text{m}$



# Localizing Decryption Core using EOFM

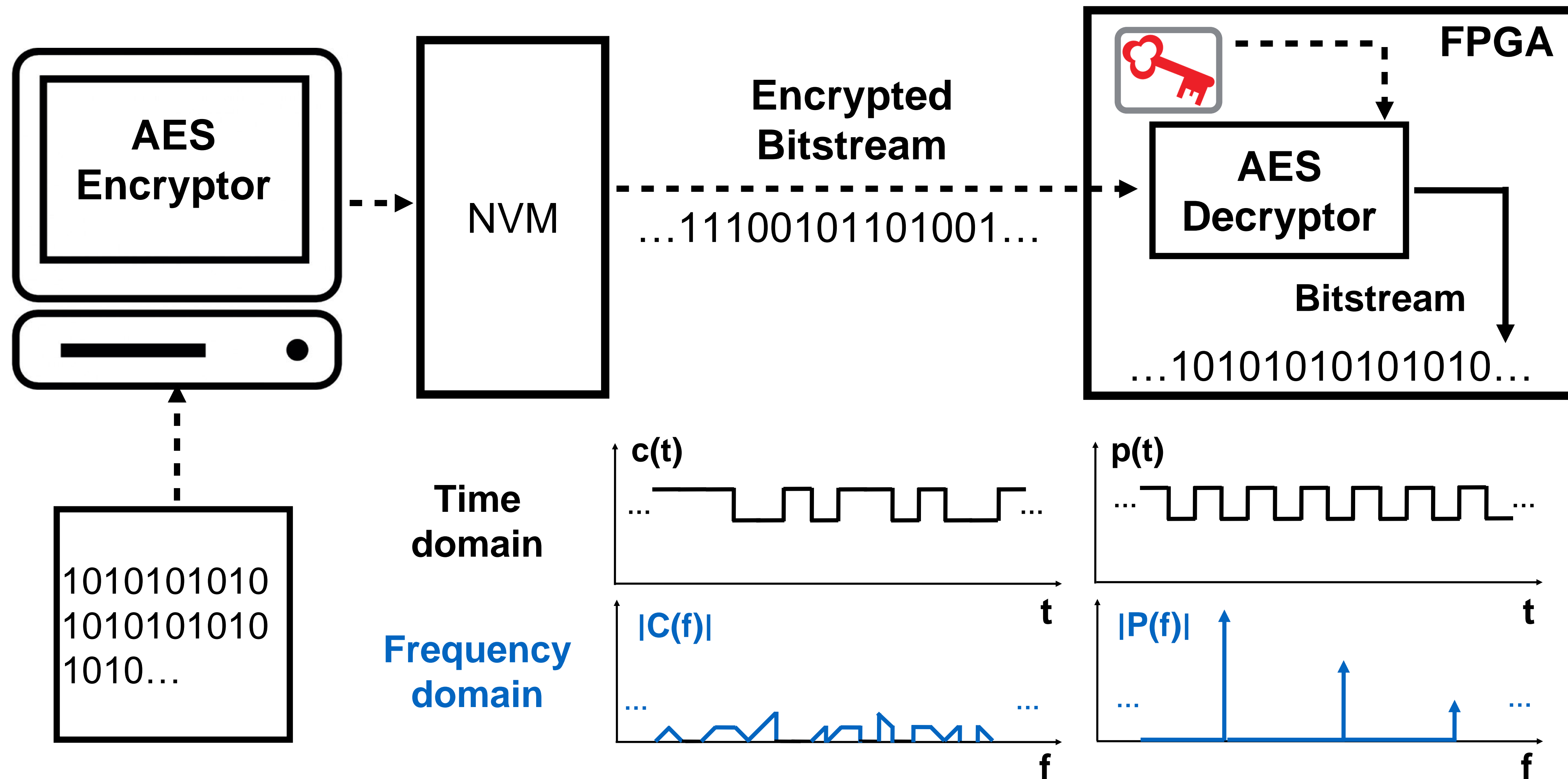
AES Core

Main Core

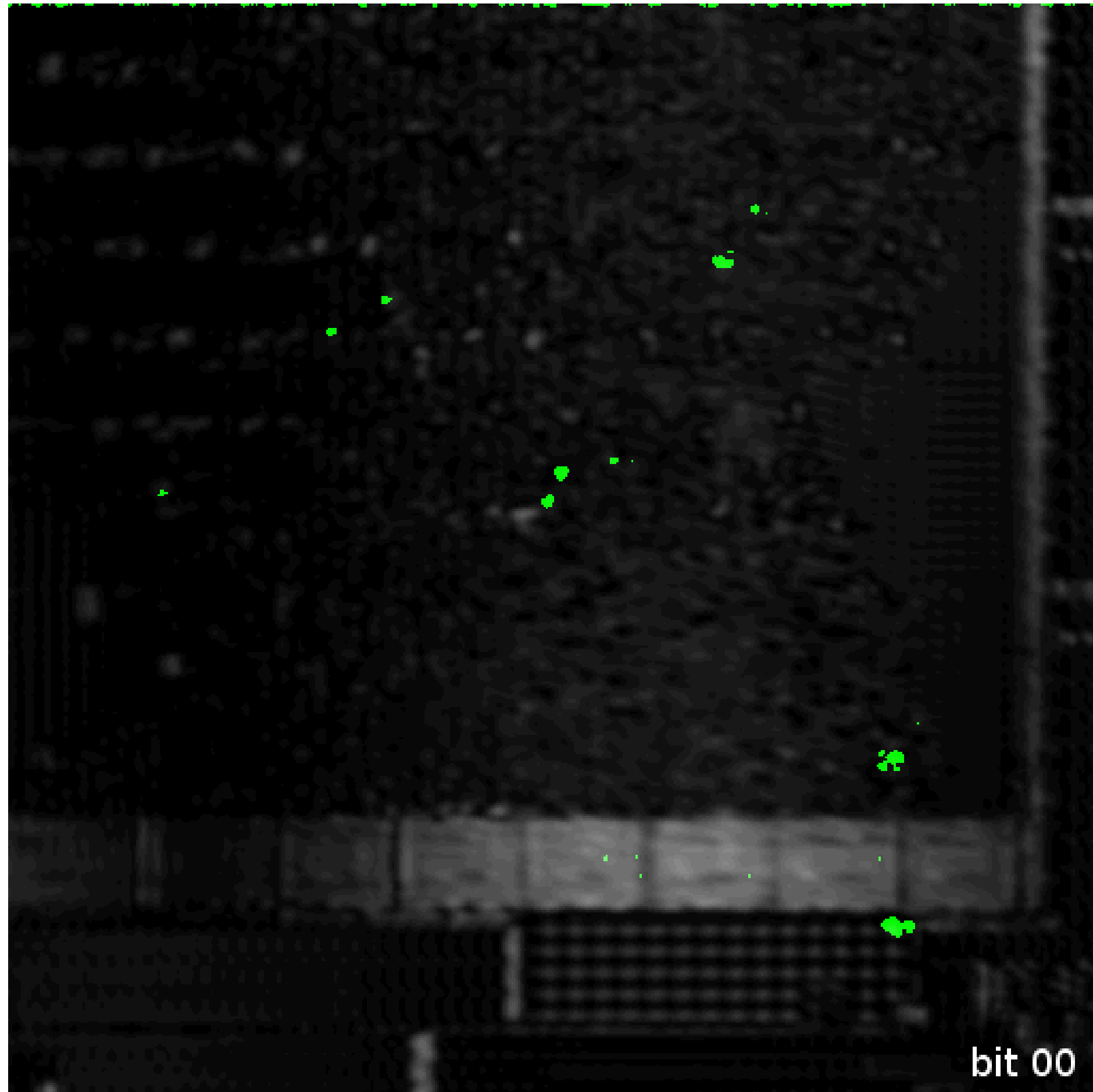


Clock activity for encrypted bitstream

# Frequency Analysis of Regular Bitstream

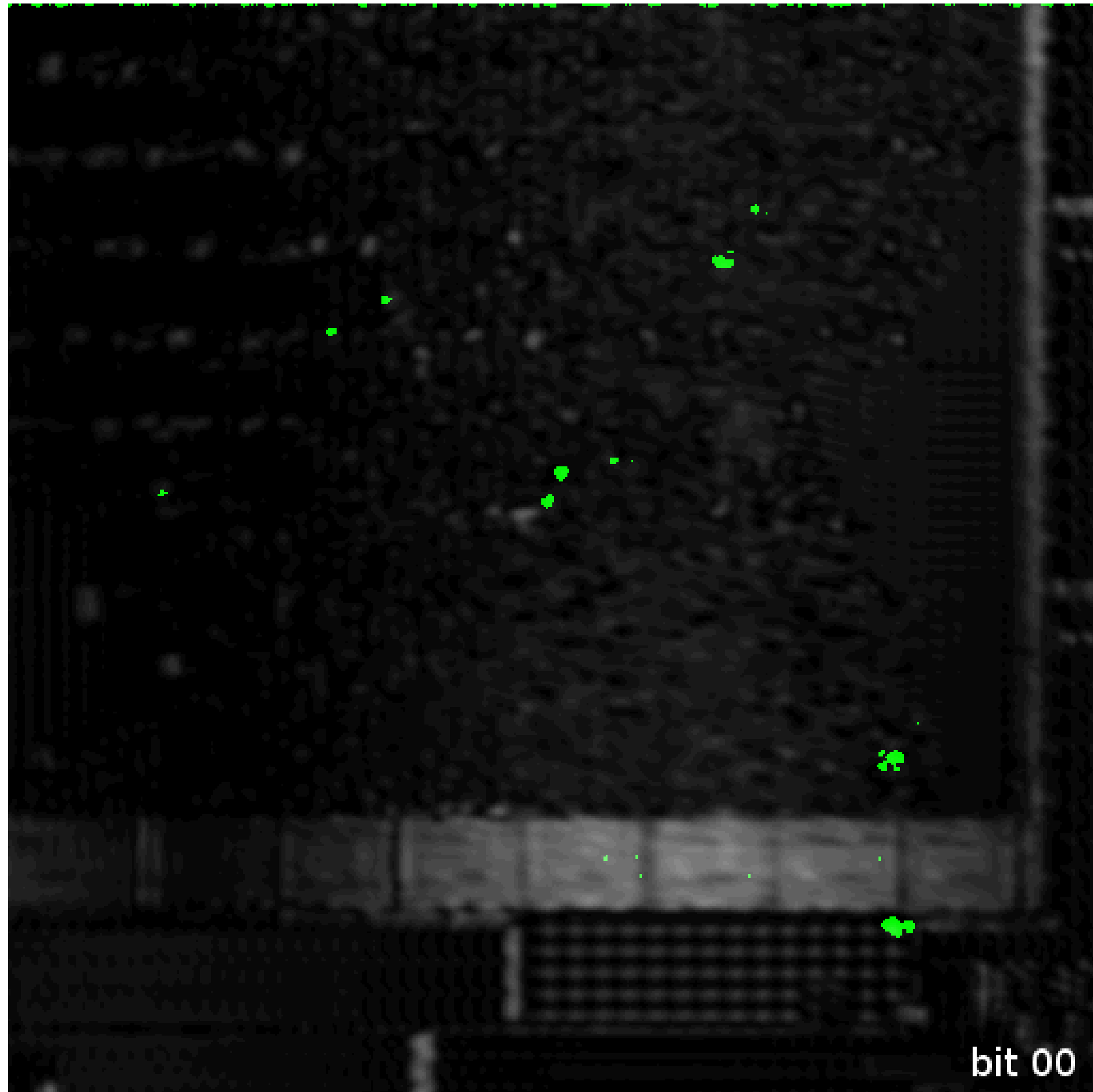


# Locating the plaintext data

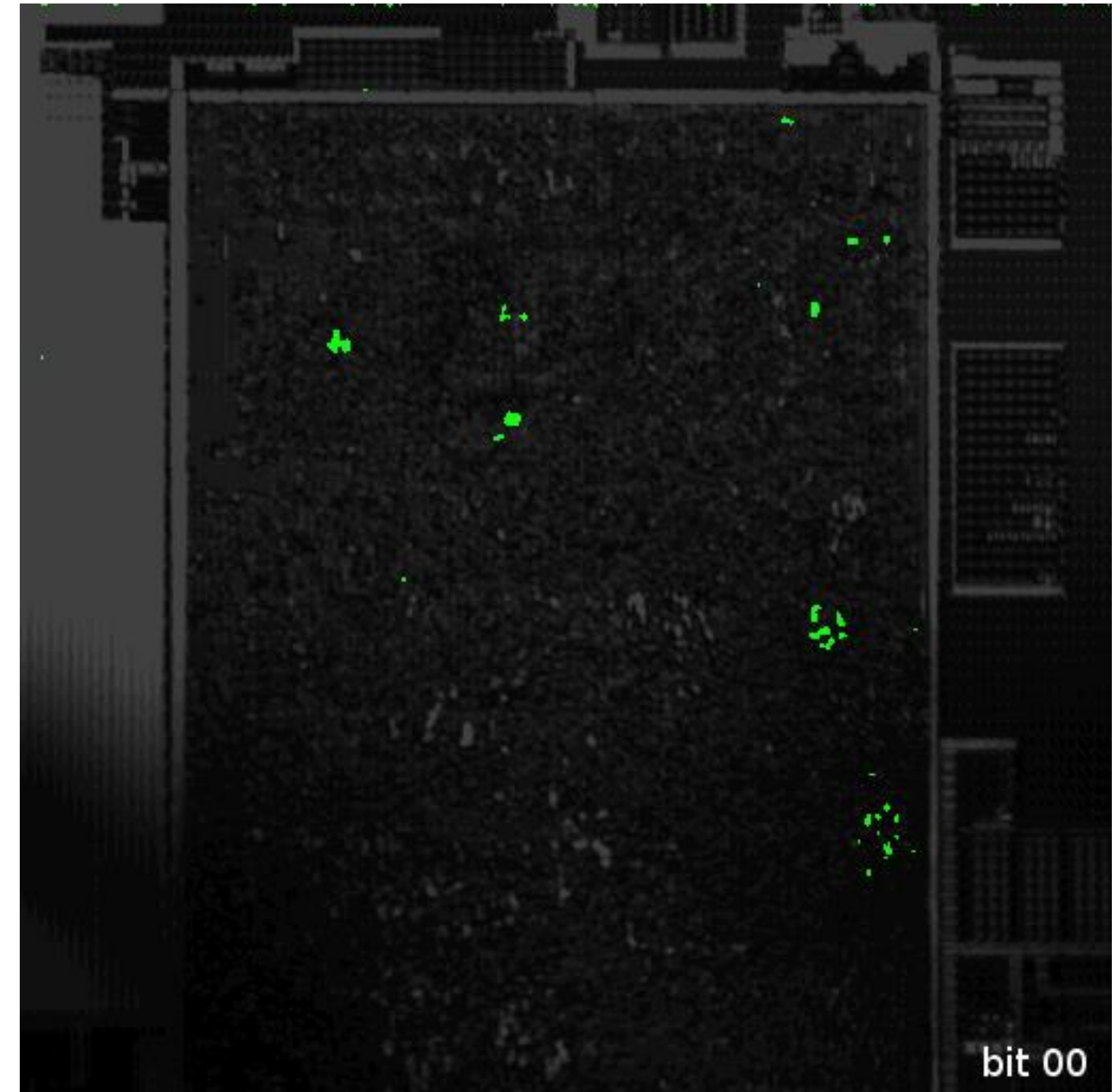


Locations in AES output port

# Locating the plaintext data

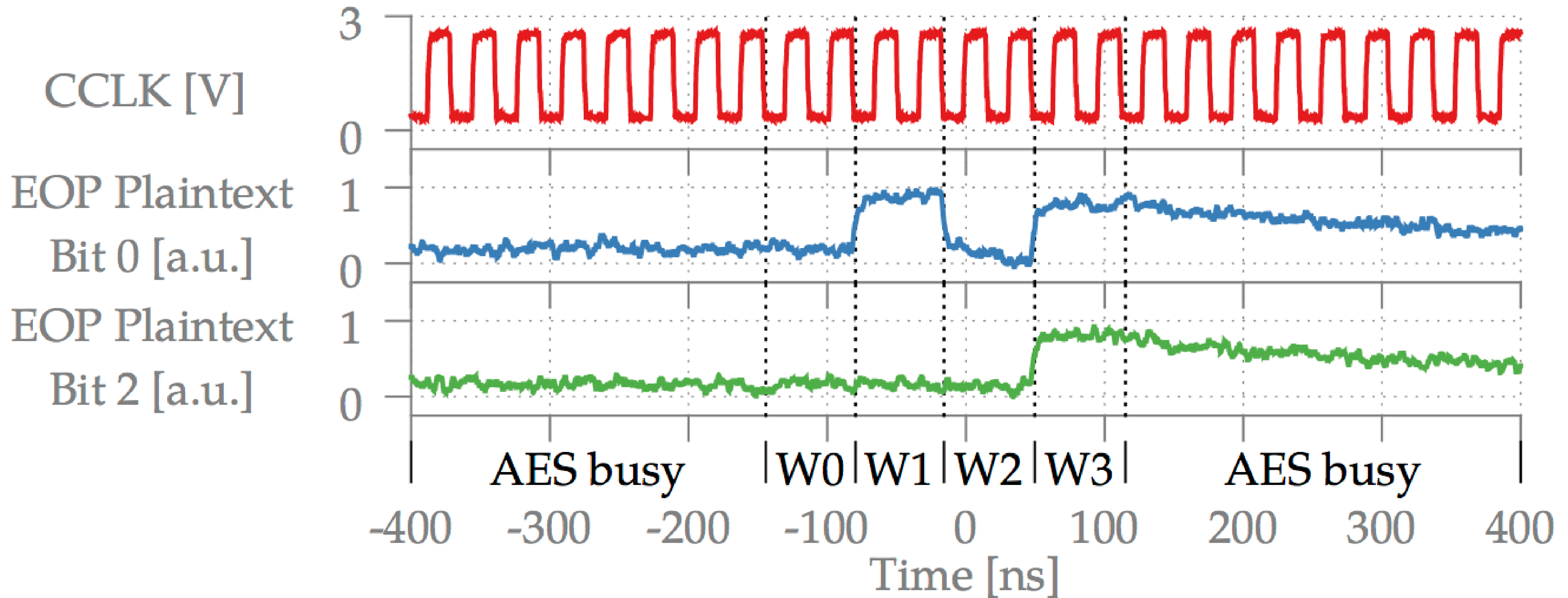


Locations in AES output port



Locations inside main core logic mesh

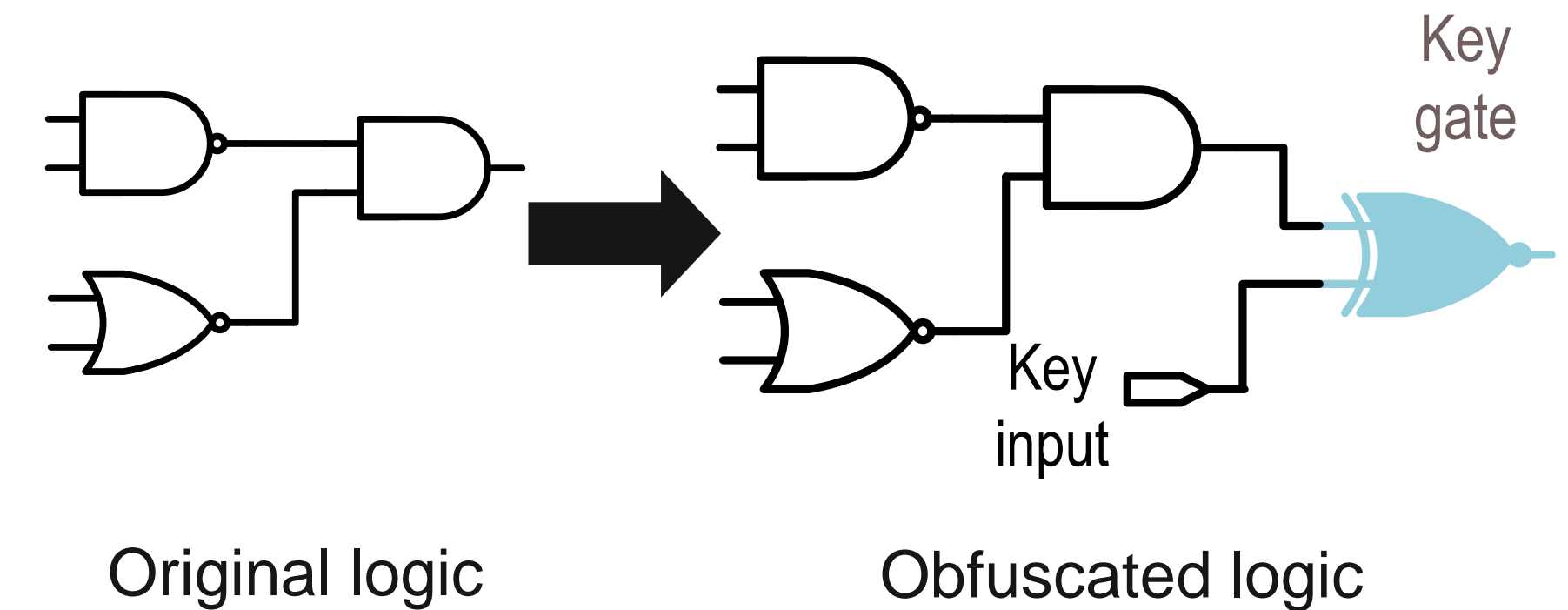
# Extracting Plaintext Data using EOP





## Goal

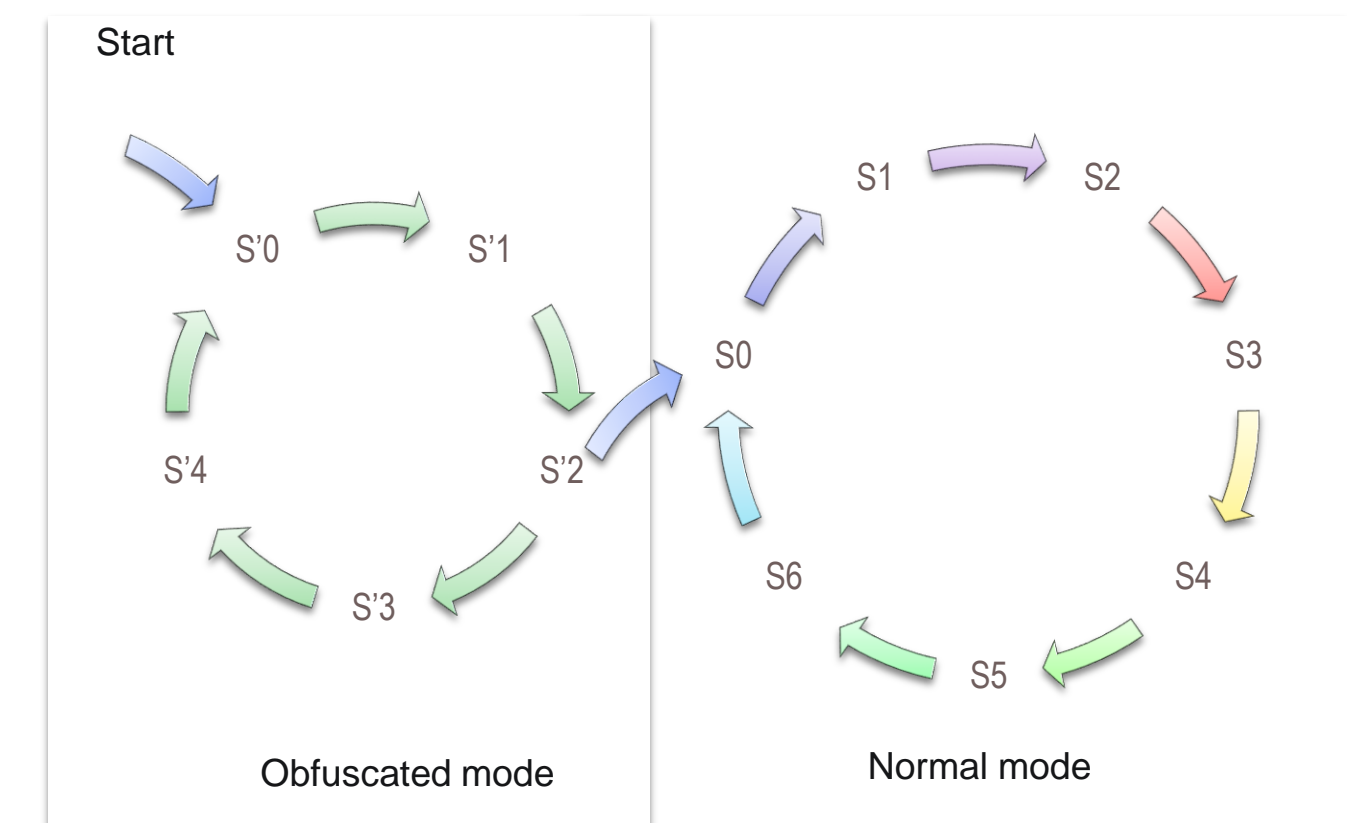
- Locking functionality of IP by inserting additional logic
- key programmed in trusted facility after fabrication



Combinational logic obfuscation

## Classification

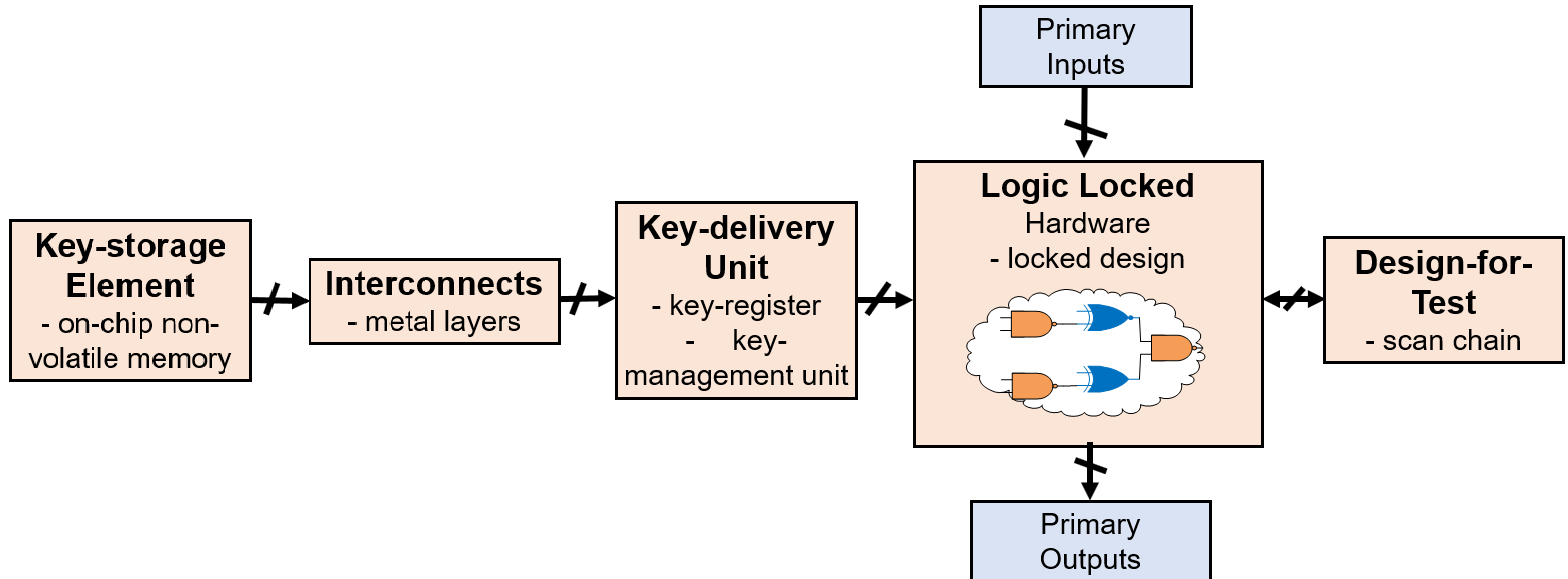
- Combinational Logic Locking: Locking design with logic gates
- Finite State Machine (FSM) Locking: Locking with state transition graph modification



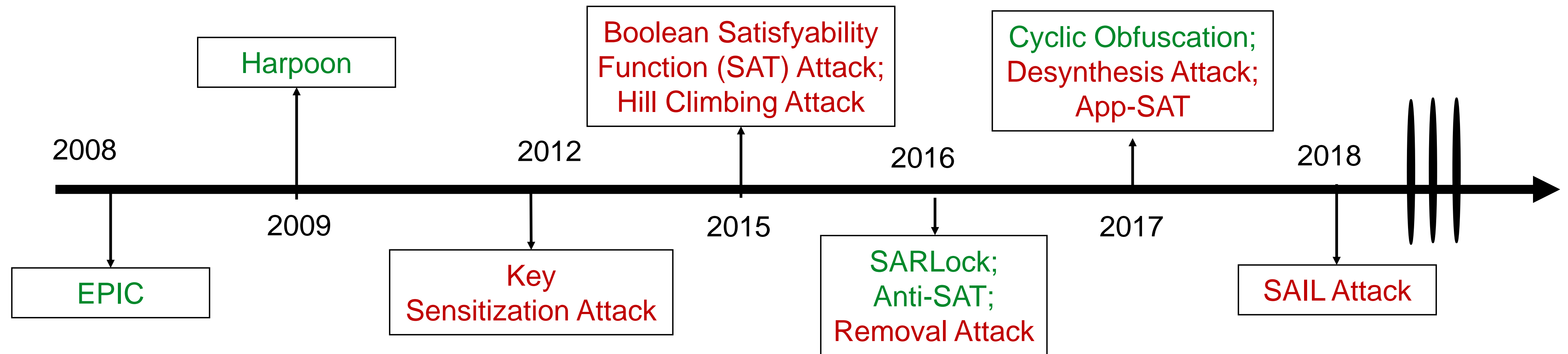
Finite State Machine Locking

# Core-Components of Logic Locking

- Components mandatory for functionality of a logic locked chip



# Time-line for Logic Locking so Far

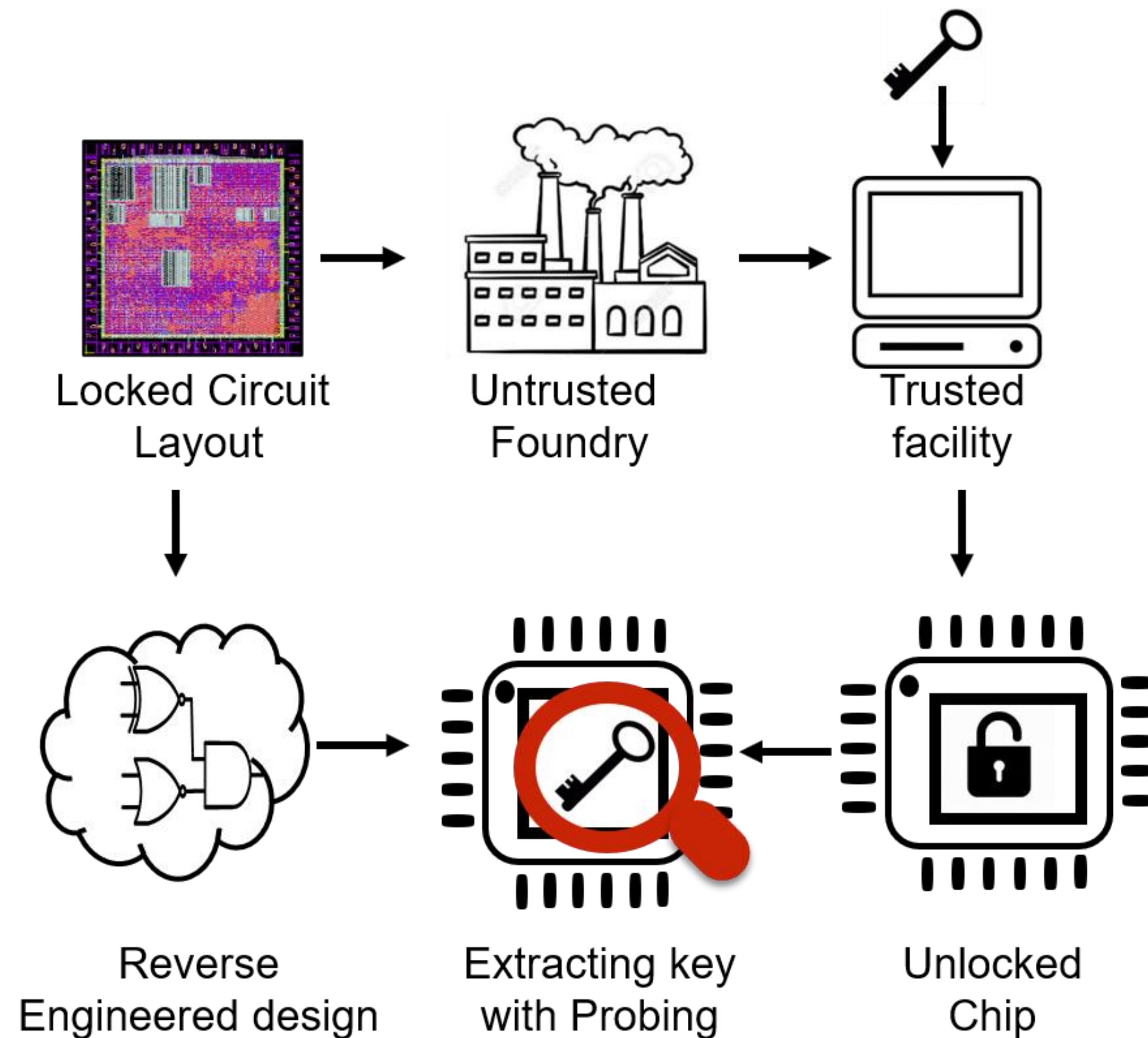


- Adversary → Only untrusted foundry?
- Vulnerable only to algorithm approach?
- What about other capabilities of adversary? → Failure analysis tools



# Threat Model & Potential Adversary

- Threat model is approach exploited by an adversary to access the protected assets, i.e, locking key



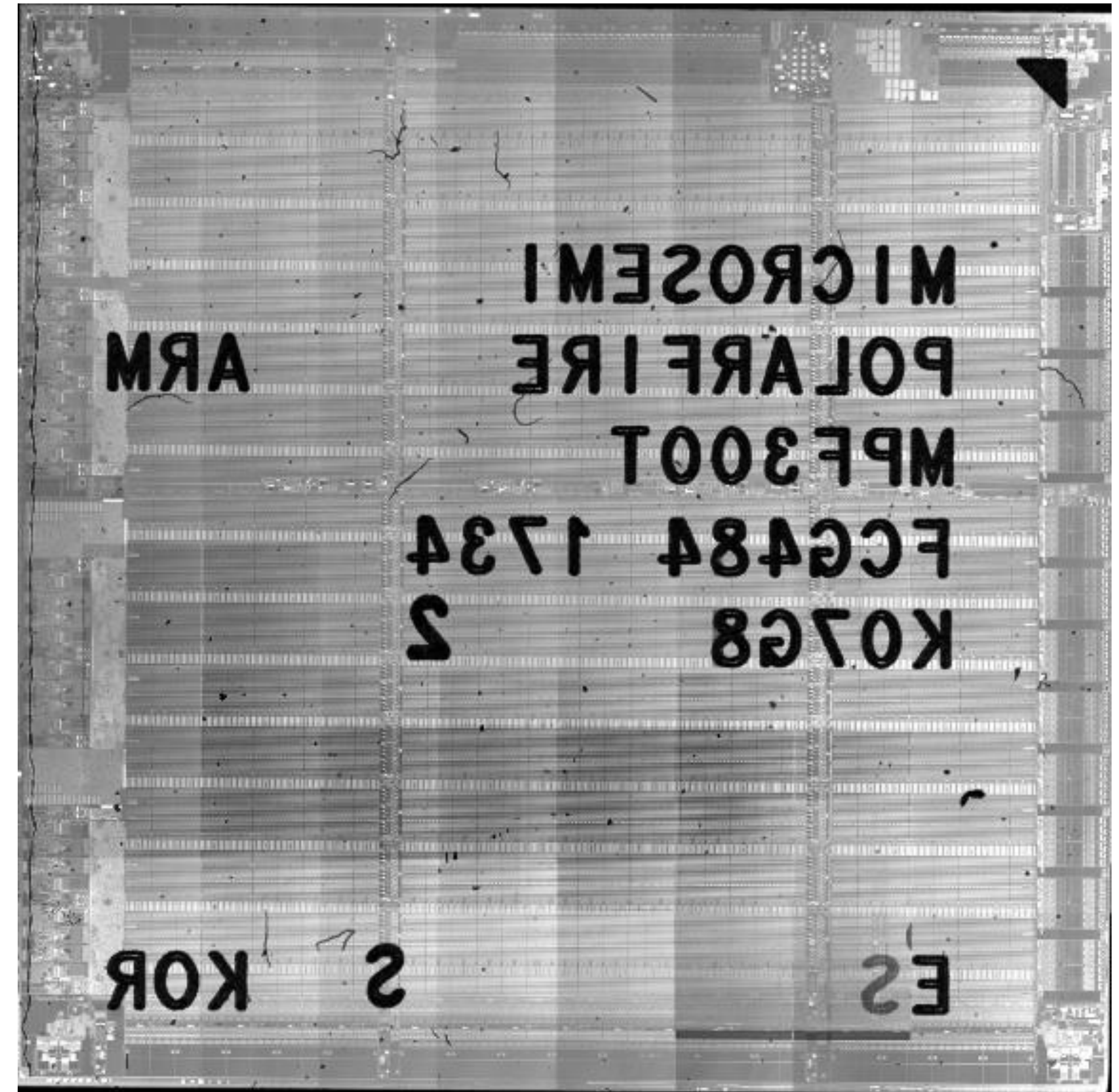
Adversary	Asset Holding
SoC Integrator	1.Soft/Hard IP 2.GDS II file
3 <sup>rd</sup> Design Service Provider	1.IP Design 2.GDS II file
Foundry	1. GDS II file
Assembly and Distributor	1. Unlocked chip
End User	1.Unlocked chip 2.Documentation of chip

**Partial reverse engineering and suitable failure analysis tool is sufficient for attack**

# Case Study –II: Flip-flop Probing

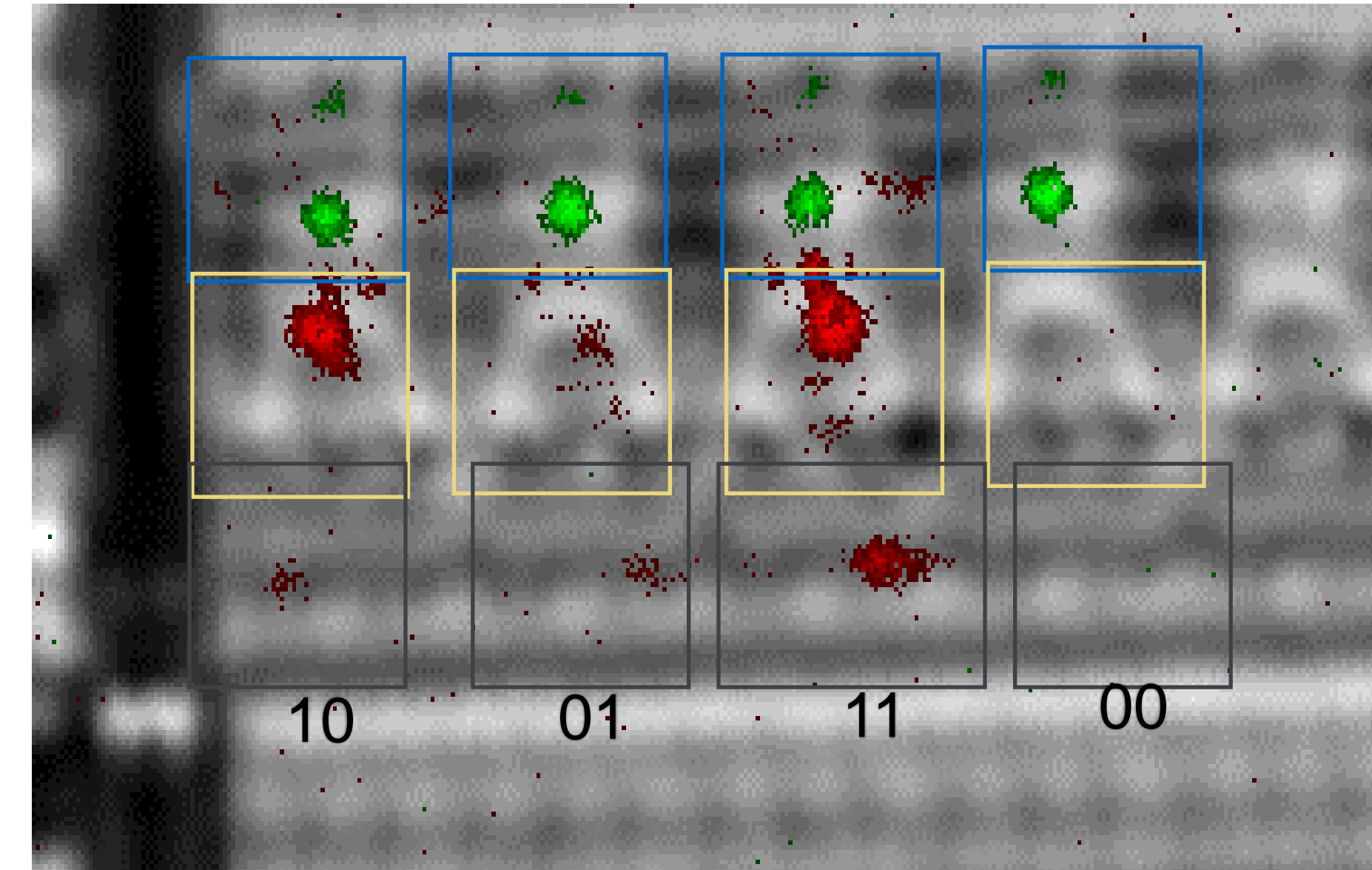
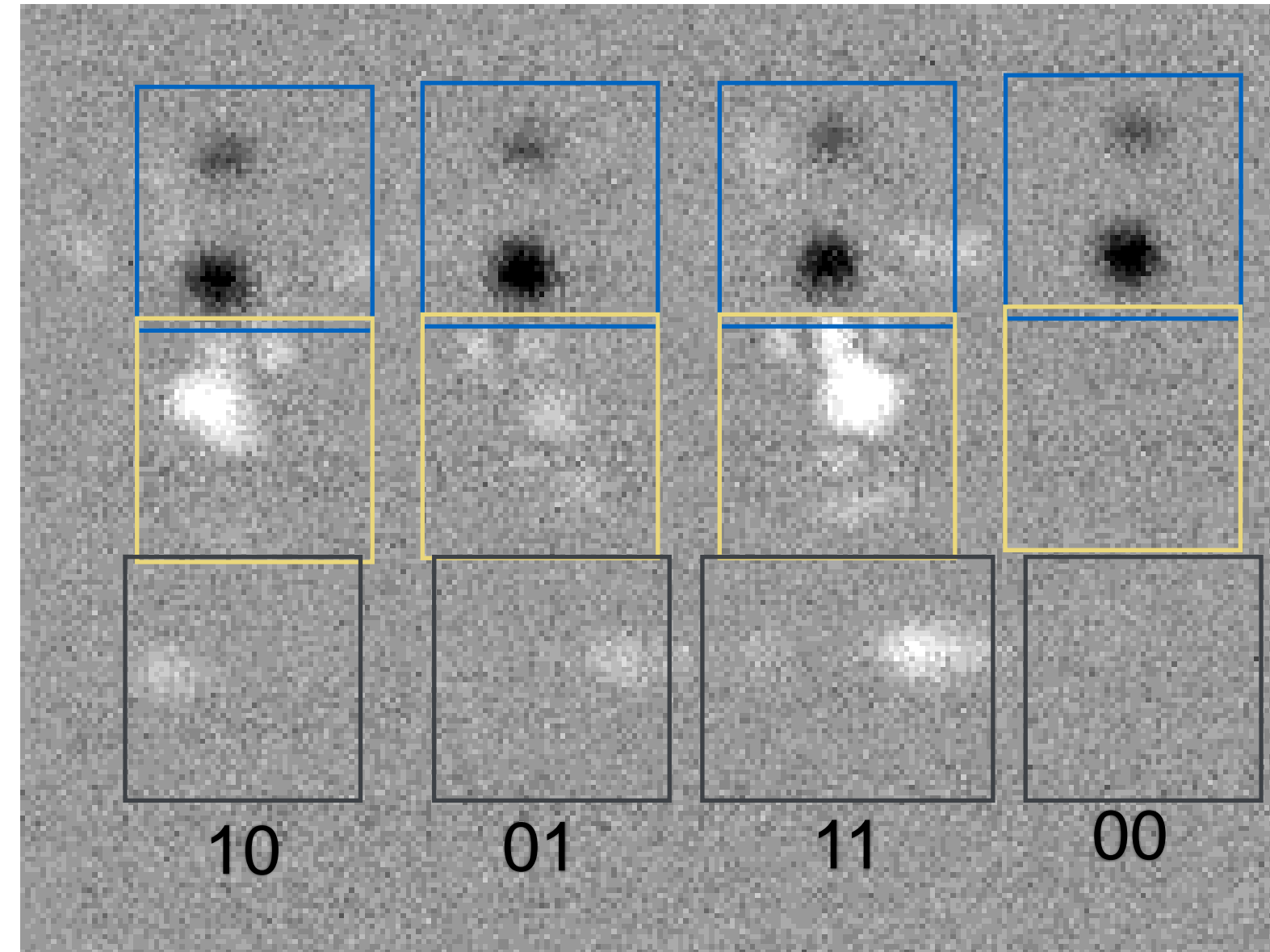
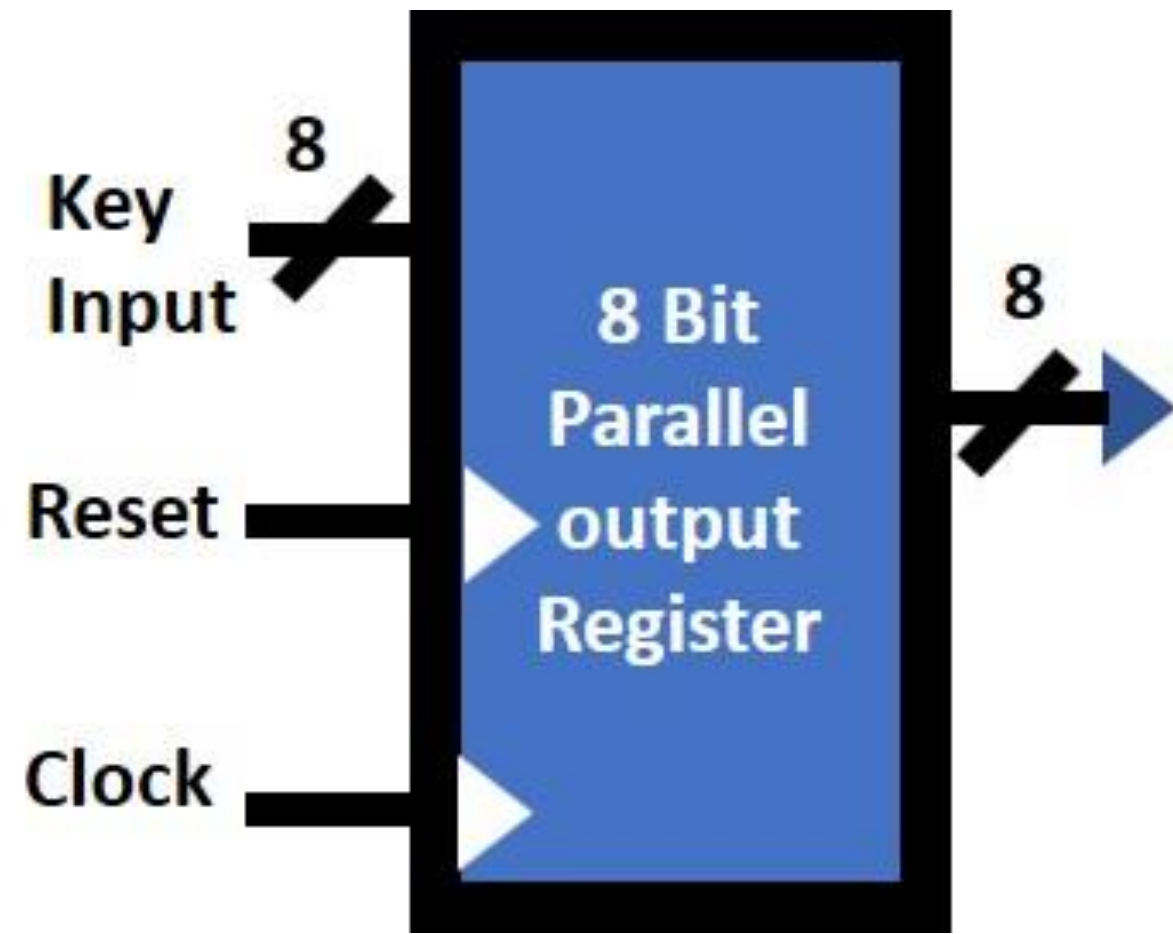


- Avalanche FPGA development board
- 28 nm technology Microsemi MPF300 Polarfire chip



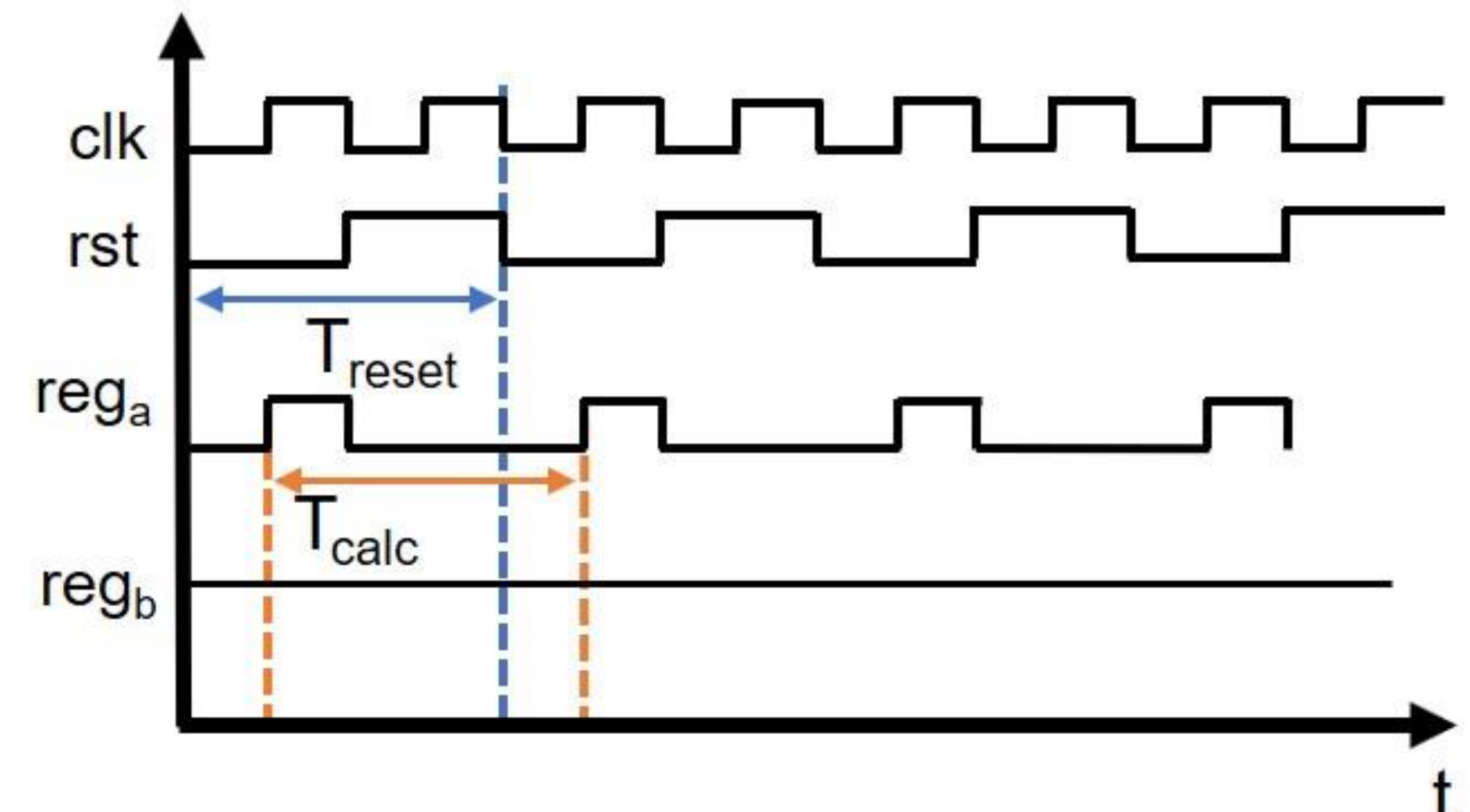
Microsemi die image collected with 1300nm laser

# Reverse Engineering DUT

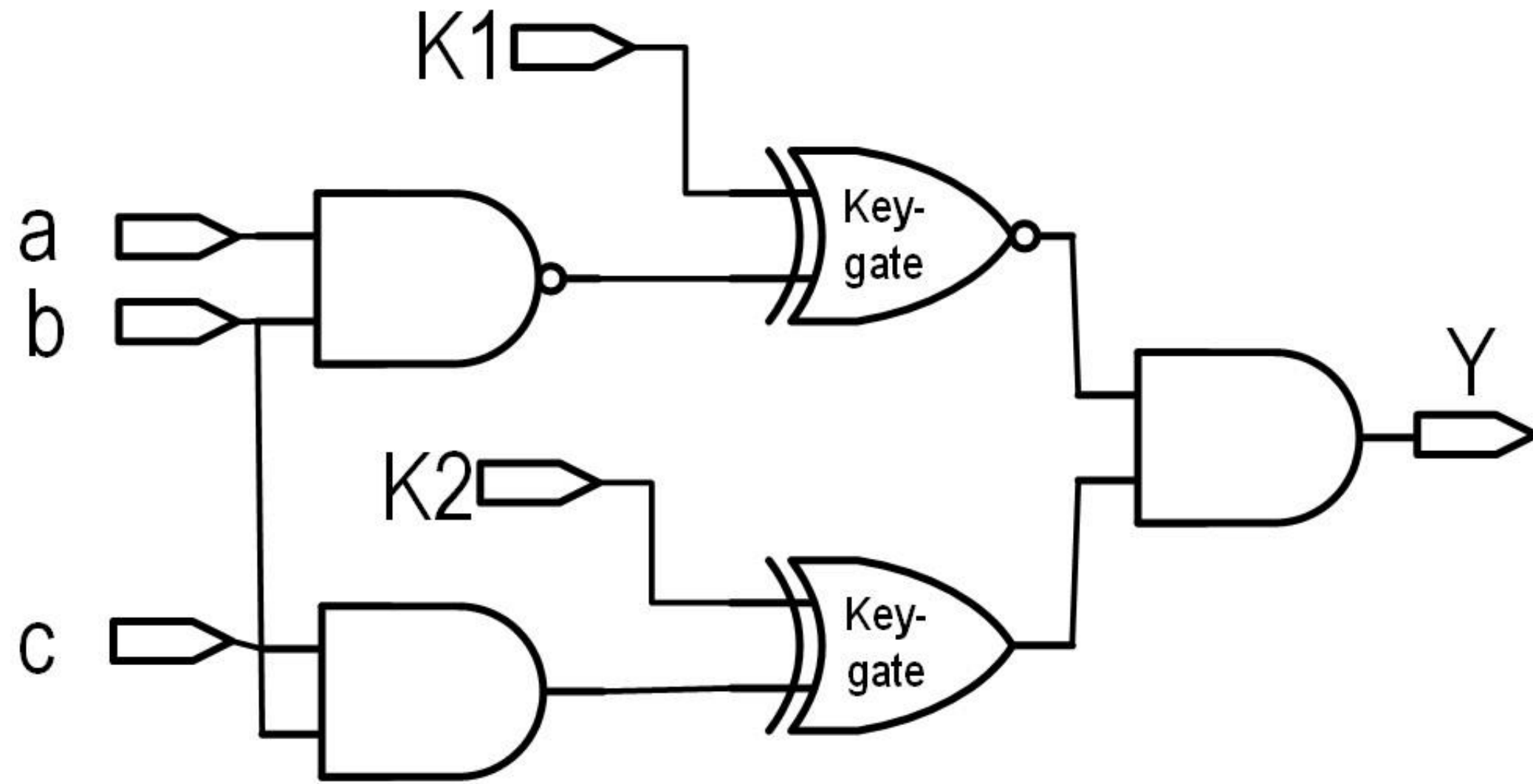


## Probing Registers in DUT

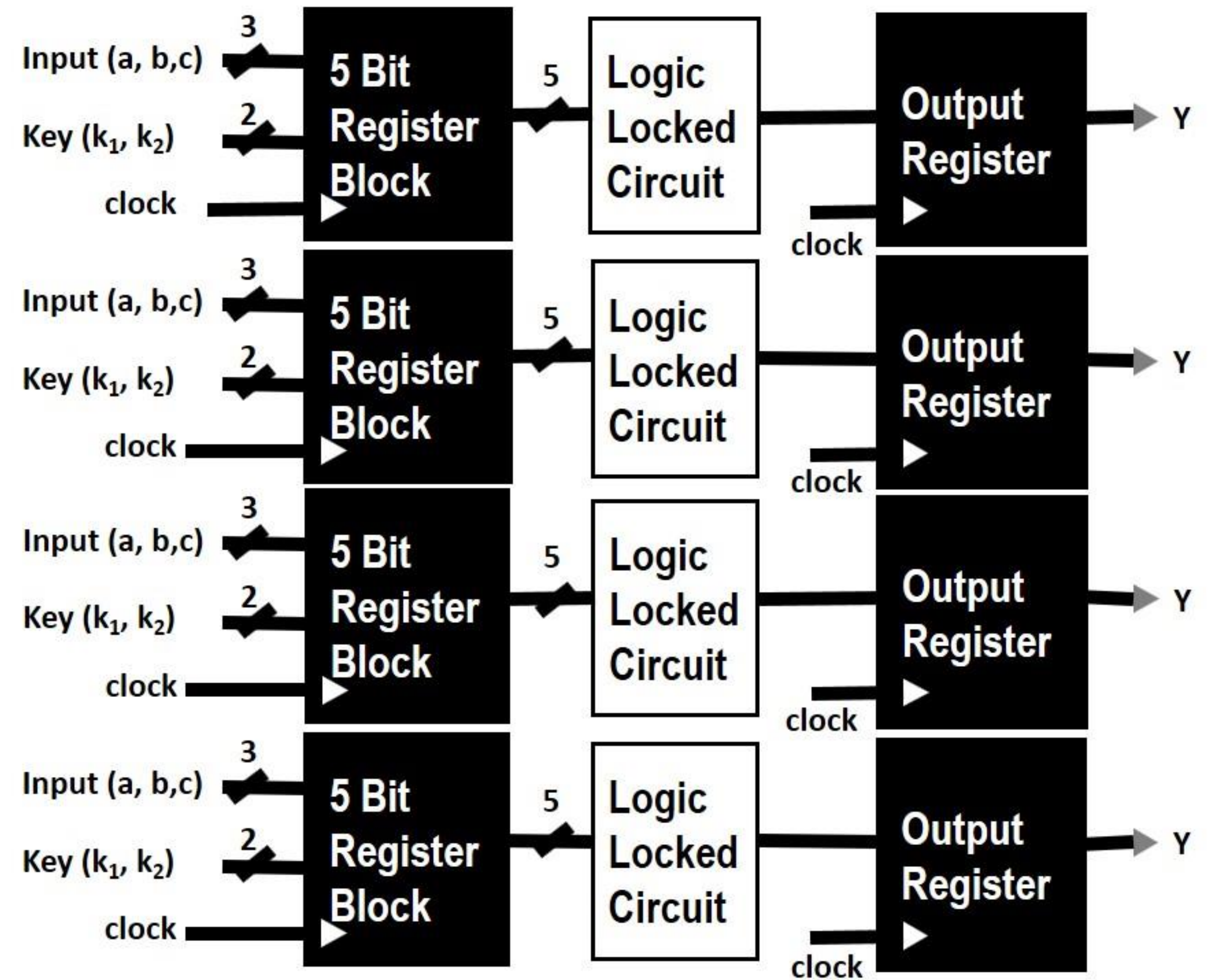
- Activity shows for two different frequency
- White dot corresponds to registers



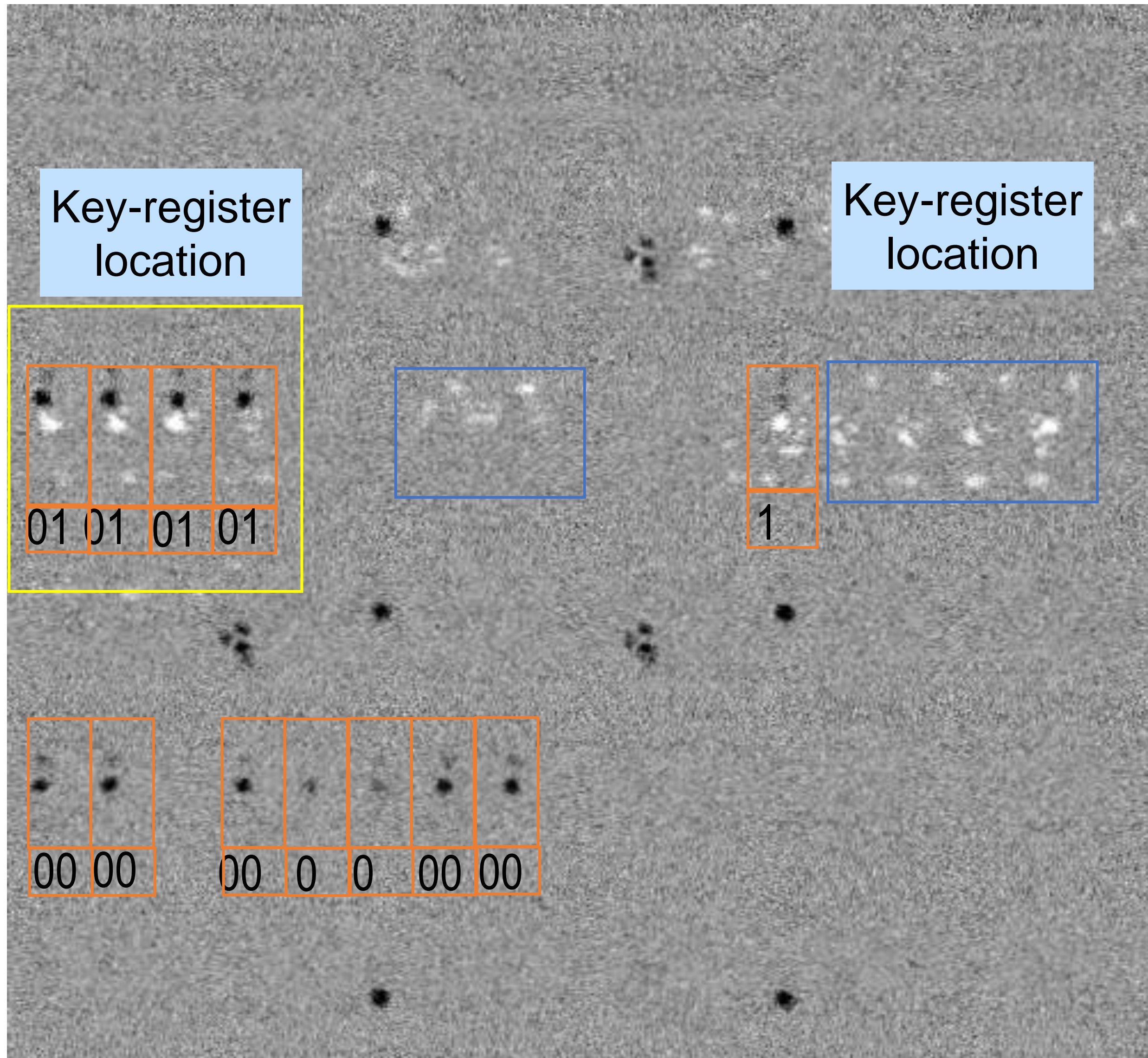
# Proof-of-Concept Implementation



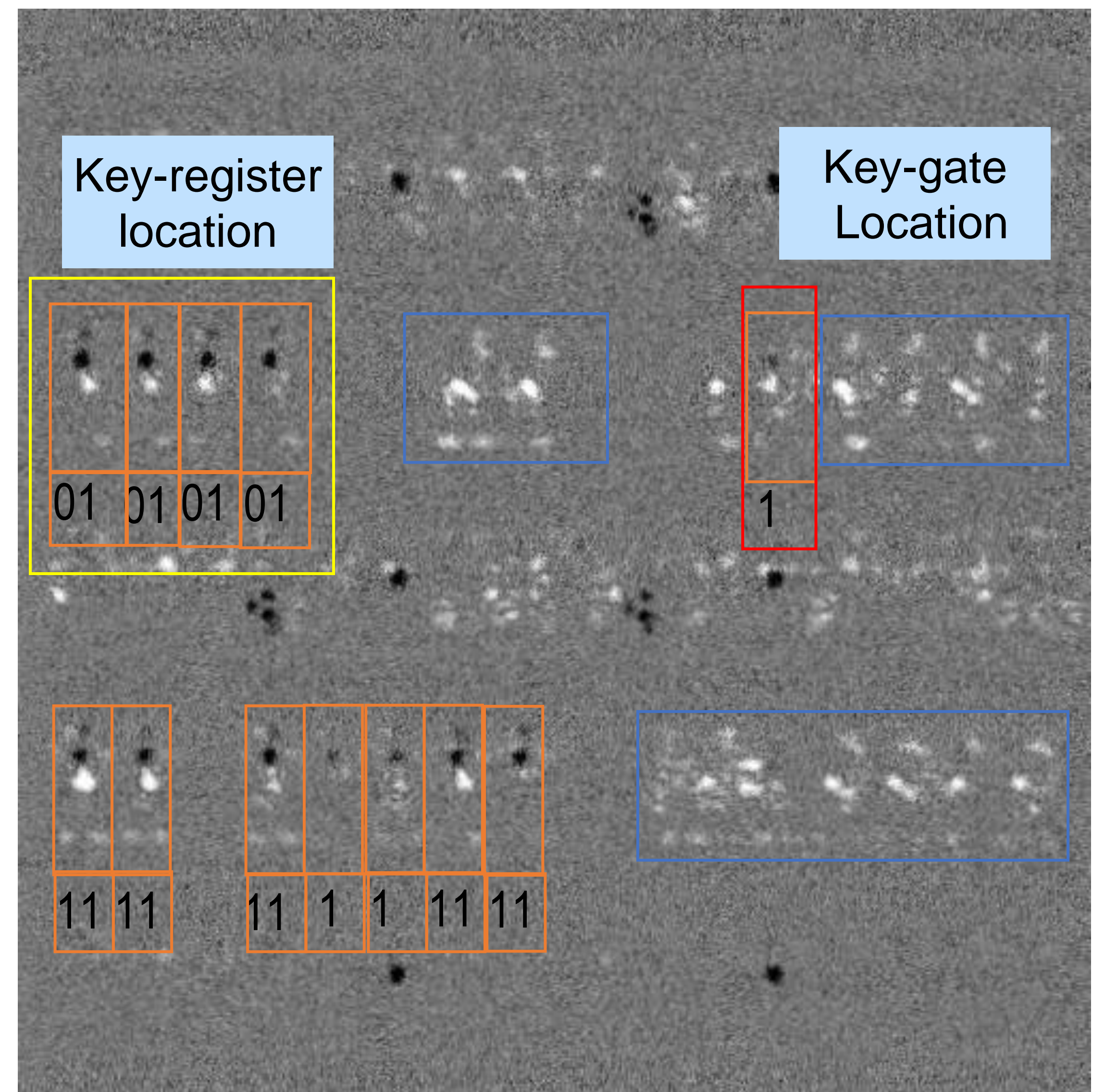
- **K1, k2** → key-input (key-register) → constant value stored
- **a, b, c** → user input (general purpose register) → variable stored value



# Exposing Key-register and Key Value



Register and clock activity when input connected to ground



Register and clock activity when input connected to active

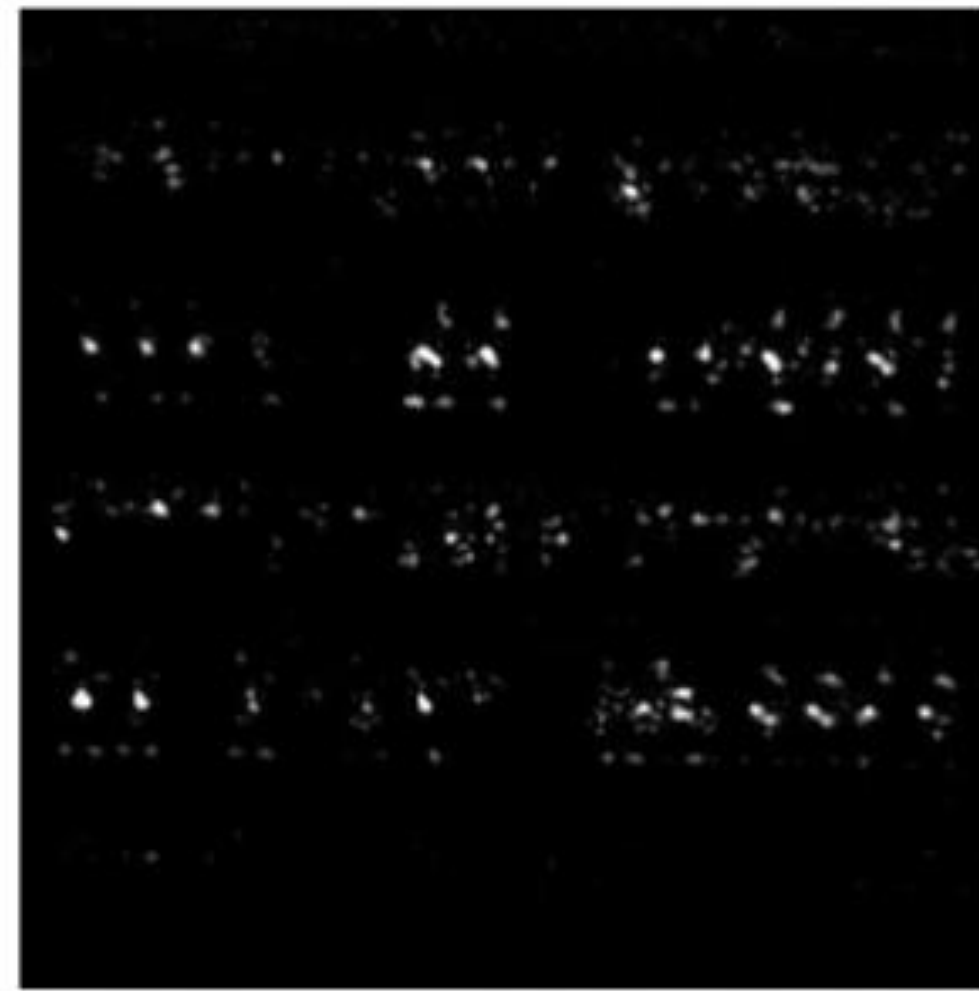


# Exposing Key-register and Key Value

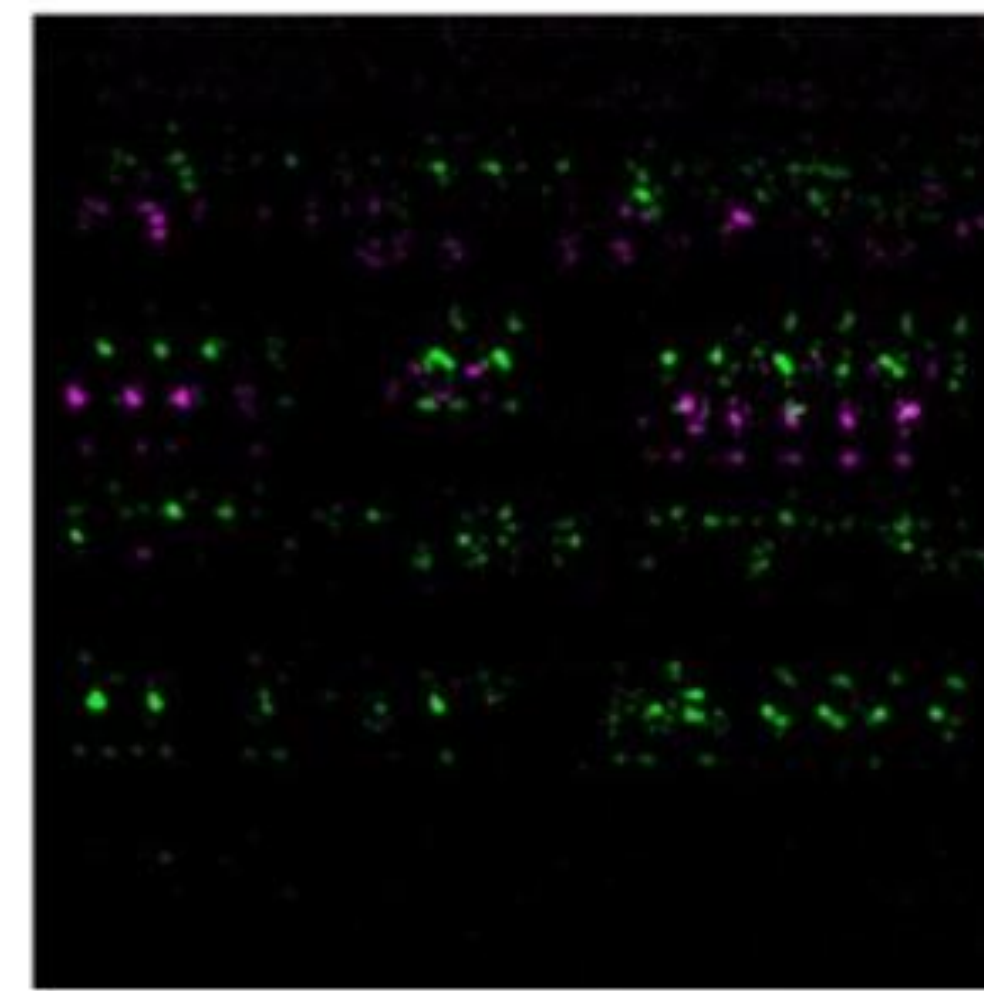
Simple image registration, subtraction, or image co-relation can automate the whole process



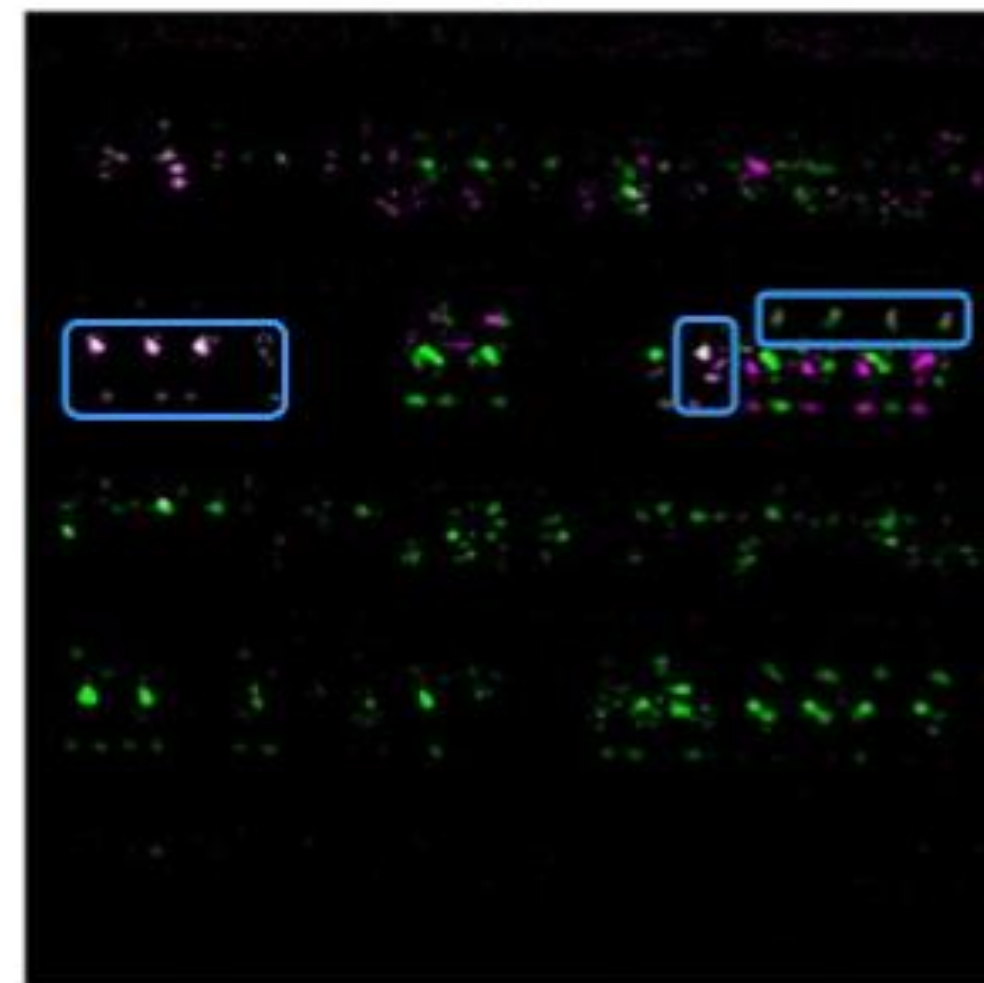
(a)



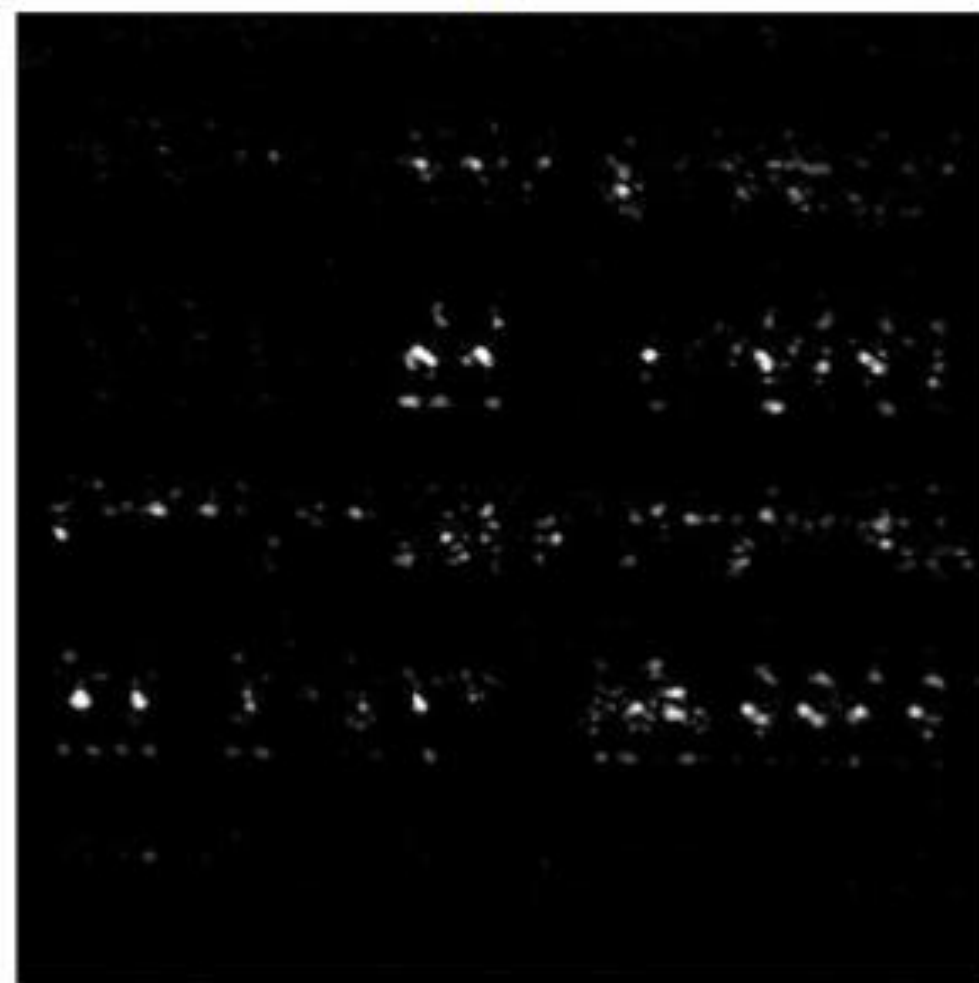
(b)



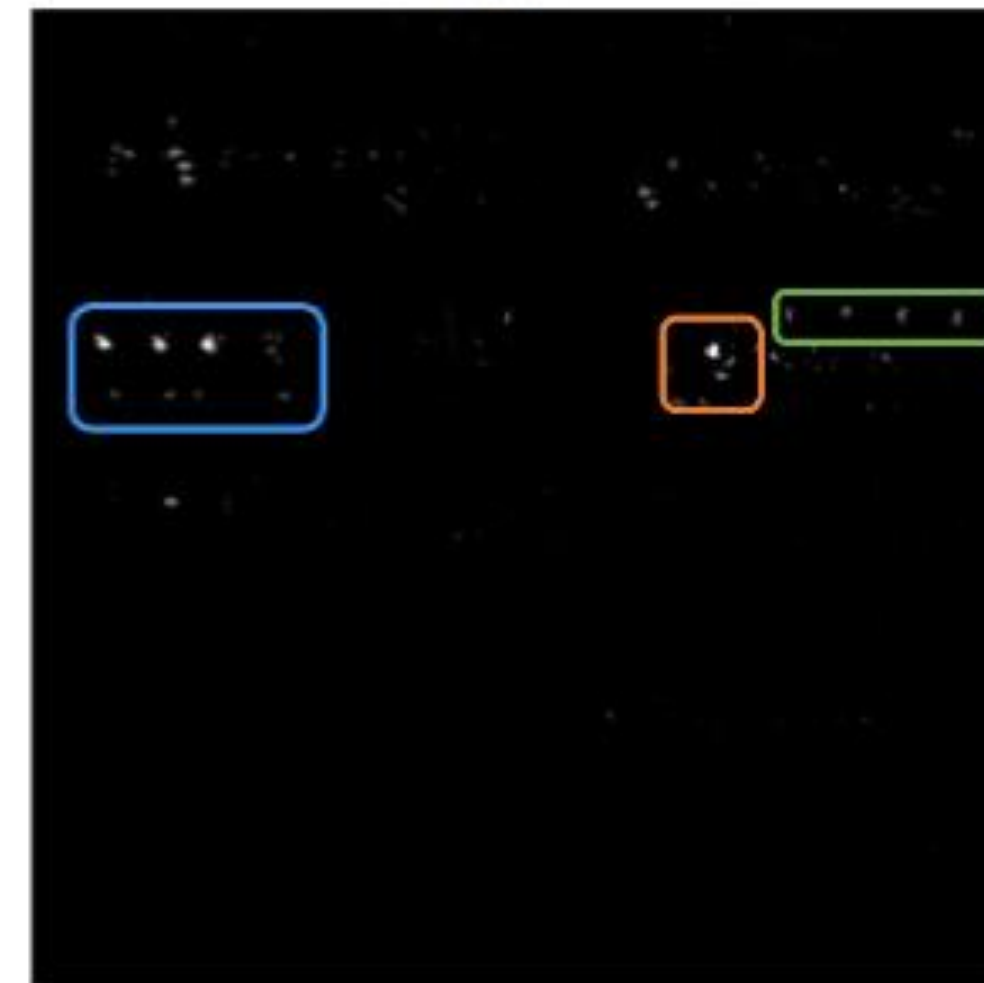
(c)



(d)



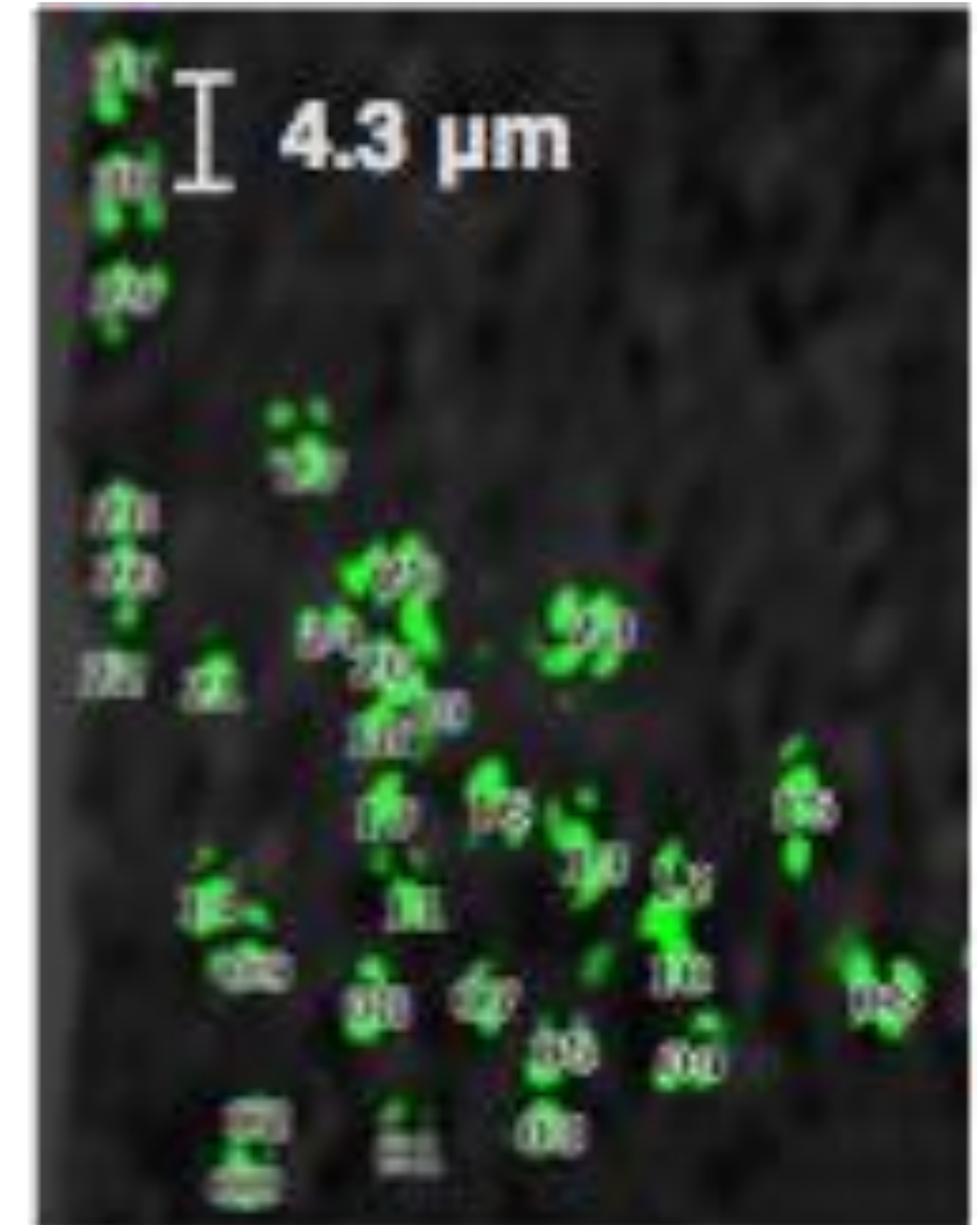
(e)



(f)

# Technology Size vs. Optical Resolution

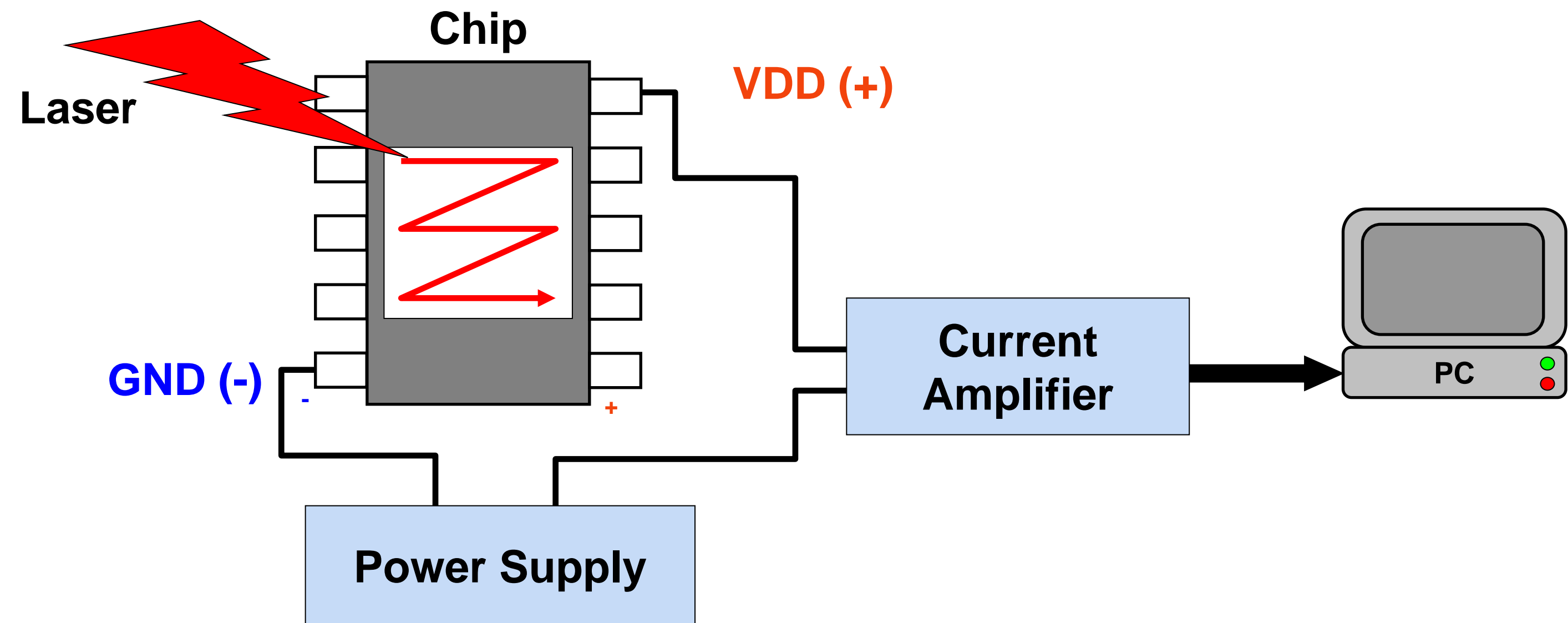
- The real limiting factor for an attacker is not the technology size, but the distance of a probing location of interest to the next location, (Optical Resolution and spot size)
- the separation between locations carrying different streams of data can actually be much larger than the technology size.



# Laser Stimulation

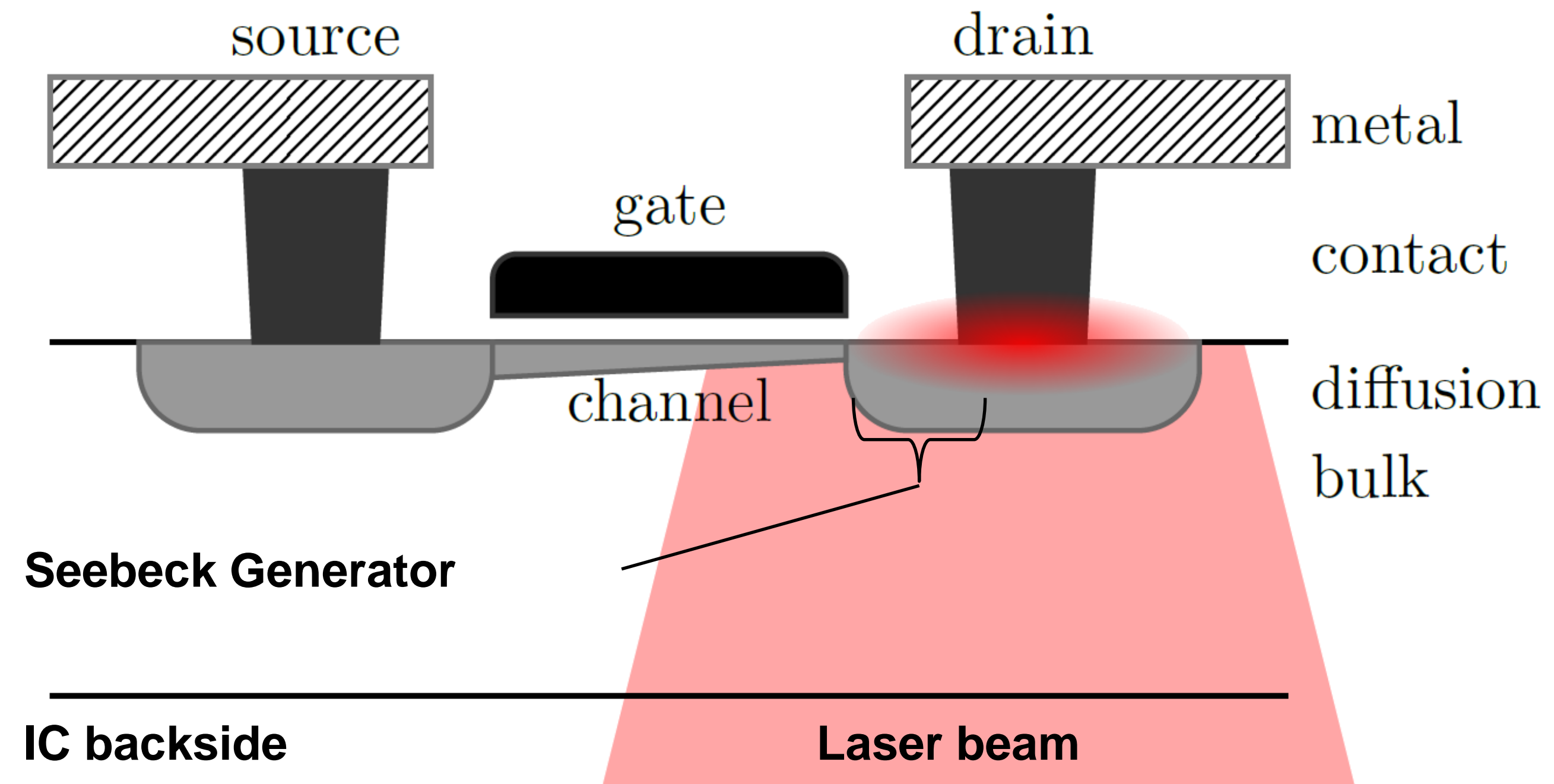
# Thermal Laser Stimulation (OBIRCH)

- The chip is scanned with a  $1.3 \mu\text{m}$  laser beam from the backside
- The current changes in response to the local thermal stimulations
- Measured current is monitored by a current amplifier  $\gg$  a proportional analog voltage is generated
- Analog voltage is fed into image acquisition hardware while scanning the laser

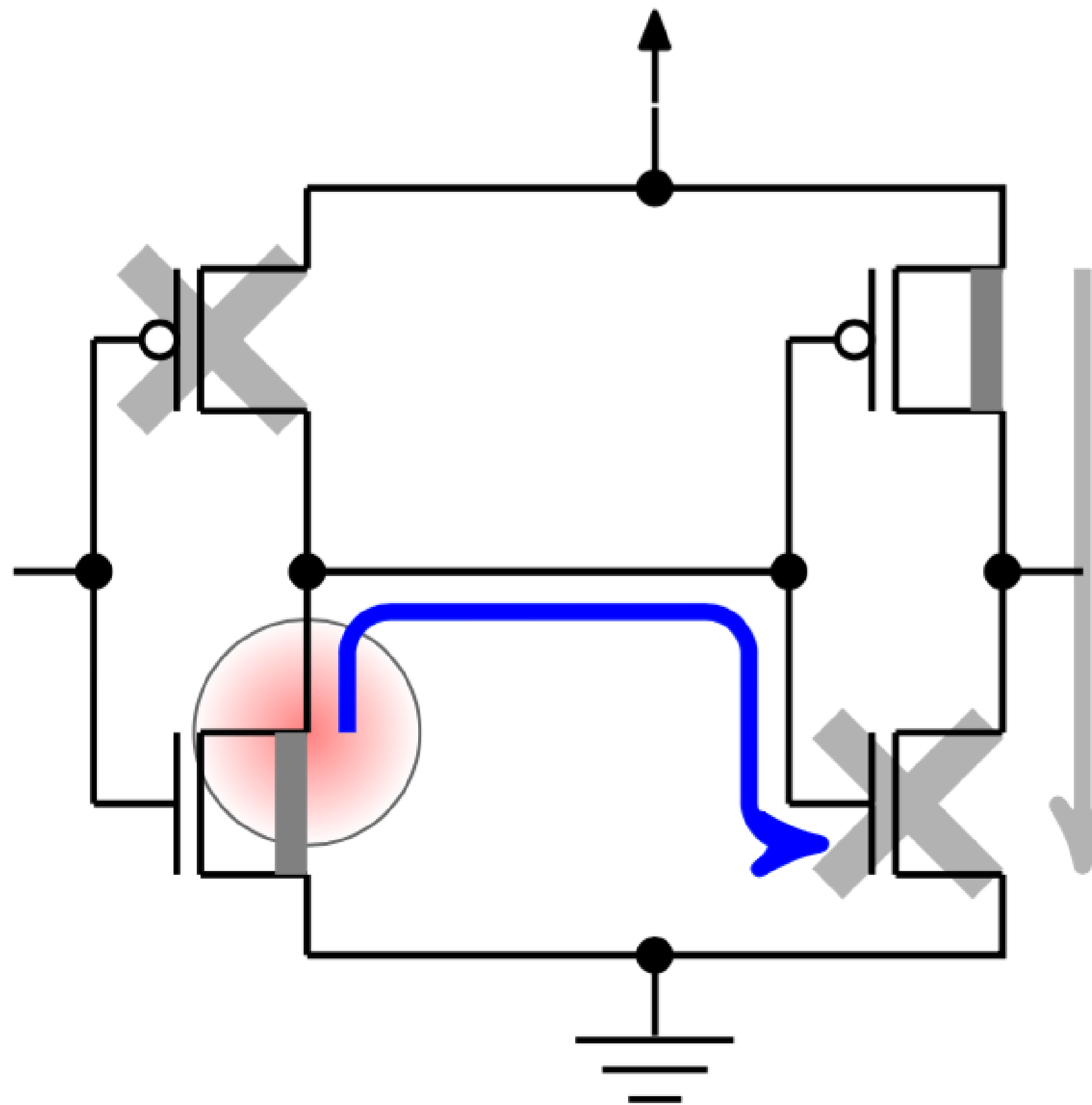


# SRAM readout using TLS (1)

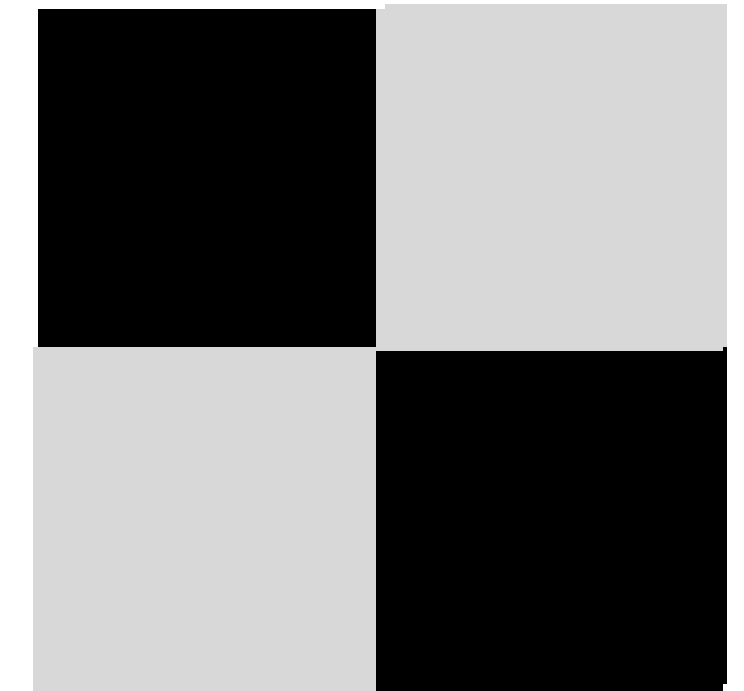
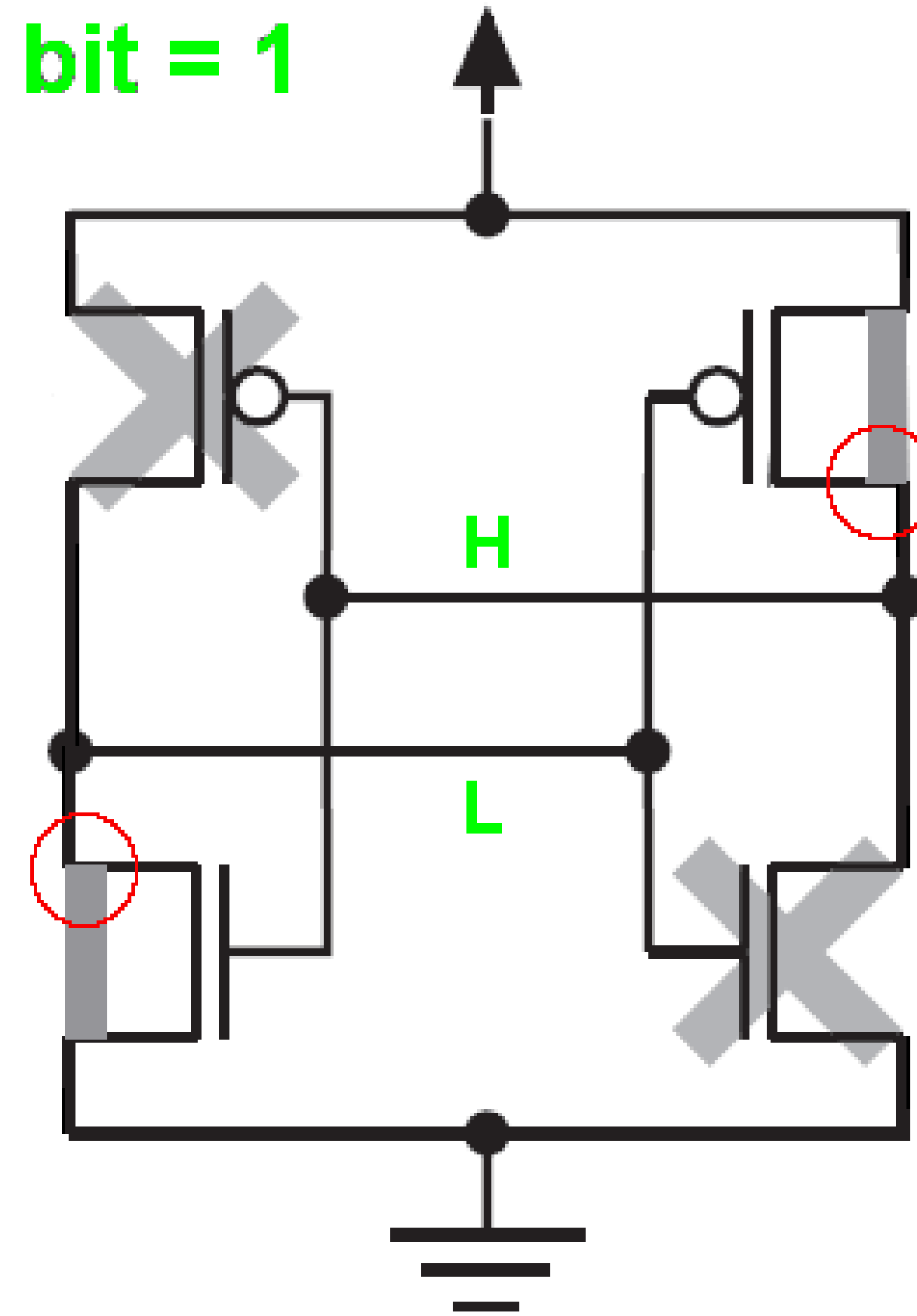
- Thermal stimulation leads to thermal gradient at the source/drain of the transistors
- Different materials lead to Seebeck voltage generation



# SRAM readout using TLS (2)



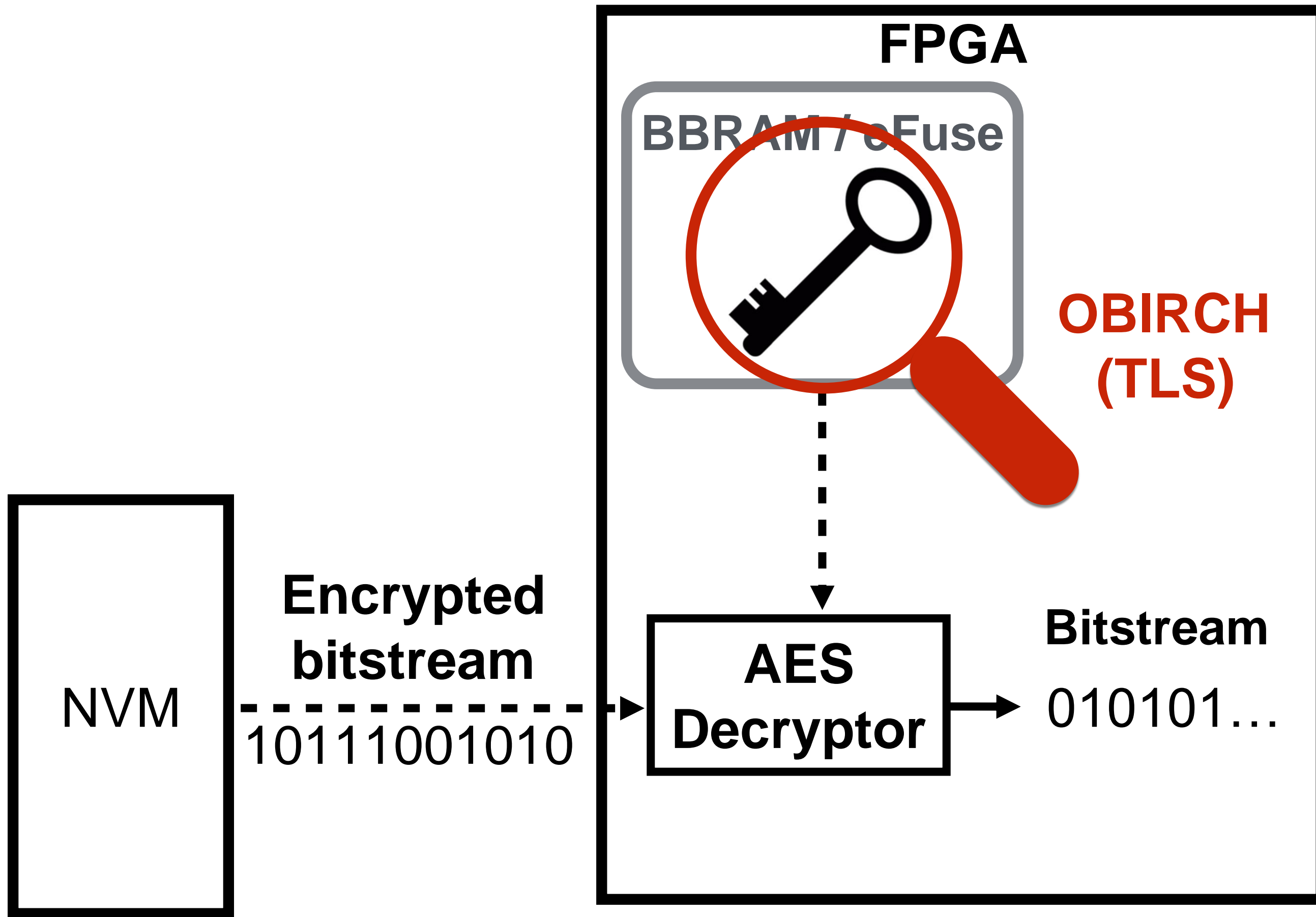
bit = 1



- The Seebeck voltage changes current flow through the “off” transistors >> leakage current increases

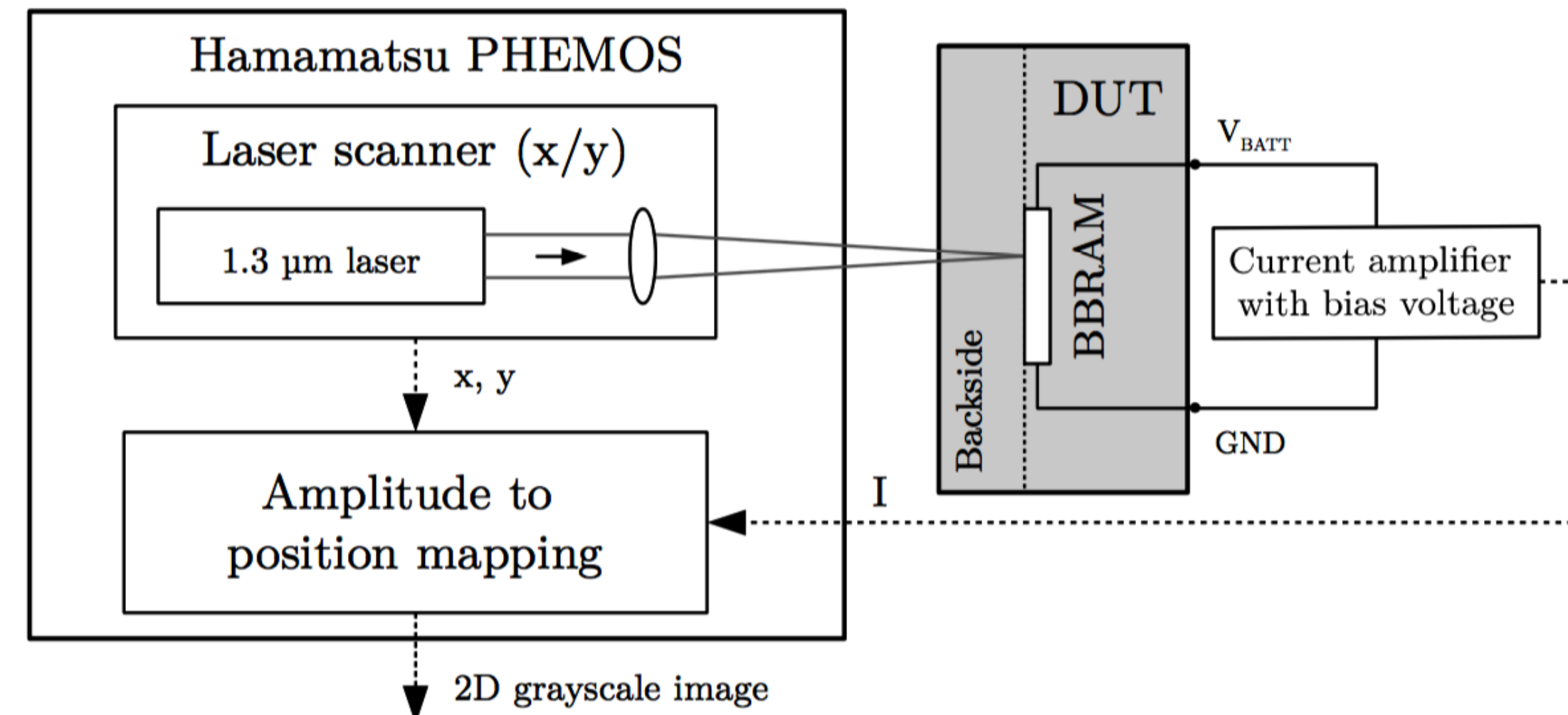
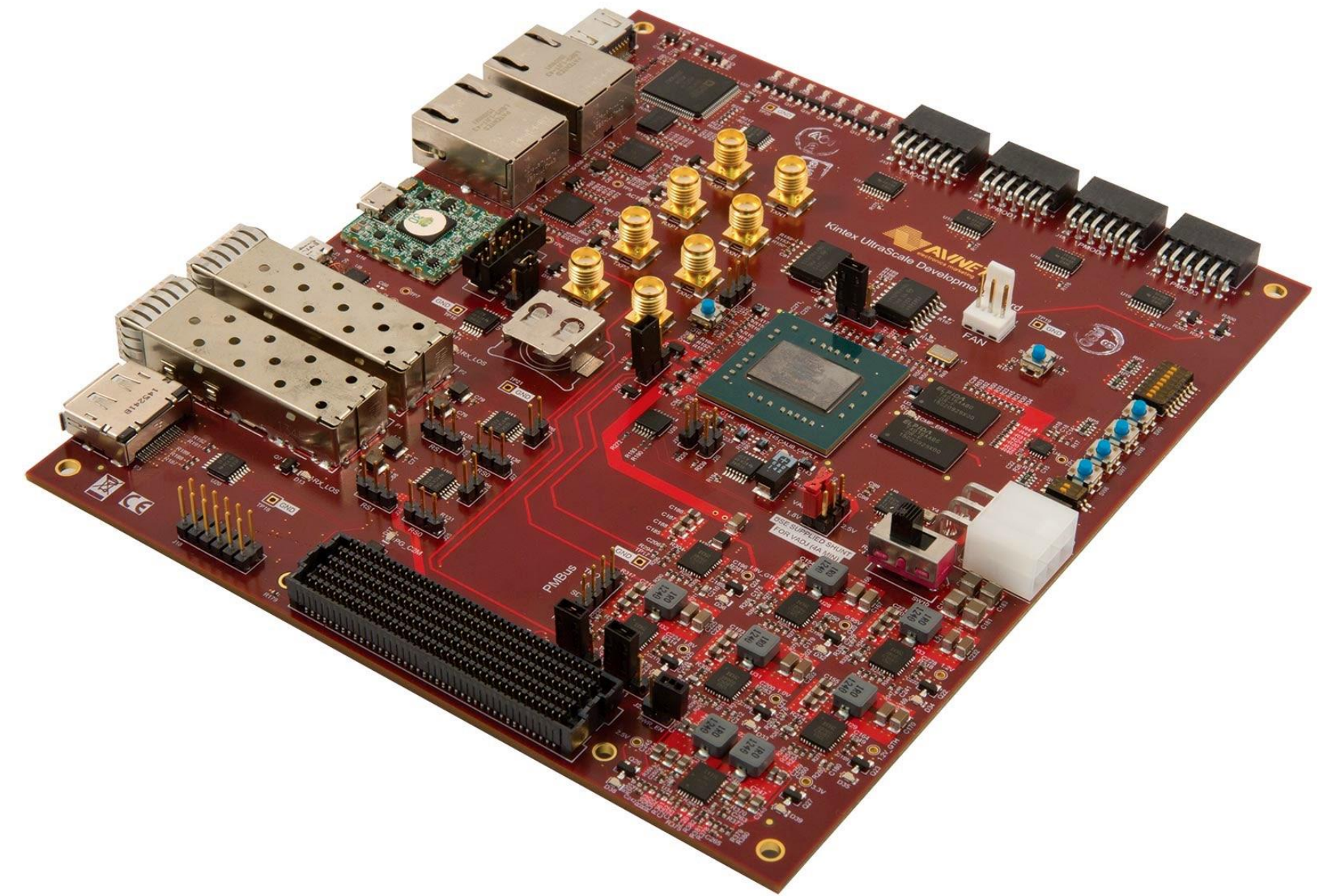
- Reaction of different areas of SRAM cells to TLS, depending on the stored value

# Key Extraction



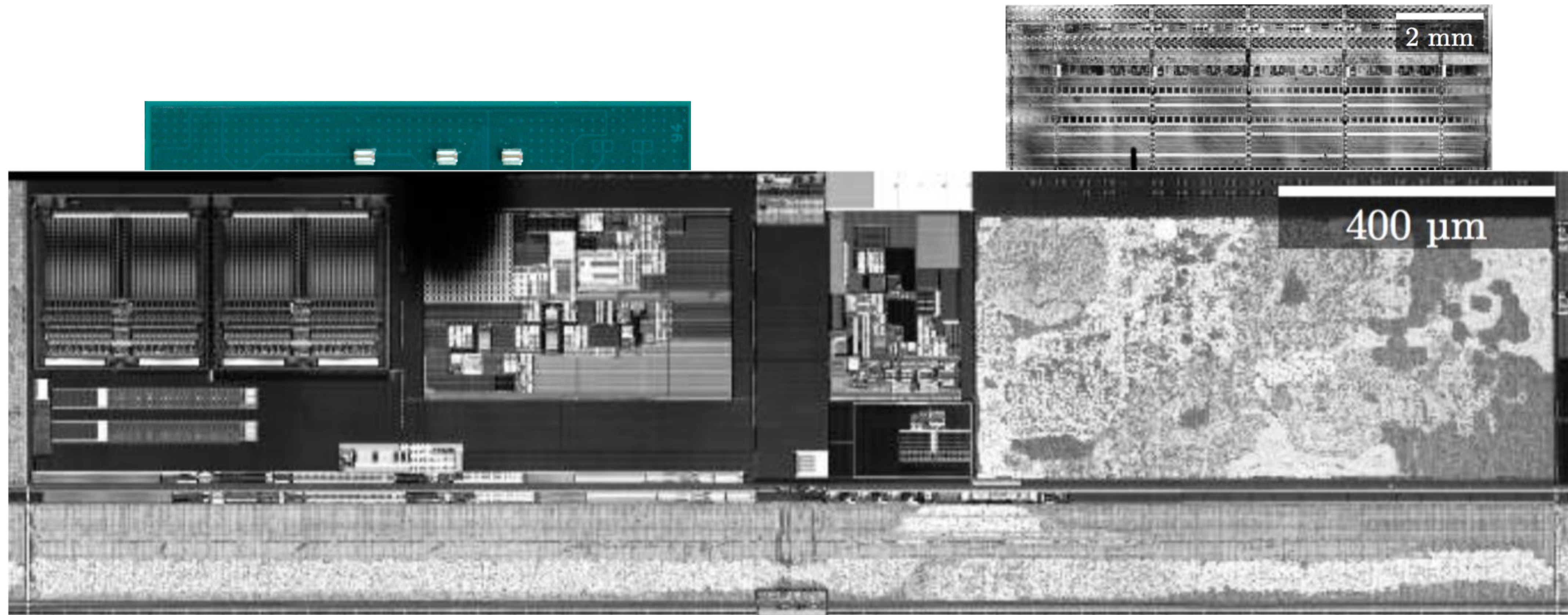
Lohrke, H., Tajik, S., Boit, C., & Seifert, J. P. "Key Extraction Using Thermal Laser Stimulation: A Case Study on Xilinx Ultrascale FPGAs," accepted for CHES 2018

- **Device under Test (DUT):** Avnet Kintex UltraScale Development Board
  - Chip's technology: 20 nm
  - No chip preparation (e.g., depackaging, silicon polishing, etc.) required
- **Optical Setup:** Hamamatsu PHEMOS-1000
  - Laser wavelengths: 1.1 and 1.3  $\mu\text{m}$
  - Laser spot size: approximately 1  $\mu\text{m}$





# Localizing the Configuration Logic



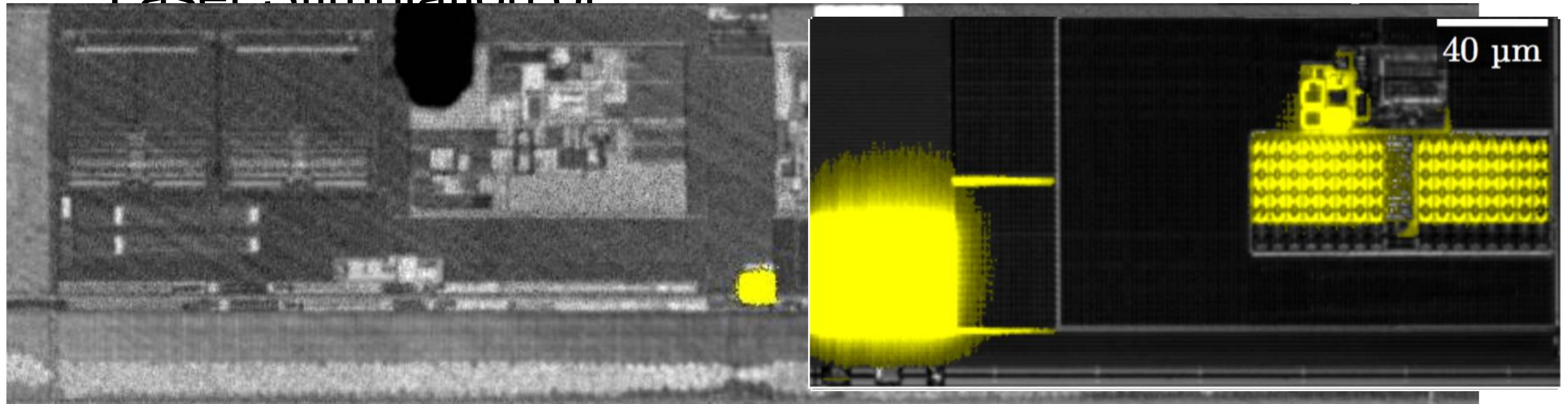
Xilinx Kintex  
UltraScale in flip chip  
package

Configuration Logic

Image acquisition with a laser  
scanning microscope

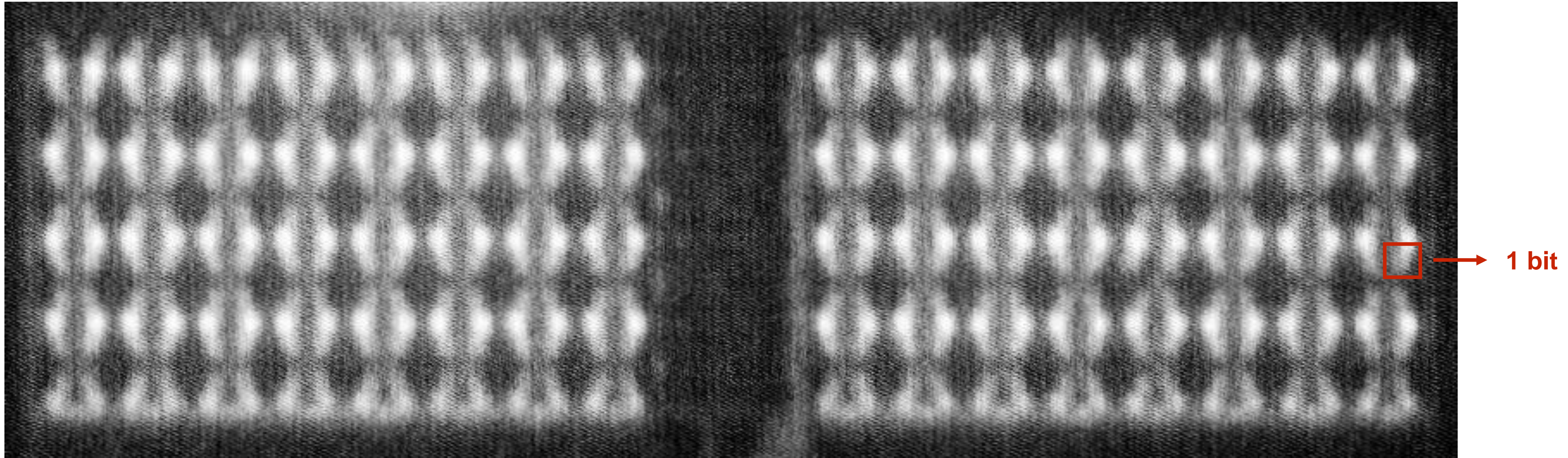
# Localizing BBRAM using Laser Stimulation

Laser Stimulation of



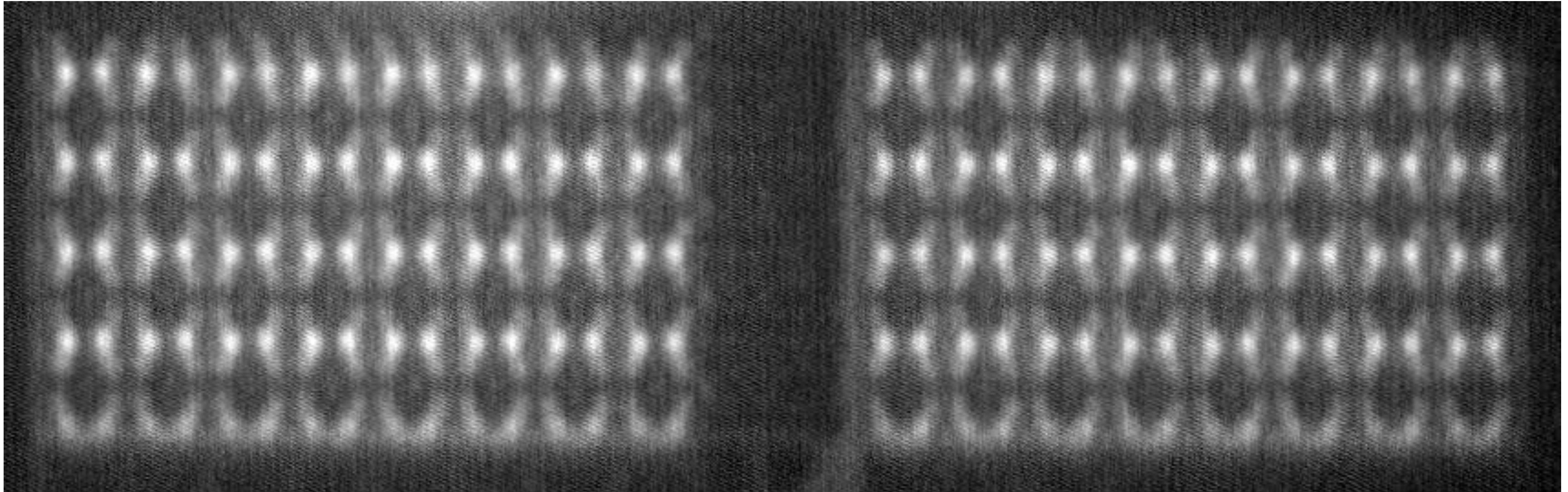
*In all experiments!*

# Localizing the key bits in BBRAM by TLS



Set 255 bits to “0” and one bit to “1”.  
Shifting the bit “1” eight times by one bit

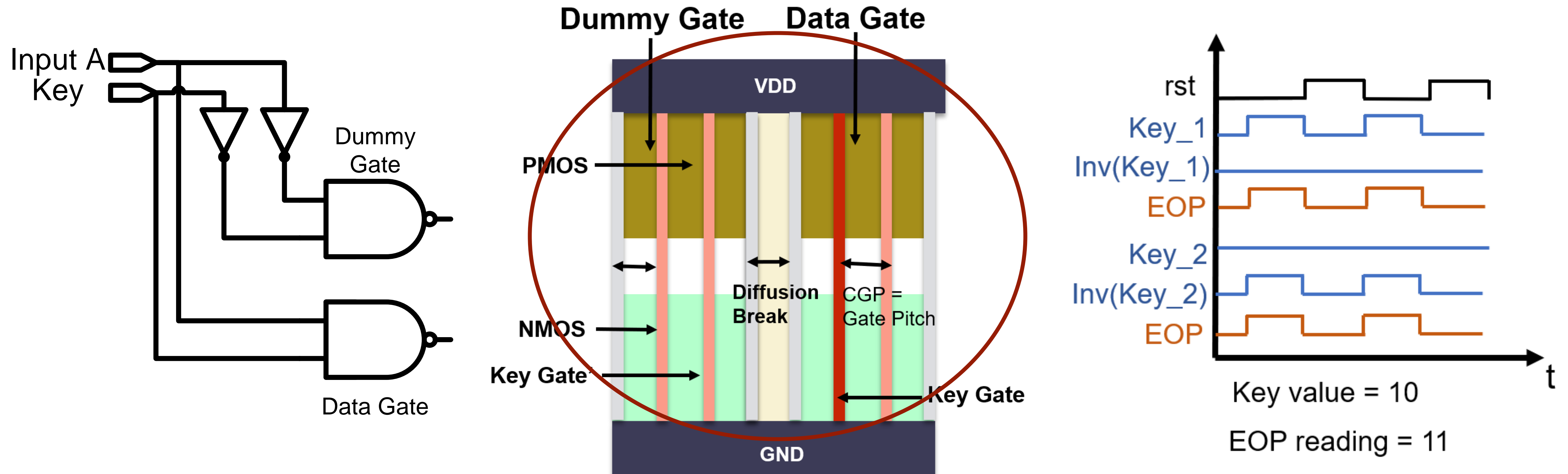
# Localizing the key bits in BBRAM



Set all 256 bits to “1” and reset all bits to “0” again.

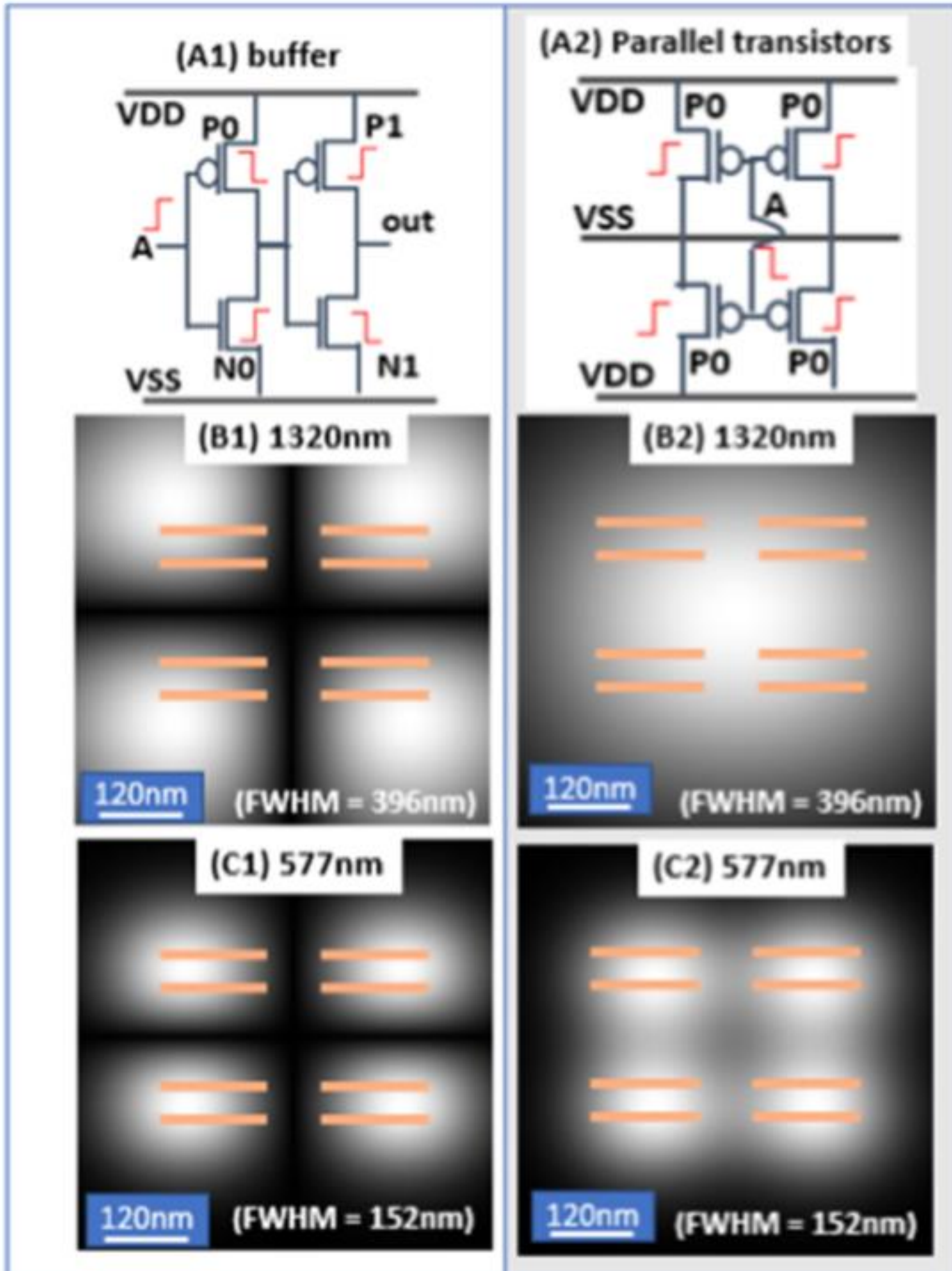
# Countermeasures against Optical Attacks

# Circuit Based Solution: Dummy Gate



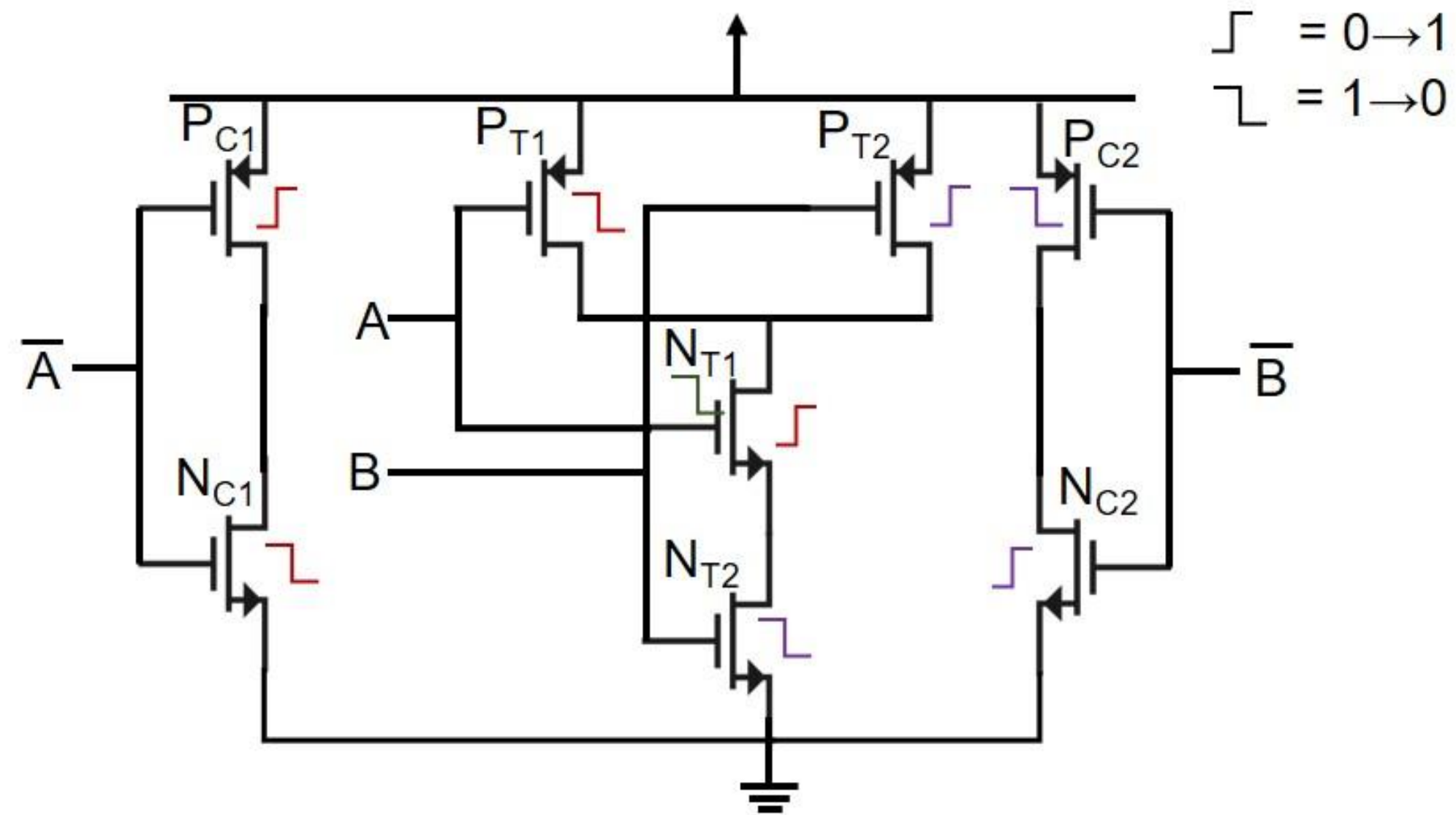
- In physical layout, dummy gate and data gate will be placed at lower distance than optical resolution
- Necessary to localize exact transistor connected to key → security by maximizing

# Concealing Gate: EOFM Protection



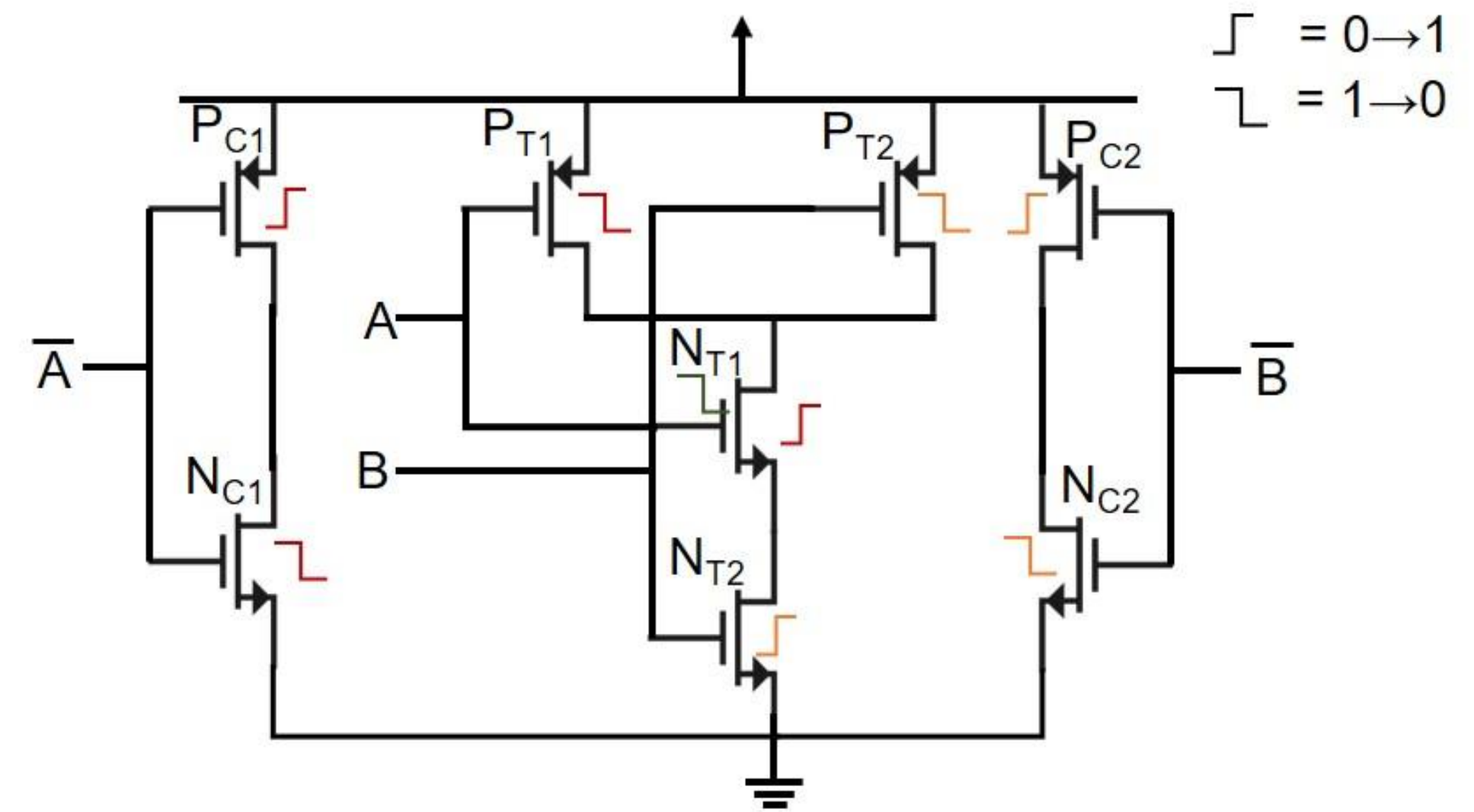
- Two transistors operating at same frequency and switching at same direction, i.e., either 1→0 or vice versa, is difficult to differentiate. (see A2 implementation)
- Two transistors operating at same frequency but with opposite switching direction will be easy to distinguish, though the transistors may be placed lower than optical resolution distance. (see A1 implementation)

# Concealing Gate: EOFM Protection



Concealing gate for input A      Target gate      Concealing gate for input B

Fig. A



Concealing gate for input A      Target gate      Concealing gate for input B

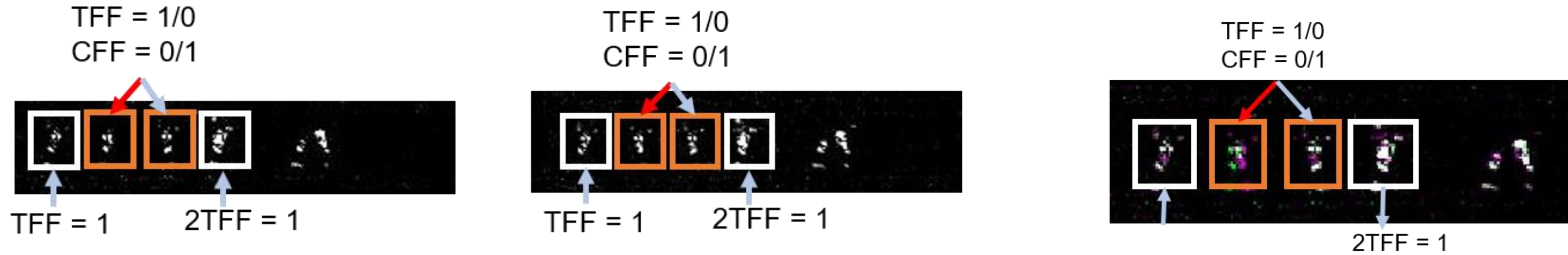
Fig. B

- $P_{C1}$  mask  $P_{T1}$  activity by merging the edges of  $P_{T2}$  (Fig A) or  $P_{C2}$ (Fig. B). If distance between  $P_{C1}$  and  $P_{C2}$  is less than optical resolution, the  $PT1$  transistor can be assumed to be protected.

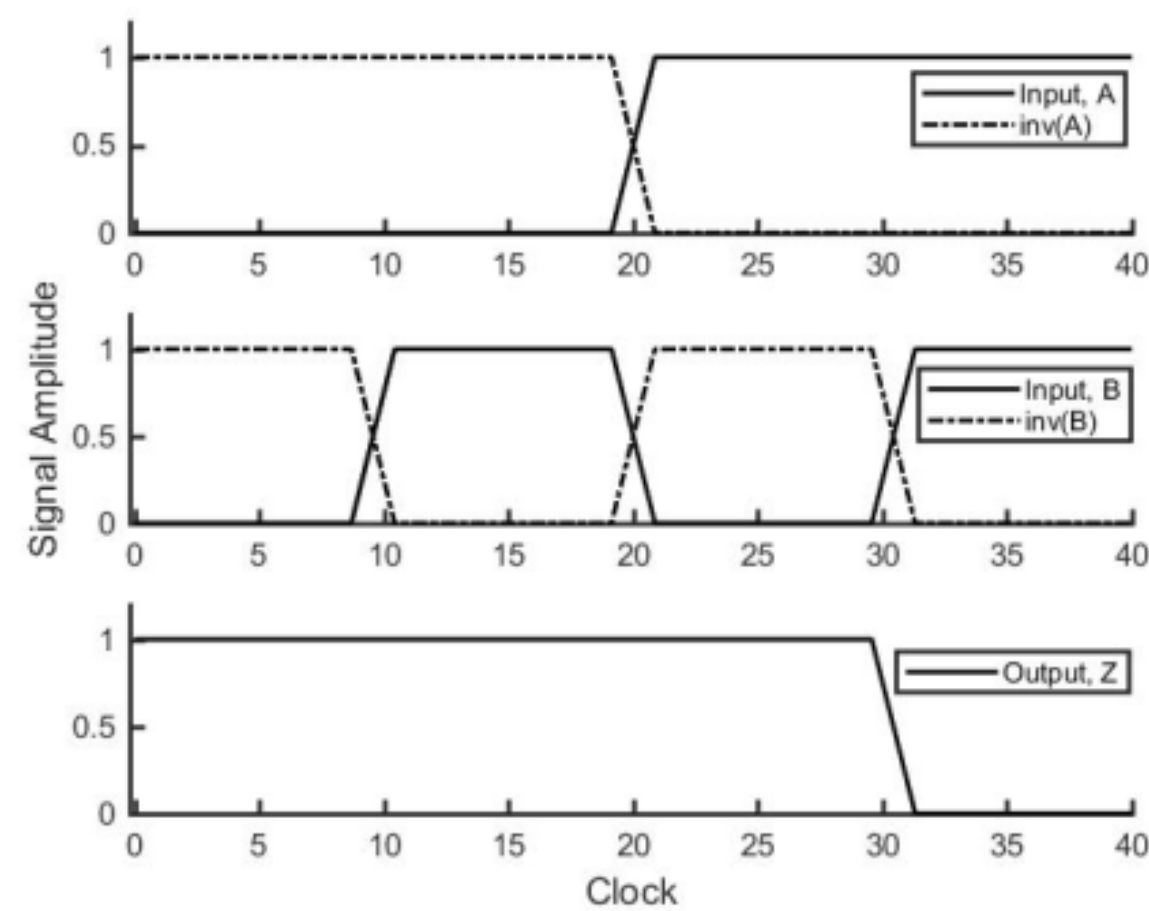


# Concealing Gate: EOFM/EOP Protection

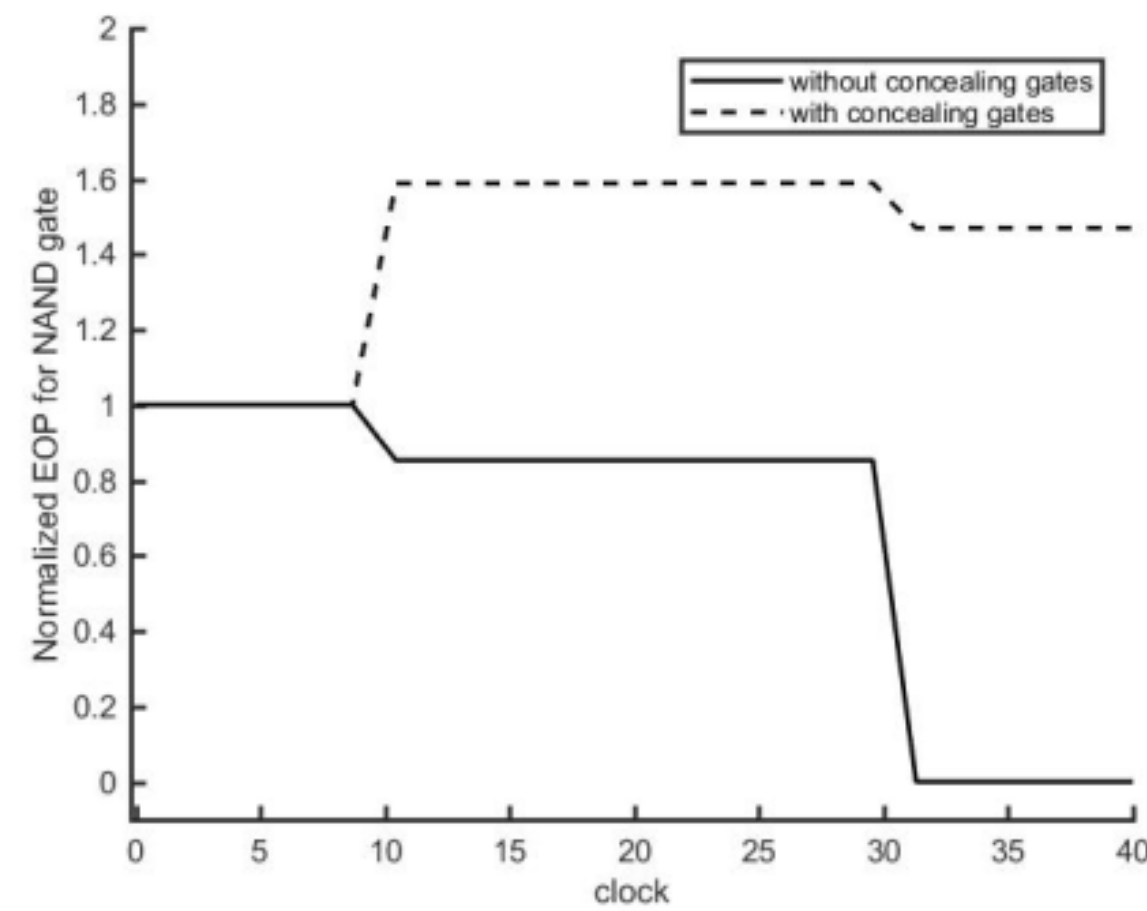
EOFM Data with Concealing Gate



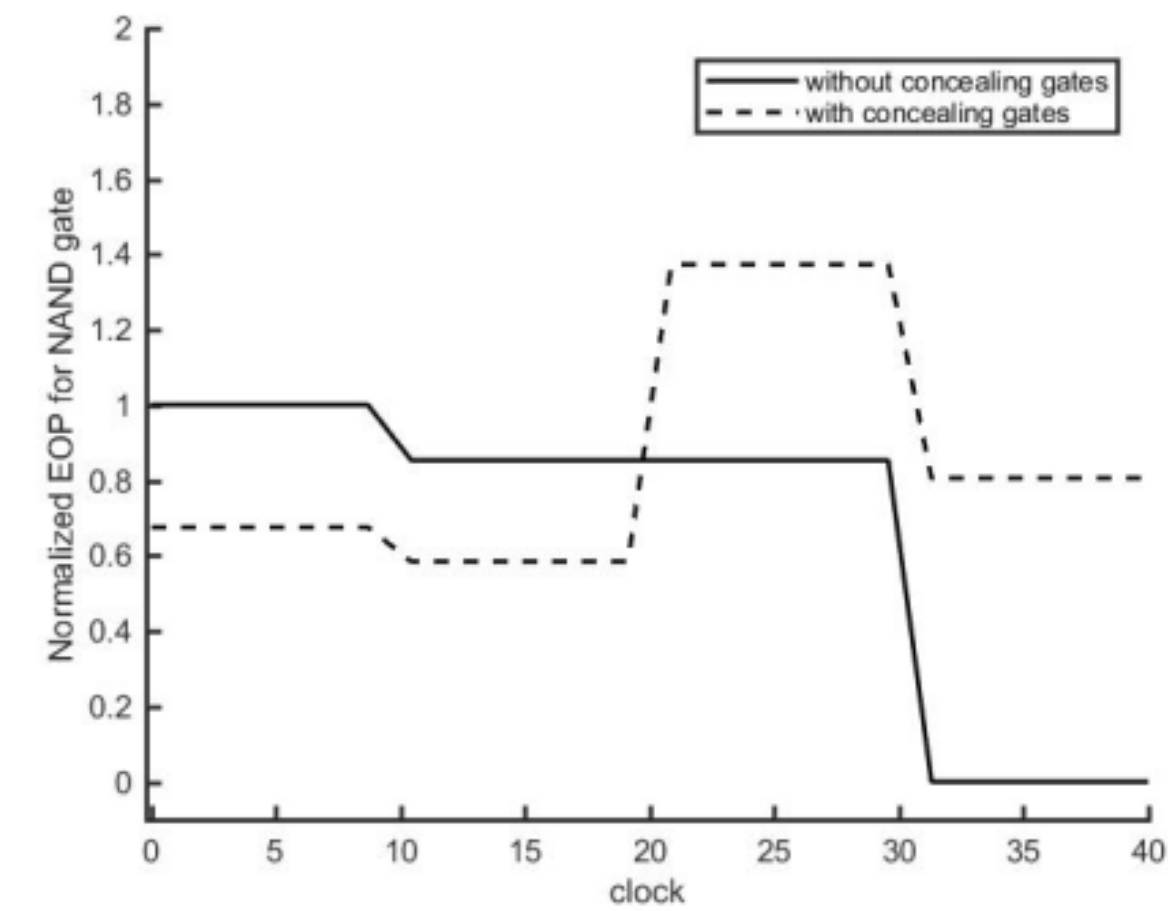
EOP Data with Concealing Gate



(a)

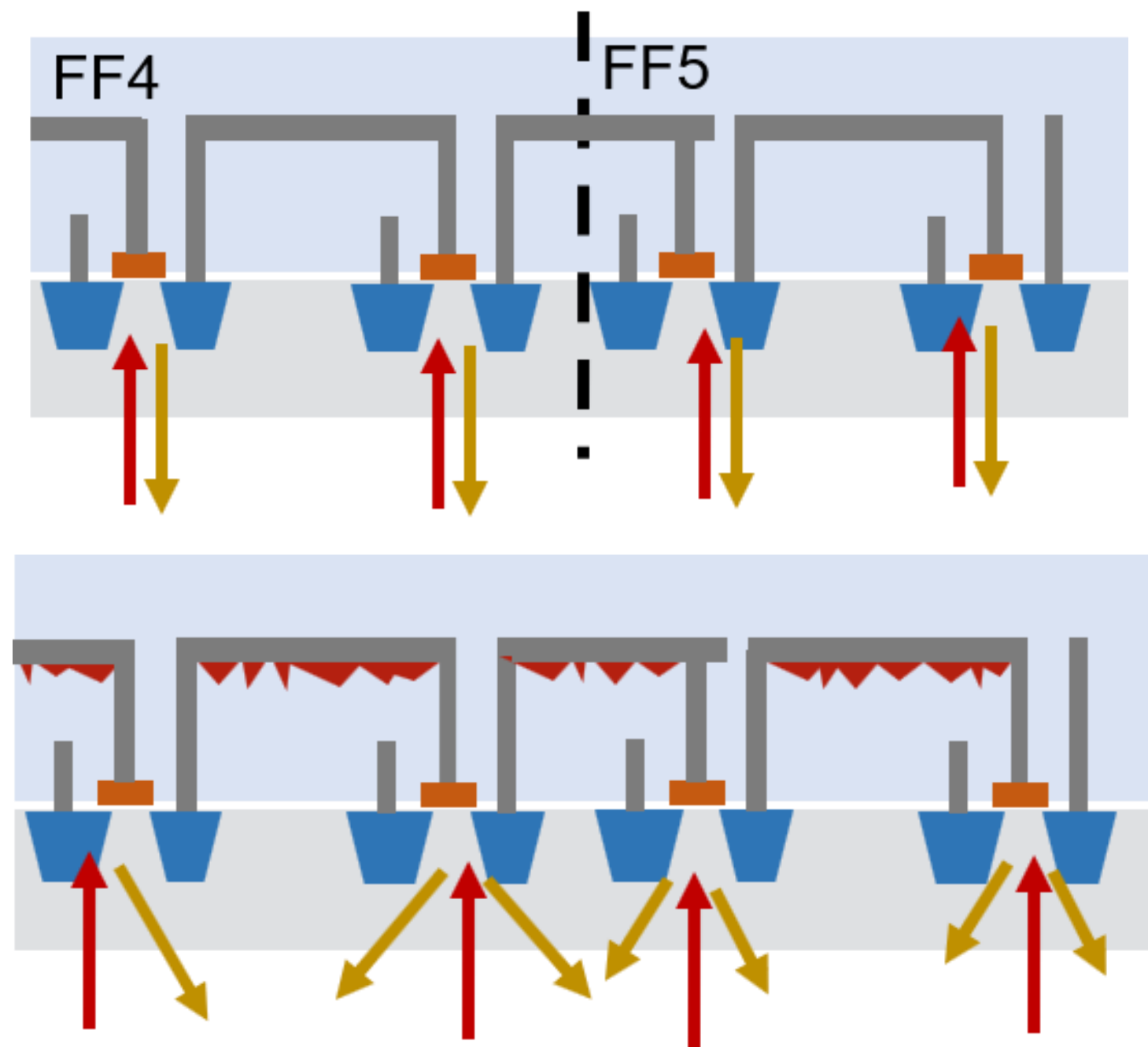


(b)

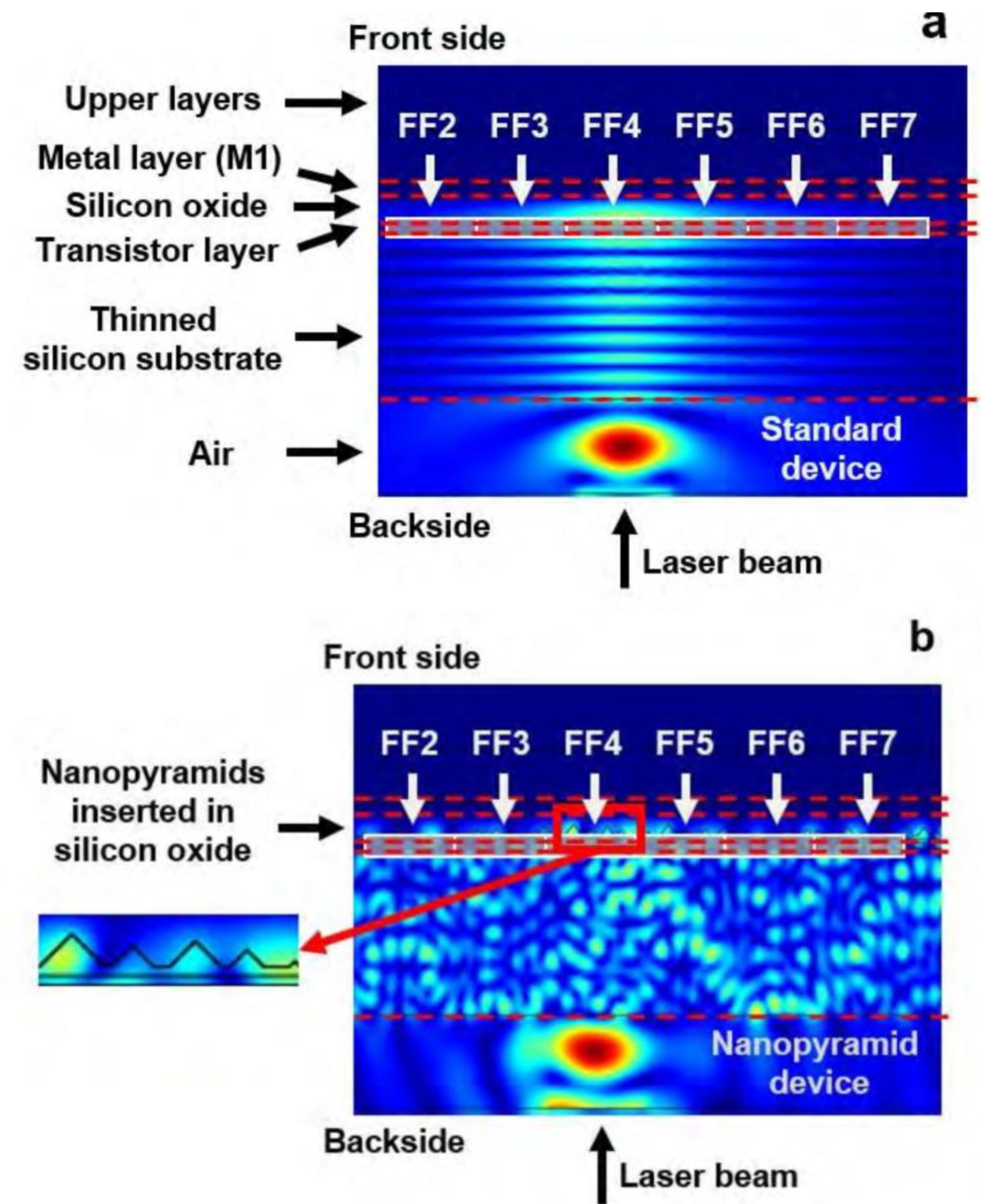


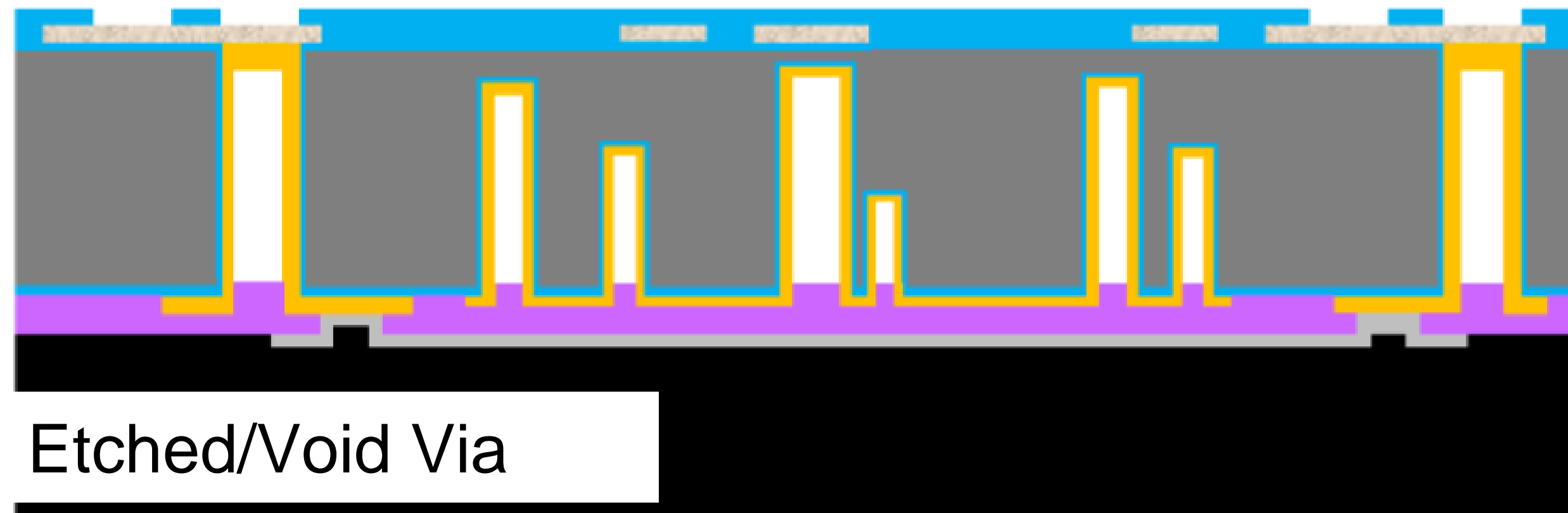
(c)

# Nanopyramid to Camouflage Circuit Activity



- Laser scattering is applicable for any laser based attack approach
- No additional power or area



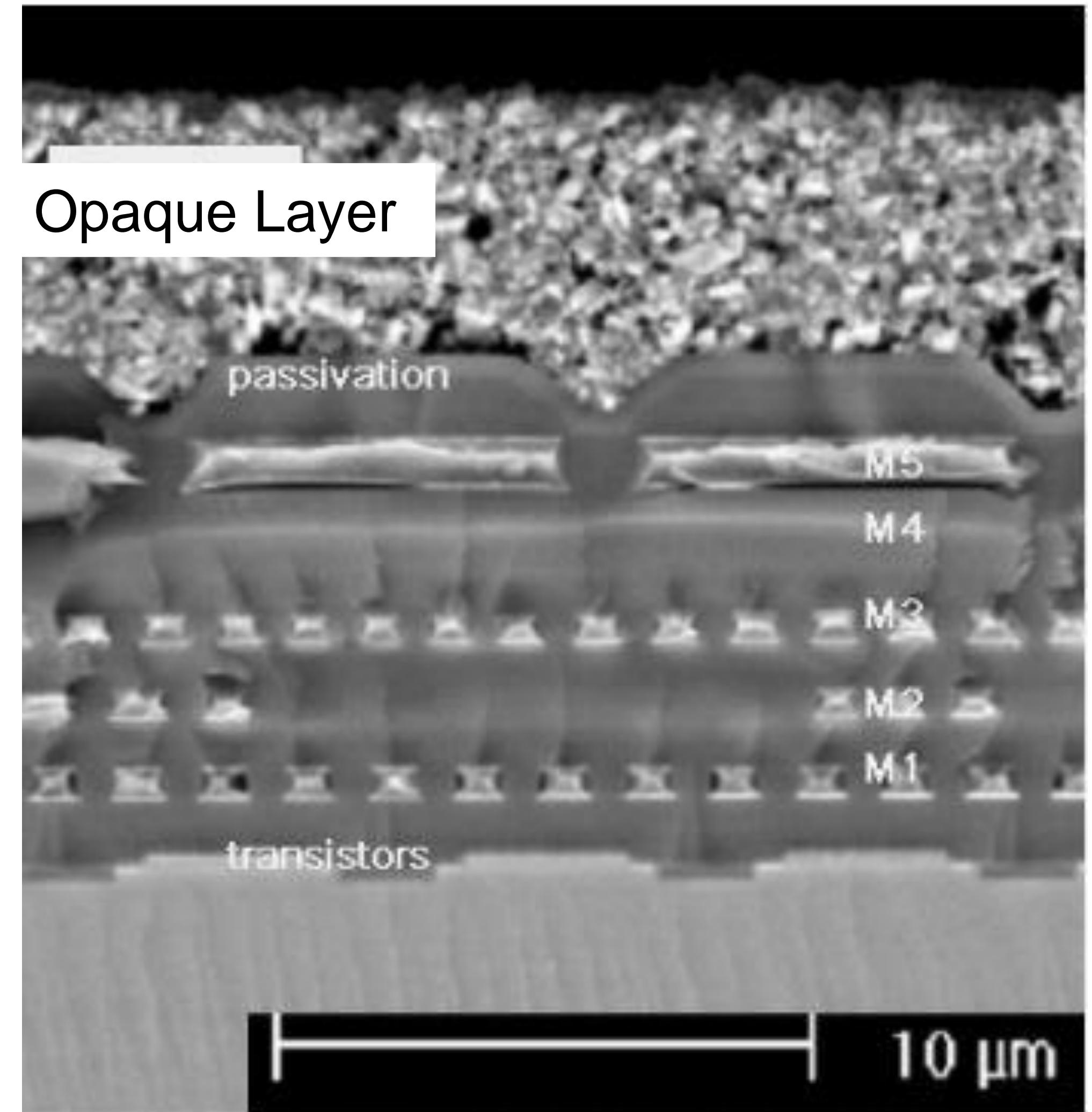


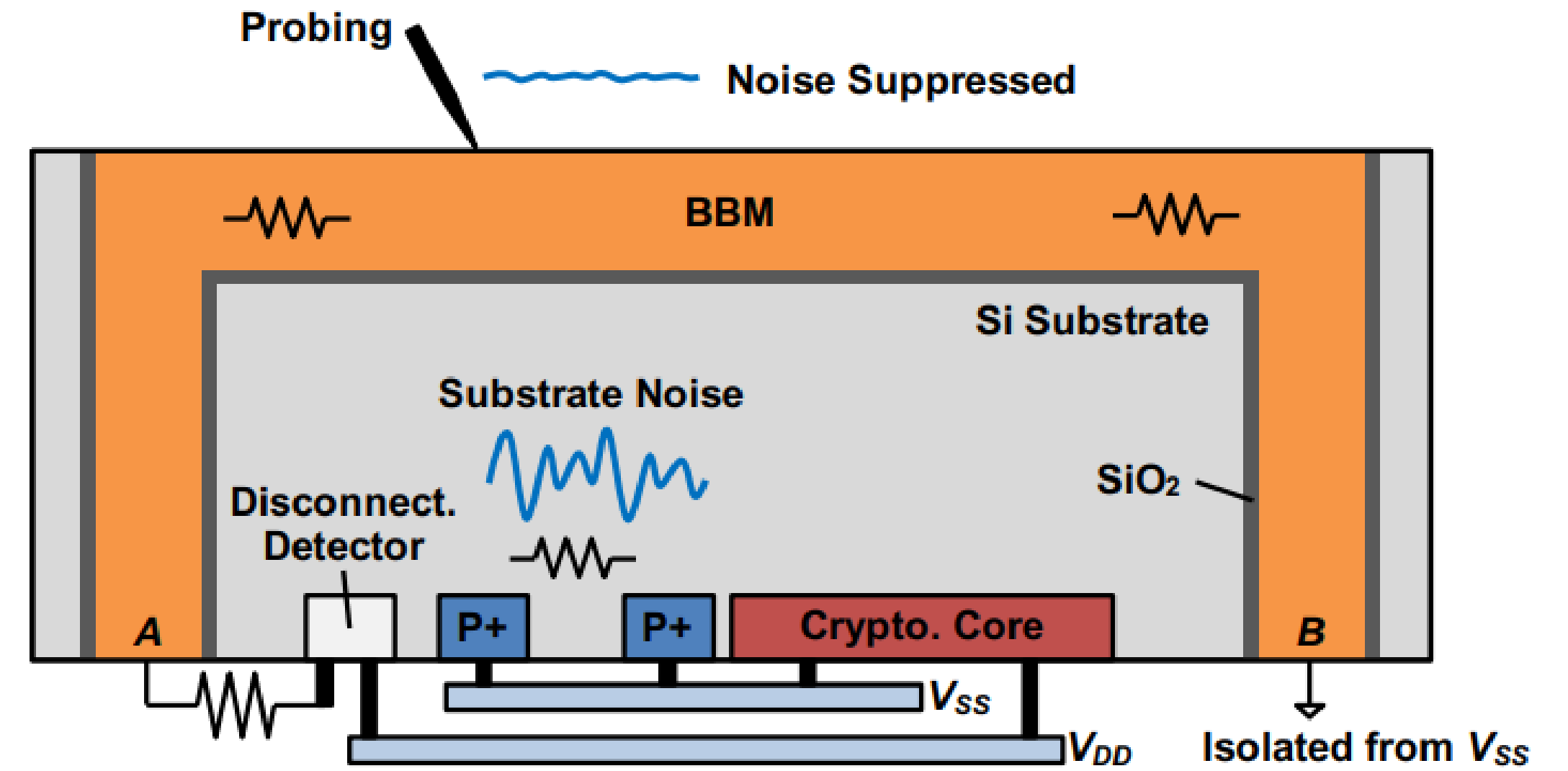
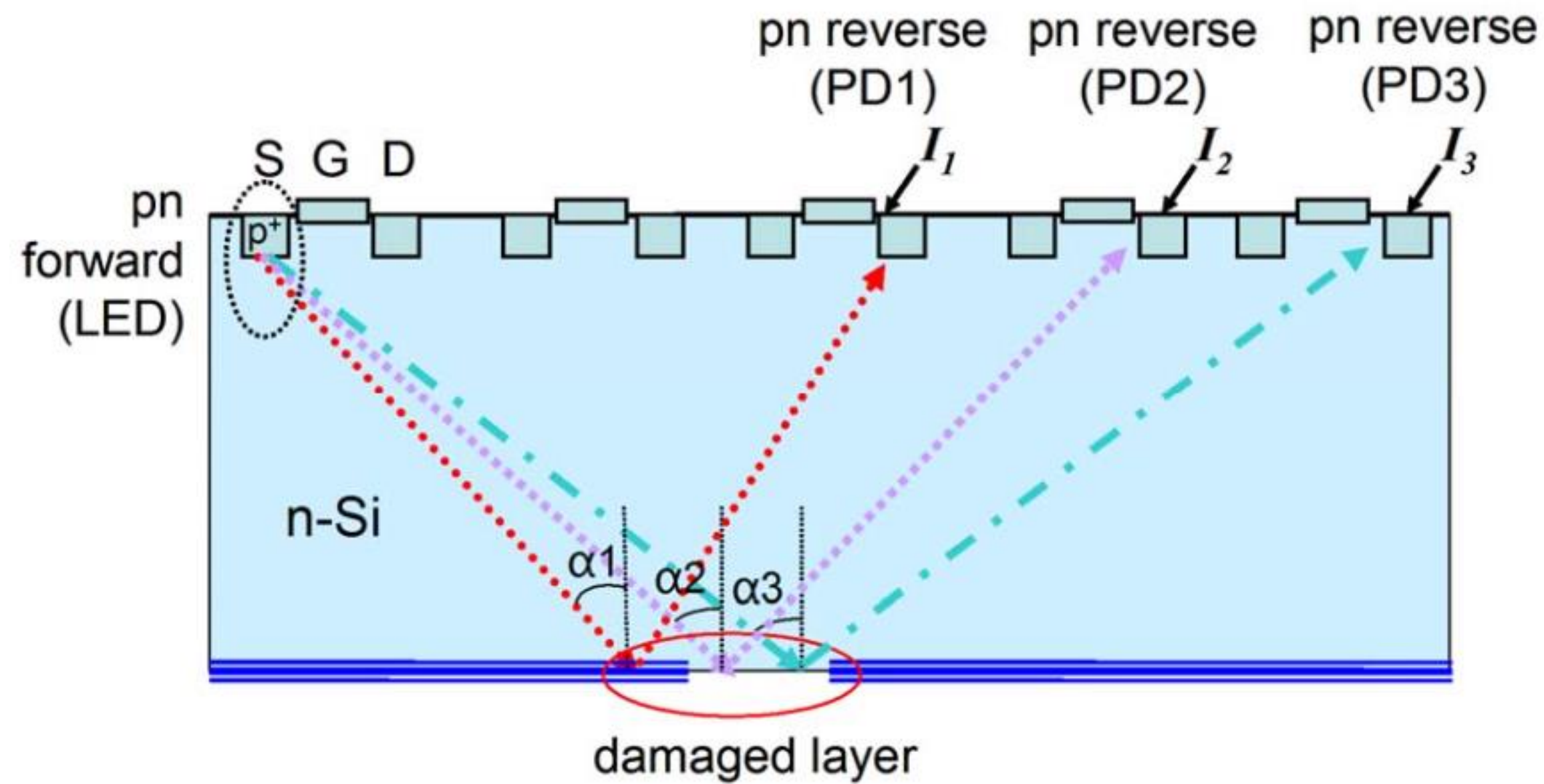
## ➤ Etched/Void Via

- aging
- reliability

## ➤ Opaque layer

- Removable by polishing



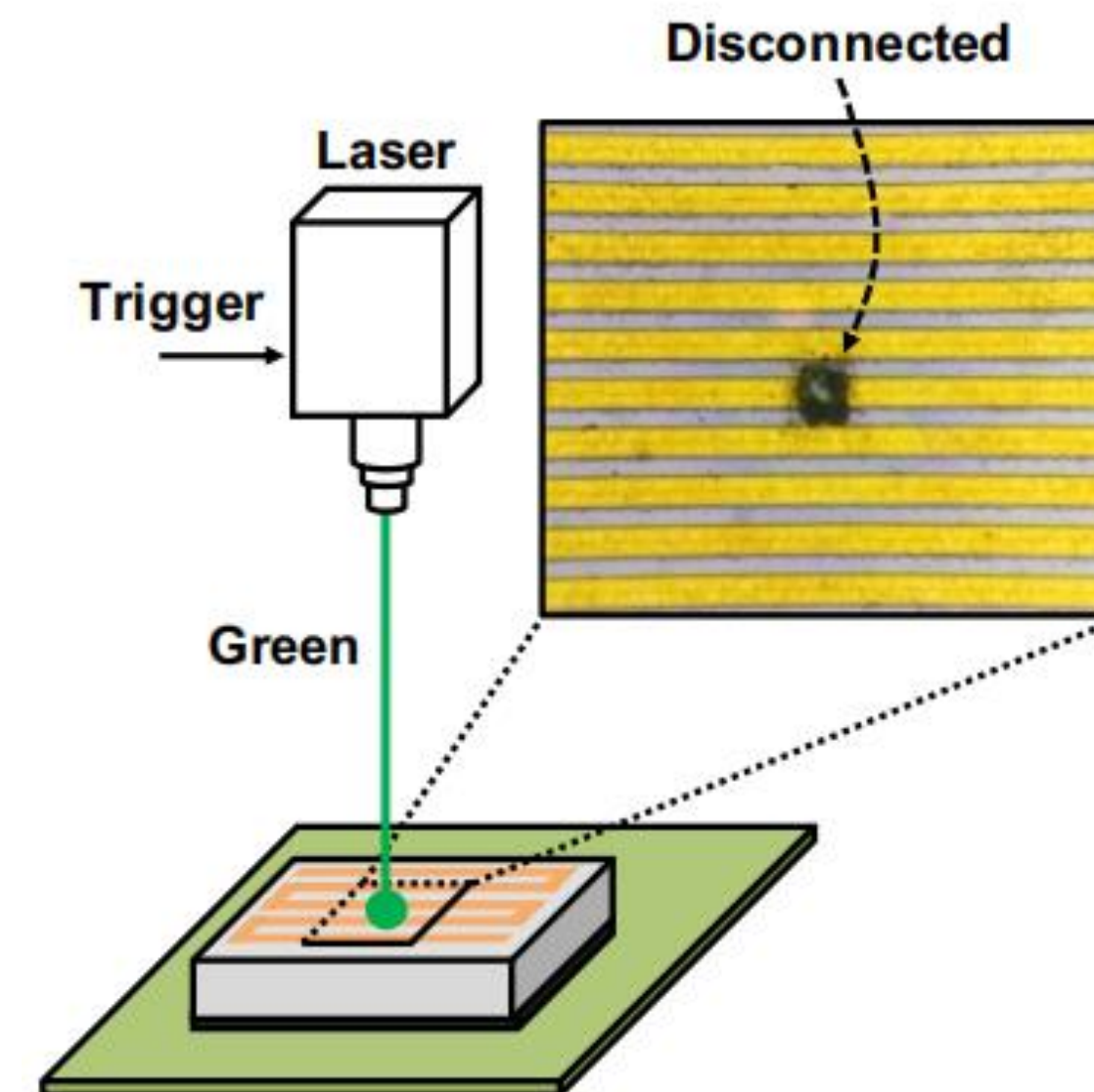


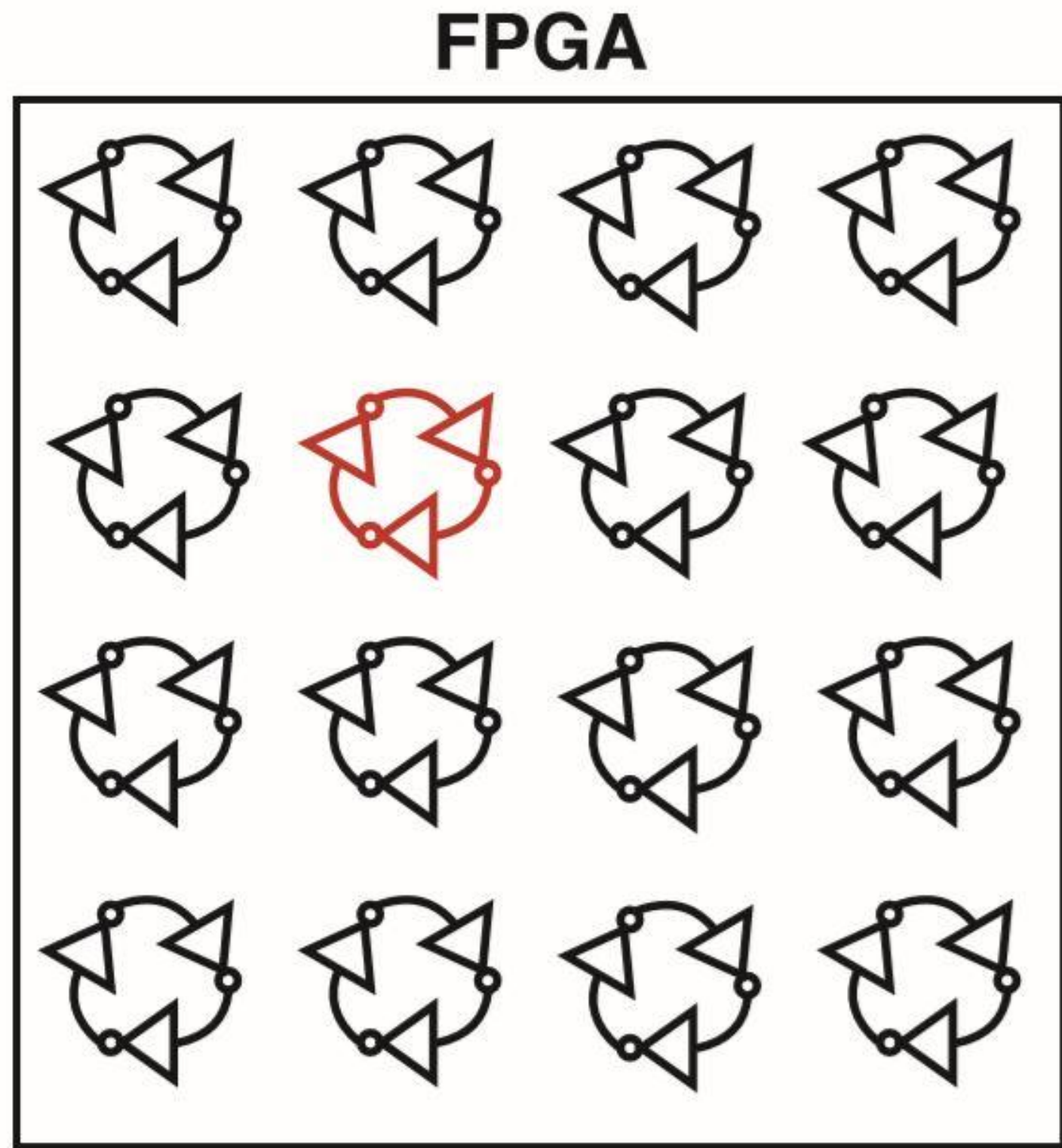
➤ **P-N photo diode:**

- Applicable for LFI

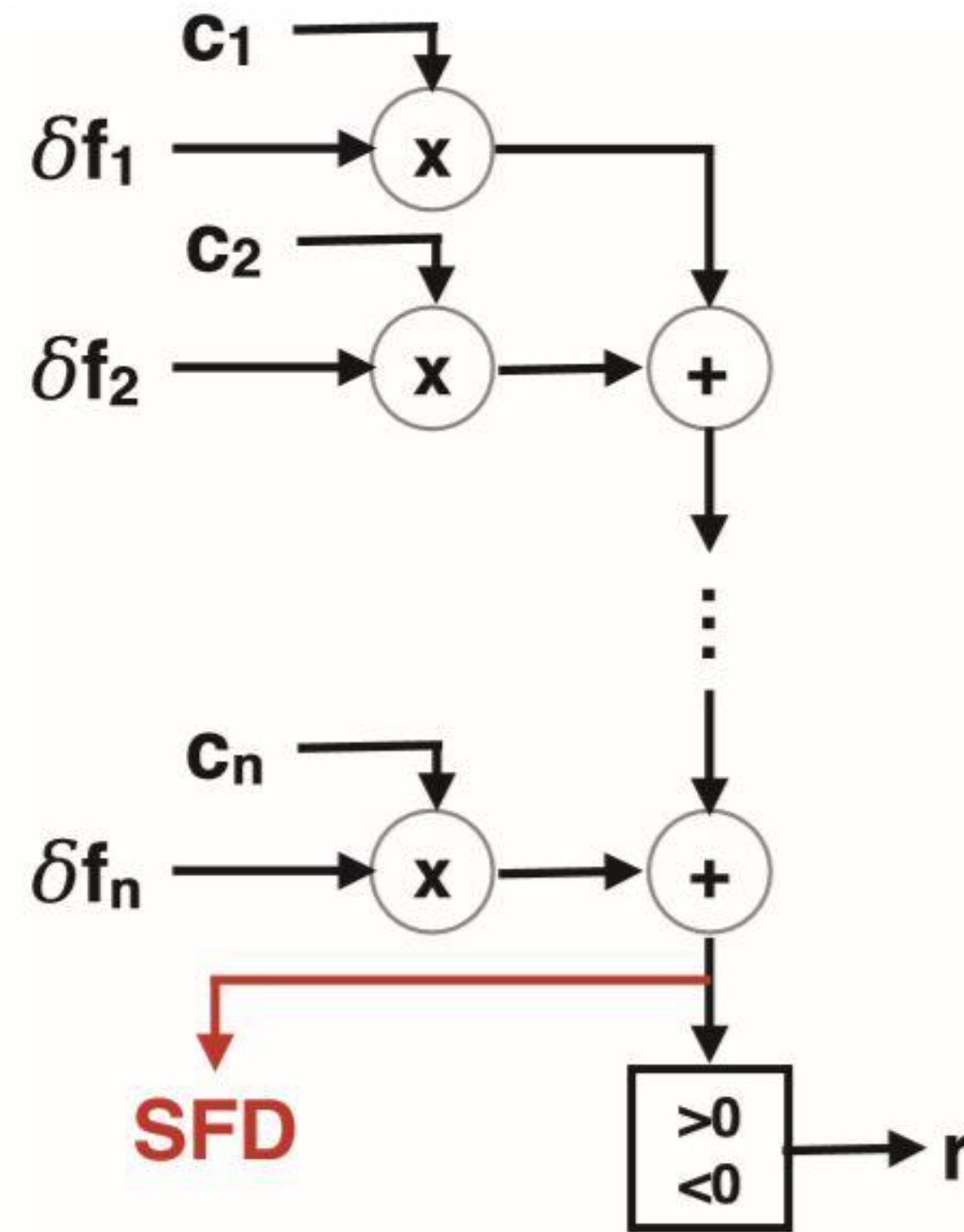
➤ **Backside Mesh:**

- Bypassed with circuit edit

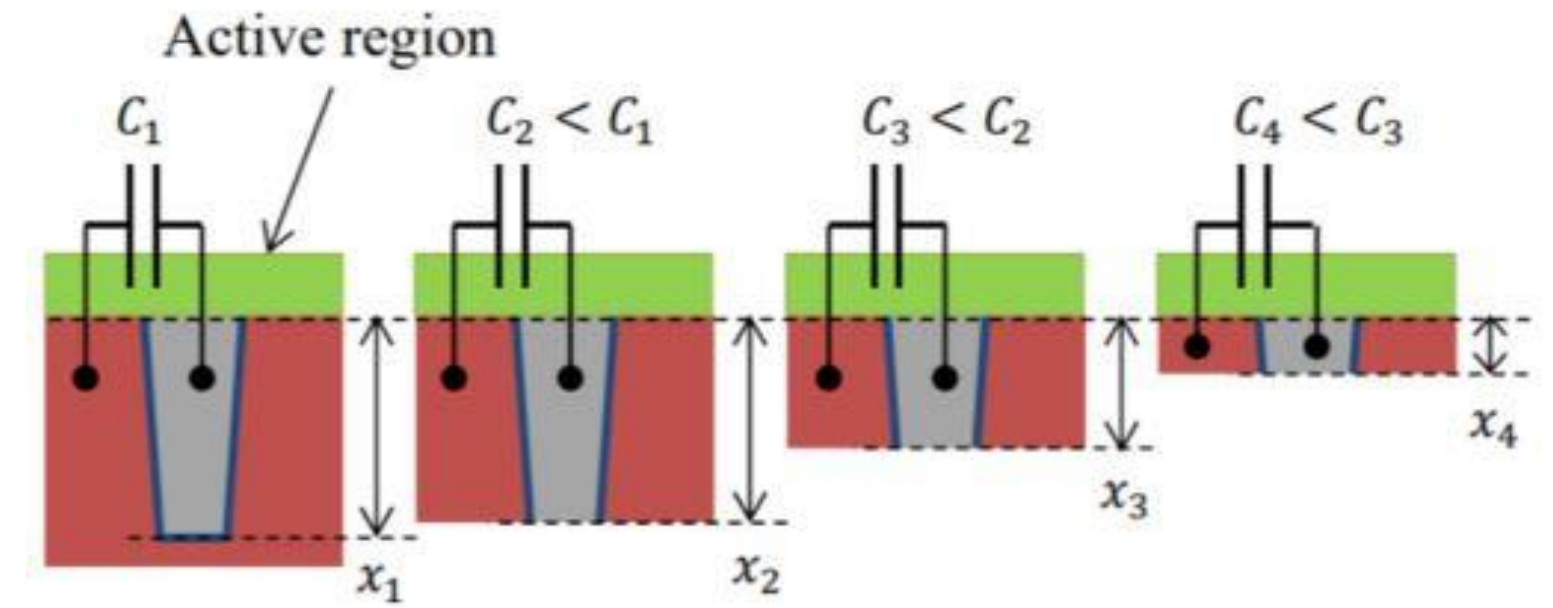




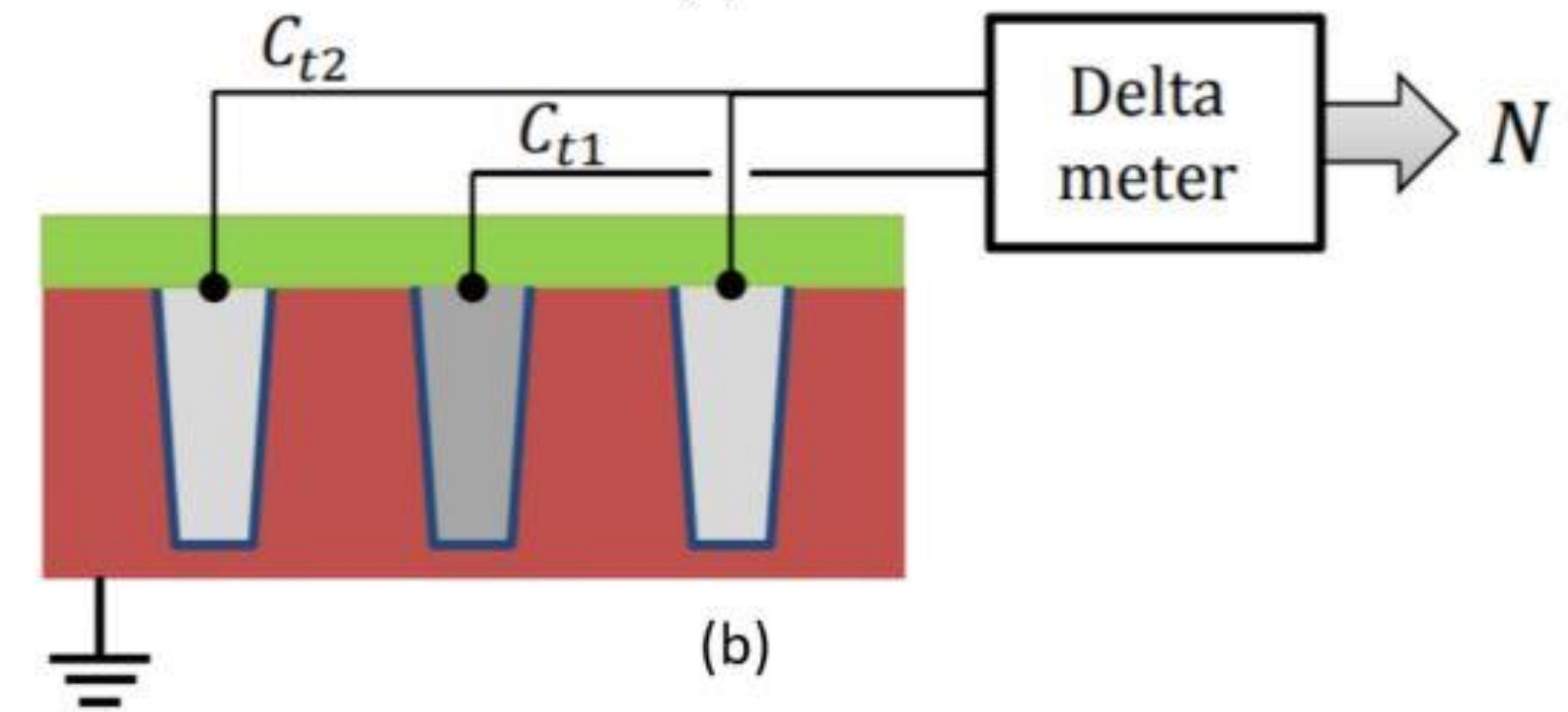
(a)



(b)



(a)



(b)

- Additional area and optimization required
- Mostly ineffective against thermal laser → focused on laser fault detection